

RL78/L1C

RENESAS MCU

R01DS0192EJ0221

Rev.2.21

Nov 30, 2022

Integrated LCD controller/driver, 12-bit resolution A/D Converter, USB 2.0 controller (function), True Low Power Platform (as low as 112.5 μ A/MHz, and 0.68 μ A for RTC2 + LVD), 1.6 V to 3.6 V operation, 64 to 256 Kbyte Flash, 33 DMIPS at 24 MHz, for All LCD Based Applications

1. OUTLINE

1.1 Features

Ultra-low power consumption technology

- VDD = single power supply voltage of 1.6 to 3.6 V
- HALT mode
- STOP mode
- SNOOZE mode

RL78 CPU core

- CISC architecture with 3-stage pipeline
- Minimum instruction execution time: Can be changed from high speed (0.04167 μs: @ 24 MHz operation with high-speed on-chip oscillator clock or PLL clock) to ultra-low speed (30.5 μs: @ 32.768 kHz operation with subsystem clock)
- Multiply/divide and multiply/accumulate instructions are supported.
- Address space: 1 Mbyte
- General-purpose registers: (8-bit register x 8) x 4 banks
- On-chip RAM: 8 to 16 KB

Code flash memory

- Code flash memory: 64 to 256 KB
- · Block size: 1 KB
- Prohibition of block erase and rewriting (security function)
- · On-chip debug function
- Self-programming (with boot swap function/flash shield window function)

Data flash memory

- Data flash memory: 8 KB
- Background operation (BGO): Instructions can be executed from the program memory while rewriting the data flash memory.
- Number of rewrites: 1,000,000 times (TYP.)
- Voltage of rewrites: VDD = 1.8 to 3.6 V

High-speed on-chip oscillator

- Select from 48 MHz, 24 MHz, 16 MHz, 12 MHz, 8 MHz, 6 MHz, 4 MHz, 3 MHz, 2 MHz, and 1 MHz
- High accuracy: ±1.0% (VDD = 1.8 to 3.6 V, TA = -20 to +85°C)

Operating ambient temperature

- TA = -40 to +85°C (A: Consumer applications)
- TA = -40 to +105°C (G: Industrial applications)

Power management and reset function

- On-chip power-on-reset (POR) circuit
- On-chip voltage detector (LVD) (Select interrupt and reset from 12 levels)

Data transfer controller (DTC)

- Transfer modes: Normal transfer mode, repeat transfer mode, block transfer mode
- Activation sources: Activated by interrupt sources (30 to 33 sources).
- · Chain transfer function

Event link controller (ELC)

 Event signals of 30 or 31 types can be linked to the specified peripheral function.

Serial interfaces

- Simplified SPI (CSI Note 1): 4 channels
- UART/UART (LIN-bus supported): 4 channels
- I2C/simplified I2C: 5 channels

Timers

- 16-bit timer: 11 channels
- 12-bit interval timer: 1 channel
- Real-time clock 2: 1 channel (calendar for 99 years, alarm function, and clock correction function)
- Watchdog timer: 1 channel (operable with the dedicated low-speed on-chip oscillator)

LCD controller/driver

- Internal voltage boosting method, capacitor split method, and external resistance division method are switchable.
- Segment signal output: 44 (40) Note 2 to 56 (52) Note 2
- Common signal output: 4 (8) Note 2

USB Note 3

- USB version 2.0 (function controller)
- Full-speed transfer (12 Mbps) and low-speed transfer (1.5 Mbps) are supported
- Compliant to Battery Charging Specification Revision 1.2

A/D converter

- 8/10-bit resolution A/D converter (VDD = 1.6 to 3.6 V)
- 12-bit resolution A/D converter (VDD = 2.4 to 3.6 V)
- Analog input: 9 to 13 channels
- Internal reference voltage (TYP. 1.45 V) and temperature sensor Note 3

D/A converter

- 8-bit resolution D/A converter (VDD = 1.6 to 3.6 V)
- Analog output: 2 channels
- Output voltage: 0 V to VDD
- Real-time output function

Comparator

- 2 channels
- Operating modes: Comparator high-speed mode, comparator low-speed mode, window mode
- The external reference voltage or internal reference voltage can be selected as the reference voltage.

I/O ports

- I/O ports: 59 to 77 (N-ch open drain I/O [withstand voltage of 6 V]: 2)
- Can be set to N-ch open drain, TTL input buffer, and on-chip pull-up
- On-chip key interrupt function
- On-chip clock output/buzzer output controller

Others

- · On-chip BCD (binary-coded decimal) correction circuit
 - Note 1. Although the CSI function is generally called SPI, it is also called CSI in this product, so it is referred to as such in this manual.
 - **Note 2.** The number in parentheses indicates the number of signal outputs when 8 coms are used.
 - Note 3. Selectable only in HS (high-speed main) mode.
 - Remark The functions mounted depend on the product. See 1.6 Outline of Functions.



O ROM, RAM capacities

Products with USB

Flash ROM	Data Flash	Data Flash RAM			RL78/L1C		
		KAW	80 pins	85 pins	100 pins		
256 KB	8 KB	16 KB Note	R5F110MJ	R5F110NJ	R5F110PJ		
192 KB	8 KB	16 KB Note	R5F110MH	R5F110NH	R5F110PH		
128 KB	8 KB	12 KB	R5F110MG	R5F110NG	R5F110PG		
96 KB	8 KB	10 KB	R5F110MF	R5F110NF	R5F110PF		
64 KB	8 KB	8 KB	R5F110ME	R5F110NE	R5F110PE		

Products without USB

Flash ROM	Data Flash	RAM	RL78/L1C			
Flasii KOW	Data Flasii	KAIVI	80 pins	85 pins	100 pins	
256 KB	8 KB	16 KB Note	R5F111MJ	R5F111NJ	R5F111PJ	
192 KB	8 KB	16 KB Note	R5F111MH	R5F111NH	R5F111PH	
128 KB	8 KB	12 KB	R5F111MG	R5F111NG	R5F111PG	
96 KB	8 KB	10 KB	R5F111MF	R5F111NF	R5F111PF	
64 KB	8 KB	8 KB	R5F111ME	R5F111NE	R5F111PE	

Note This is about 15 KB when the self-programming function and data flash function are used (For details, see CHAPTER 3 in the RL78/L1C User's Manual).

1.2 Ordering Information

<R> Products with USB

Pin		Fields of	Orderable Part Number			
Count	Package	Application	Product Name	Packaging Specifications	RENESAS Code	
80 pins	80-pin plastic LFQFP (12 x 12 mm, 0.5 mm pitch)	А	R5F110MEAFB, R5F110MFAFB, R5F110MGAFB, R5F110MHAFB, R5F110MJAFB	#10,#50	PLQP0080KB-B PLQP0080KJ-A	
				#30	PLQP0080KB-B	
		G	R5F110MEGFB, R5F110MFGFB, R5F110MGGFB, R5F110MHGFB, R5F110MJGFB	#10,#50	PLQP0080KB-B PLQP0080KJ-A	
				#30	PLQP0080KB-B	
85 pins	85-pin plastic VFLGA (7 x 7 mm, 0.65 mm pitch)	А	R5F110NEALA, R5F110NFALA, R5F110NGALA, R5F110NHALA, R5F110NJALA	#U0,#W0	PVLG0085JA-A	
		G	R5F110NEGLA, R5F110NFGLA, R5F110NGGLA, R5F110NHGLA, R5F110NJGLA			
100 pins	100-pin plastic LFQFP (14 × 14 mm, 0.5 mm pitch)	А	R5F110PEAFB, R5F110PFAFB, R5F110PGAFB, R5F110PHAFB, R5F110PJAFB	#10,#50	PLQP0100KB-B PLQP0100KP-A	
				#30	PLQP0100KB-B	
		G	R5F110PEGFB, R5F110PFGFB, R5F110PGGFB, R5F110PHGFB, R5F110PJGFB	#10,#50	PLQP0100KB-B PLQP0100KP-A	
				#30	PLQP0100KB-B	

Products without USB

<R>

Pin		Fields of	Orderable Part Number			
Count	Package	Application	Product Name	Packaging Specifications	RENESAS Code	
80 pins	80-pin plastic LFQFP (12 x 12 mm, 0.5 mm pitch)	A	R5F111MEAFB, R5F111MFAFB, R5F111MGAFB, R5F111MHAFB, R5F111MJAFB	#10,#50	PLQP0080KB-B PLQP0080KJ-A	
				#30	PLQP0080KB-B	
		G	R5F111MEGFB, R5F111MFGFB, R5F111MGGFB, R5F111MHGFB, R5F111MJGFB	#10,#50	PLQP0080KB-B PLQP0080KJ-A	
				#30	PLQP0080KB-B	
85 pins	85-pin plastic VFLGA (7 x 7 mm, 0.65 mm pitch)	А	R5F111NEALA, R5F111NFALA, R5F111NGALA, R5F111NHALA, R5F111NJALA	#U0,#W0	PVLG0085JA-A	
		G	R5F111NEGLA, R5F111NFGLA, R5F111NGGLA, R5F111NHGLA, R5F111NJGLA			
100 pins	100-pin plastic LFQFP (14 x 14 mm, 0.5 mm pitch)	А	R5F111PEAFB, R5F111PFAFB, R5F111PGAFB, R5F111PHAFB, R5F111PJAFB	#10,#50	PLQP0100KB-B PLQP0100KP-A	
				#30	PLQP0100KB-B	
		G	R5F111PEGFB, R5F111PFGFB, R5F111PGGFB, R5F111PHGFB, R5F111PJGFB	#10,#50	PLQP0100KB-B PLQP0100KP-A	
				#30	PLQP0100KB-B	

Part No. R 5 F 1 1 0 P E A x x x F B # 3 0 Packaging specification: #10, #30: Tray (LFQFP) #U0: Tray (VFLGA) #50: Embossed Tape (LFQFP) #W0: Embossed Tape (VFLGA) Package type: FB: LFQFP, 0.50 mm pitch LA: VFLGA, 0.65 mm pitch ROM number (Omitted with blank products) Fields of application: A: Consumer applications, T_A = -40 to +85°C G: Industrial applications, TA = -40 to +105°C ROM capacity: E: 64 KB F: 96 KB G: 128 KB H: 192 KB J: 256 KB Pin count: M: 80-pin N: 85-pin P: 100-pin RL78/L1C Group 110: Products with USB 111: Products without USB Memory type: F: Flash memory

Figure 1 - 1 Part Number, Memory Size, and Package of RL78/L1C

Caution Orderable part numbers are current as of when this manual was published.

Please make sure to refer to the relevant product page on the Renesas website for the latest part numbers.

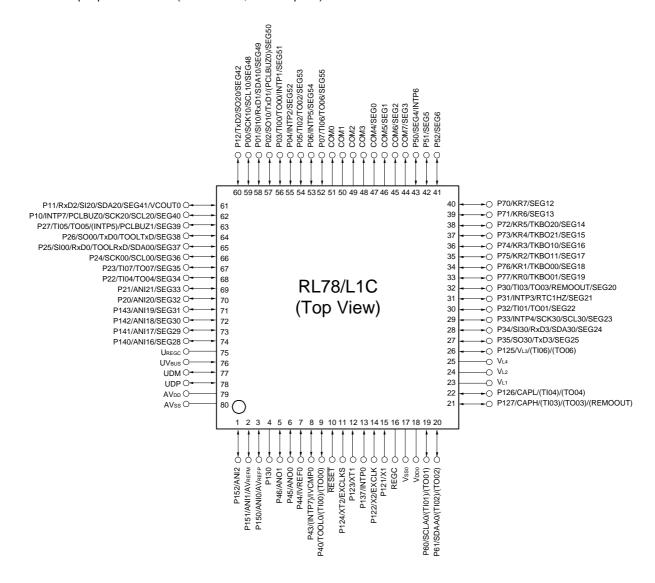
Renesas MCU

Renesas semiconductor product

1.3 Pin Configuration (Top View)

1.3.1 80-pin products (with USB)

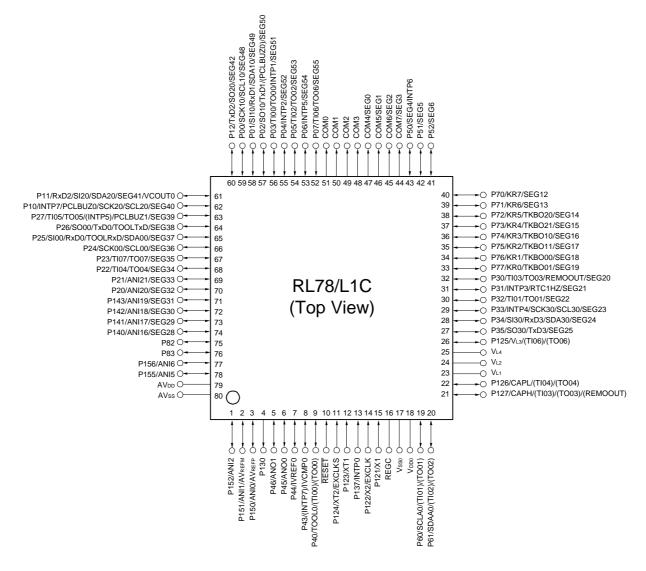
• 80-pin plastic LFQFP (12 x 12 mm, 0.5 mm pitch)



- Caution 1. Connect the REGC pin to Vss pin via a capacitor (0.47 to 1 $\mu\text{F}).$
- Caution 2. Connect the UREGC pin to VSS pin via a capacitor (0.33 µF).
- Remark 1. For pin identification, see 1.4 Pin Identification.
- Remark 2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR).

1.3.2 80-pin products (without USB)

• 80-pin plastic LFQFP (fine pitch) (12 x 12 mm, 0.5 mm pitch)

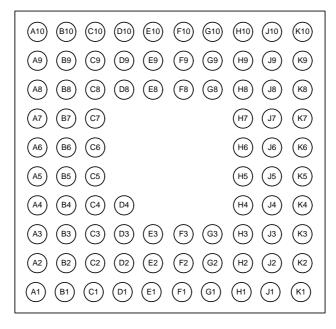


Caution Connect the REGC pin to Vss pin via a capacitor (0.47 to 1 μ F).

Remark 1. For pin identification, see 1.4 Pin Identification.

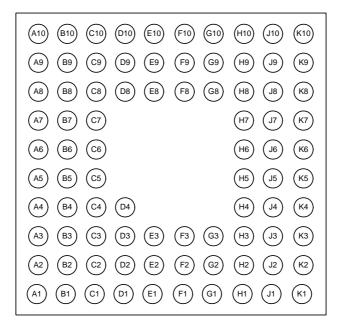
Remark 2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR).

1.3.3 85-pin products (with USB)



Pin	Name	Pin	Name	Pin	Name	Pin	Name	Pin	Name
A1	COM7/SEG3	C1	COM2	E1	P04/INTP2/SEG52	G1	P00/SCK10/SCL10/ SEG48	J1	Vsso
A2	P51/SEG5	C2	COM5/SEG1	E2	P05/Tl02/TO02/SEG53	G2	Vsso	J2	P11/RxD2/SI20/SDA20/ SEG41/VCOUT0
А3	P70/KR7/SEG12	C3	COM6/SEG2	E3	P06/INTP5/SEG54	G3	P12/TxD2/SO20/SEG42/ VCOUT1	J3	P26/SO00/TxD0/ TOOLTxD/SEG38
A4	P73/KR4/TKBO21/SEG15	C4	P71/KR6/SEG13	E4	_	G4	_	J4	P23/TI07/TO07/SEG35
A5	P74/KR3/TKBO10/SEG16	C5	P76/KR1/TKBO00/SEG18	E5	_	G5	_	J5	P20/ANI20/SEG32
A6	P31/INTP3/RTC1HZ/ SEG21	C6	P77/KR0/TKBO01/SEG19	E6	_	G6	_	J6	P141/ANI17/SEG29
A7	P33/INTP4/SCK30/SCL30/ SEG23	C7	P34/SI30/RxD3/SDA30/ SEG24	E7	_	G7	_	J7	UREGC
A8	P35/SO30/TxD3/SEG25	C8	VL1	E8	P40/TOOL0/(TI00)/(TO00)	G8	P44/(SCK10)/(SCL10)/ IVREF0	J8	UVBUS
A9	VL4	C9	P61/SDAA0/(TI02)/(TO02)	E9	P137/INTP0	G9	P45/ANO0	J9	AVDD
A10	P126/CAPL/(TI04)/(TO04)	C10	VDD0	E10	P122/X2/EXCLK	G10	P123/XT1	J10	P150/ANI0/AVREFP
B1	COM4/SEG0	D1	СОМО	F1	P03/TI00/TO00/INTP1/ SEG51	H1	Vsso	K1	Vsso
B2	P50/SEG4/INTP6	D2	COM1	F2	P02/SO10/TxD1/ (PCLBUZ0)/SEG50	H2	Vsso	K2	P27/TI05/TO05/(INTP5)/ PCLBUZ1/SEG39
В3	P52/SEG6	D3	P07/TI06/TO06/SEG55	F3	P01/SI10/RxD1/SDA10/ SEG49	НЗ	P10/INTP7/PCLBUZ0/ SCK20/SCL20/SEG40	K3	P25/SI00/RxD0/ TOOLRxD/SDA00/SEG37
B4	P72/KR5/TKBO20/SEG14	D4	СОМЗ	F4	_	H4	P24/SCK00/SCL00/ SEG36	K4	P22/TI04/TO04/SEG34
B5	P75/KR2/TKBO11/SEG17	D5	_	F5	_	H5	P21/ANI21/SEG33	K5	P143/ANI19/SEG31
B6	P30/TI03/TO03/ REMOOUT/SEG20	D6	_	F6	_	H6	P140/ANI16/SEG28	K6	P142/ANI18/SEG30
В7	P32/TI01/TO01/SEG22	D7	_	F7	=	H7	P152/ANI2	K7	UDM
B8	P125/VL3/(TI06)/(TO06)	D8	P60/SCLA0/(TI01)/(TO01)	F8	P43/(INTP7)/(SI10)/ (RxD1)/(SDA10)/IVCMP0	H8	P46/ANO1	K8	UDP
В9	VL2	D9	REGC	F9	RESET	Н9	P130	K9	AVss
B10	P127/CAPH/(TI03)/ (TO03)/(REMOOUT)	D10	P121/X1	F10	Vsso	H10	P124/XT2/EXCLKS	K10	P151/ANI1/AVREFM

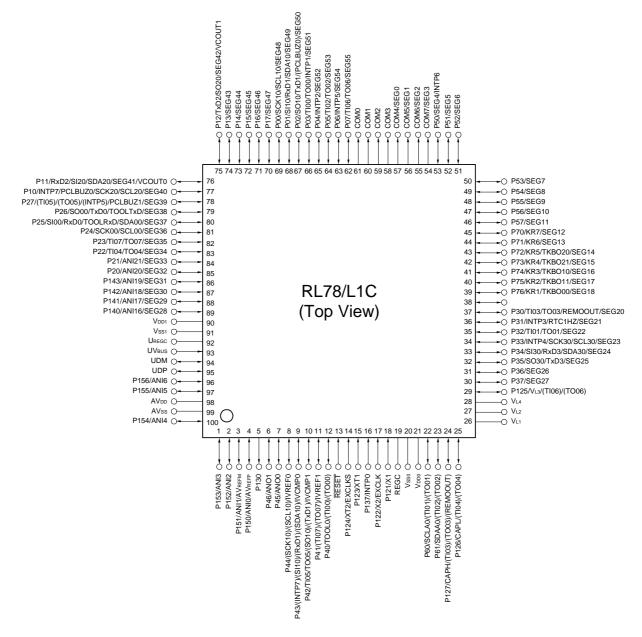
1.3.4 85-pin products (without USB)



Pin	Name	Pin	Name	Pin	Name	Pin	Name	Pin	Name
A1	COM7/SEG3	C1	COM2	E1	P04/INTP2/SEG52	G1	P00/SCK10/SCL10/ SEG48	J1	Vsso
A2	P51/SEG5	C2	COM5/SEG1	E2	P05/Tl02/TO02/SEG53	G2	Vsso	J2	P11/RxD2/SI20/SDA20/ SEG41/VCOUT0
А3	P70/KR7/SEG12	C3	COM6/SEG2	E3	P06/INTP5/SEG54	G3	P12/TxD2/SO20/SEG42/ VCOUT1	J3	P26/SO00/TxD0/ TOOLTxD/SEG38
A4	P73/KR4/TKBO21/SEG15	C4	P71/KR6/SEG13	E4	_	G4	_	J4	P23/TI07/TO07/SEG35
A5	P74/KR3/TKBO10/SEG16	C5	P76/KR1/TKBO00/SEG18	E5	_	G5	_	J5	P20/ANI20/SEG32
A6	P31/INTP3/RTC1HZ/ SEG21	C6	P77/KR0/TKBO01/ SEG19	E6	_	G6	_	J6	P141/ANI17/SEG29
A7	P33/INTP4/SCK30/ SCL30/SEG23	C7	P34/SI30/RxD3/SDA30/ SEG24	E7	_	G7	_	J7	P82
A8	P35/SO30/TxD3/SEG25	C8	VL1	E8	P40/TOOL0/(TI00)/(TO00)	G8	P44/(SCK10)/(SCL10)/ IVREF0	J8	P83
A9	VL4	C9	P61/SDAA0/(TI02)/(TO02)	E9	P137/INTP0	G9	P45/ANO0	J9	AVDD
A10	P126/CAPL/(TI04)/(TO04)	C10	VDD0	E10	P122/X2/EXCLK	G10	P123/XT1	J10	P150/ANI0/AVREFP
B1	COM4/SEG0	D1	СОМО	F1	P03/TI00/TO00/INTP1/ SEG51	H1	Vsso	K1	Vsso
B2	P50/SEG4/INTP6	D2	COM1	F2	P02/SO10/TxD1/ (PCLBUZ0)/SEG50	H2	Vsso	K2	P27/TI05/TO05/(INTP5)/ PCLBUZ1/SEG39
В3	P52/SEG6	D3	P07/TI06/TO06/SEG55	F3	P01/SI10/RxD1/SDA10/ SEG49	НЗ	P10/INTP7/PCLBUZ0/ SCK20/SCL20/SEG40	K3	P25/SI00/RxD0/ TOOLRxD/SDA00/SEG37
B4	P72/KR5/TKBO20/SEG14	D4	СОМЗ	F4	_	H4	P24/SCK00/SCL00/ SEG36	K4	P22/TI04/TO04/SEG34
В5	P75/KR2/TKBO11/SEG17	D5	_	F5	_	H5	P21/ANI21/SEG33	K5	P143/ANI19/SEG31
B6	P30/TI03/TO03/ REMOOUT/SEG20	D6	_	F6	_	H6	P140/ANI16/SEG28	K6	P142/ANI18/SEG30
В7	P32/TI01/TO01/SEG22	D7	_	F7	_	H7	P152/ANI2	K7	P156/ANI6
B8	P125/VL3/(TI06)/(TO06)	D8	P60/SCLA0/(TI01)/(TO01)	F8	P43/(INTP7)/(SI10)/ (RxD1)/(SDA10)/IVCMP0	H8	P46/ANO1	K8	P155/ANI5
В9	VL2	D9	REGC	F9	RESET	Н9	P130	K9	AVss
B10	P127/CAPH/(TI03)/ (TO03)/(REMOOUT)	D10	P121/X1	F10	Vsso	H10	P124/XT2/EXCLKS	K10	P151/ANI1/AVREFM

1.3.5 100-pin products (with USB)

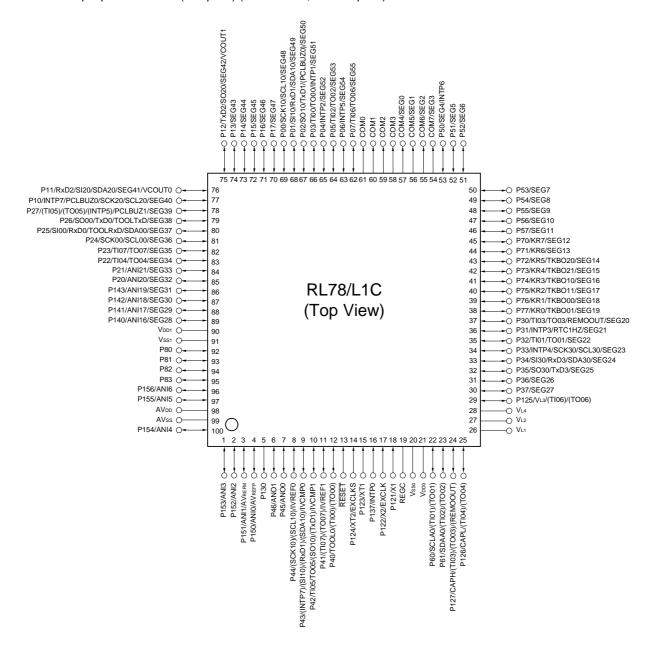
• 100-pin plastic LFQFP (fine pitch) (14 x 14 mm, 0.5 mm pitch)



- Caution 1. Connect the REGC pin to Vss pin via a capacitor (0.47 to 1 µF).
- Caution 2. Connect the UREGC pin to Vss pin via a capacitor (0.33 μF).
- Remark 1. For pin identification, see 1.4 Pin Identification.
- Remark 2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR).

1.3.6 100-pin products (without USB)

• 100-pin plastic LFQFP (fine pitch) (14 x 14 mm, 0.5 mm pitch)



Caution Connect the REGC pin to Vss pin via a capacitor (0.47 to 1 μ F).

Remark 1. For pin identification, see 1.4 Pin Identification.

Remark 2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR).

1.4 Pin Identification

ANIO to ANI6, SCL00, SCL10, SCL20, SCL30 : Serial Clock Output : Analog Input

ANI16 to ANI21

SDAA0, SDA00, SDA10, : Serial Data Input/Output ANO0, ANO1 SDA20, SDA30 : Analog Output

AVDD : Analog Power Supply SEG0 to SEG55 : LCD Segment Output AVREFM : Analog Reference Voltage SI00, SI10, SI20, SI30 : Serial Data Input

> SO00, SO10, SO20, SO30 Minus

AVREFP : Analog Reference Voltage TI00 to TI07 : Timer Input

> Plus TO00 to TO07 : Timer Output

TKBO00, TKBO01, TKBO10, **AVss** : Analog Ground CAPH, CAPL : Capacitor for LCD TKBO11, TKBO20, TKBO21

COM0 to COM7 : LCD Common Output TOOLO : Data Input/Output for Tool

EXCLK : External Clock Input TOOLRxD, TOOLTxD : Data Input/Output for

> (Main System Clock) **External Device**

: Serial Data Output

: Crystal Oscillator

EXCLKS : External Clock Input UDM, UDP : USB Input/Output

(Subsystem Clock) **UREGC** : USB Regulator Capacitance INTP0 to INTP7 : External Interrupt Input **UV**BUS : USB Input/USB Power Supply

IVCMP0, IVCMP1 TxD0 to TxD3 : Comparator Input : Transmit Data

IVREF0, IVREF1 : Comparator Reference Input VCOUT0, VCOUT1 : Comparator Output

KR0 to KR7 : Key Return VDD0, VDD1 : Power Supply P00 to P07 : Port 0 VL1 to VL4 : LCD Power Supply

P10 to P17 : Port 1 Vsso, Vss1 : Ground

P20 to P27 : Port 2 X1, X2 : Crystal Oscillator

P30 to P37 : Port 3 (Main System Clock)

XT1, XT2

P50 to P57 : Port 5 (Subsystem Clock)

P60 to P62 : Port 6 P70 to P77 : Port 7

: Port 15 PCLBUZ0, PCLBUZ1 : Programmable Clock Output/

: Port 4

: Port 8

: Port 12

: Port 13

: Port 14

Buzzer Output

REGC : Regulator Capacitance **REMOOUT** : Remote Control Output

RESET : Reset

RTC1HZ : Real-time Clock Correction

Clock (1 Hz) Output

RxD0 to RxD3 : Receive Data

SCK00, SCK10, : Serial Clock Input/Output

SCK20, SCK30

P40 to P46

P80 to P83

P121 to P127

P140 to P143

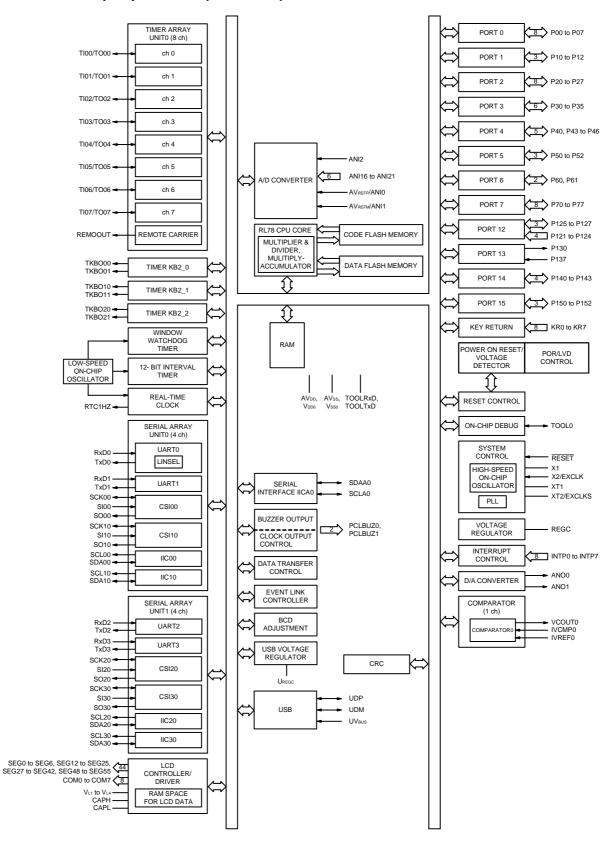
P150 to P156

P130, P137

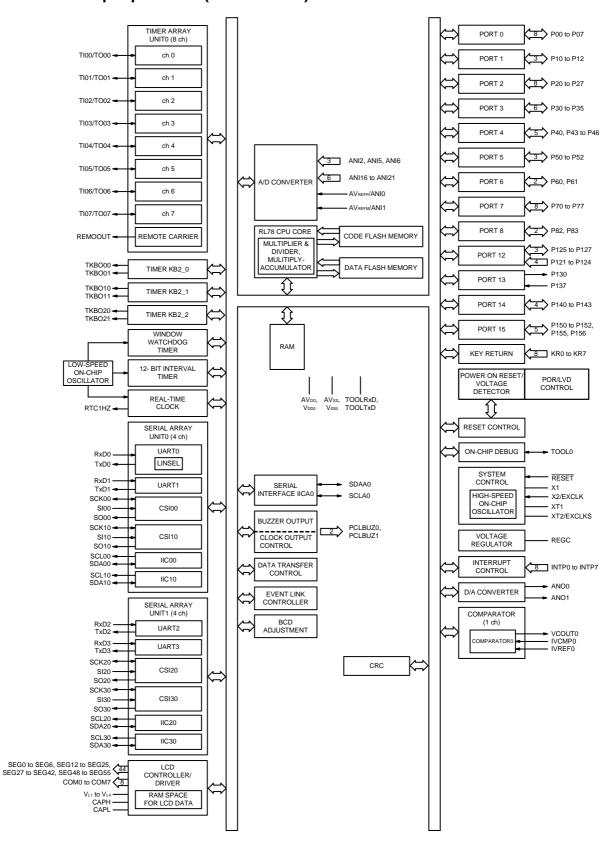
SCLA0 : Serial Clock Input/Output

1.5 Block Diagram

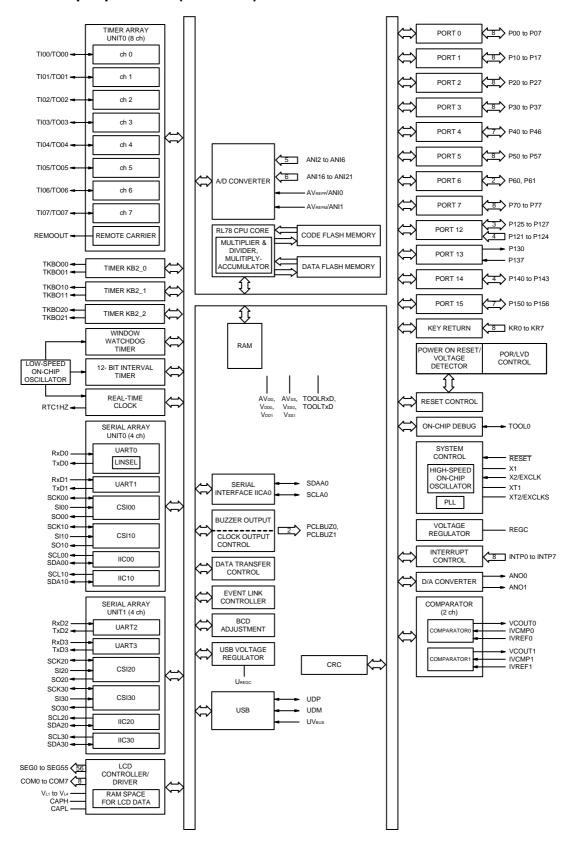
1.5.1 80/85-pin products (with USB)



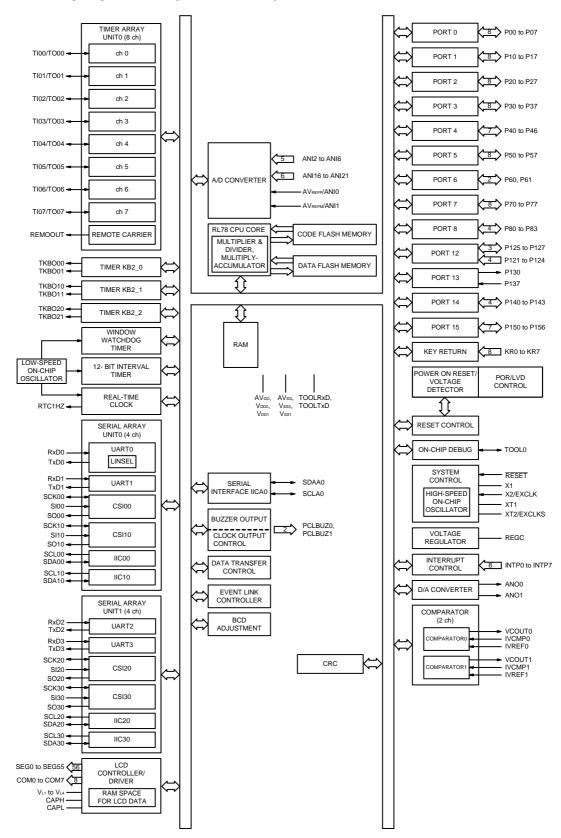
1.5.2 80/85-pin products (without USB)



1.5.3 100-pin products (with USB)



1.5.4 100-pin products (without USB)



1.6 Outline of Functions

[80/85-pin, 100-pin products (with USB)]

(1/2)

	14	80/85-pin	100-pin			
	Item	R5F110Mx/R5F110Nx (x = E to H, J)	R5F110Px (x = E to H, J)			
Code flash memory	(KB)	64 to 256	64 to 256			
Data flash memory (KB)	8	8			
RAM (KB)		8 to 16 ^{Note 1}	8 to 16 ^{Note 1}			
Memory space 1 MB						
Main system clock	High-speed system clock	X1 (crystal/ceramic) oscillation, external main sys 1 to 20 MHz: VDD = 2.7 to 3.6 V, 1 to 8 MHz: VD				
	High-speed on-chip oscillator clock	HS (high-speed main) operation mode: 1 to 24 MHz (VDD = 2.7 to 3.6 V), HS (high-speed main) operation mode: 1 to 16 MHz (VDD = 2.4 to 3.6 V), LS (low-speed main) operation mode: 1 to 8 MHz (VDD = 1.8 to 3.6 V), LV (low-voltage main) operation mode: 1 to 4 MHz (VDD = 1.6 to 3.6 V)				
	PLL clock	6, 12, 24 MHz Note 2: VDD = 2.4 to 3.6 V				
Subsystem clock		XT1 (crystal) oscillation, external subsystem clock 32.768 kHz (TYP.): VDD = 1.6 to 3.6 V	(input (EXCLKS)			
Low-speed on-chip of	oscillator clock	15 kHz (TYP.): VDD = 1.6 to 3.6 V				
General-purpose reg	jister	8 bits × 32 registers (8 bits × 8 registers × 4 banks	s)			
Minimum instruction	execution time	0.04167 μs (High-speed on-chip oscillator clock: fHOCO = fIH = 24 MHz operation)				
		0.04167 μs (PLL clock: fPLL = 48 MHz/fiH = 24 MHz Note 2 operation)				
		0.05 μs (High-speed system clock: fмx = 20 MHz operation)				
		30.5 μs (Subsystem clock: fsub = 32.768 kHz ope	eration)			
Instruction set		 Data transfer (8/16 bits) Adder and subtractor/logical operation (8/16 bits) Multiplication (8 bits × 8 bits, 16 bits × 16 bits), Division (16 bits ÷ 16 bits, 32 bits ÷ 32 bits) Multiplication and Accumulation (16 bits × 16 bits + 32 bits) Rotate, barrel shift, and bit manipulation (Set, reset, test, and Boolean operation), etc. 				
I/O port	Total	59	77			
	CMOS I/O	51	69			
	CMOS input	5	5			
	CMOS output	1	1			
	N-ch open-drain I/O (6 V tolerance)	2	2			
Timer	16-bit timer TAU	8 channels (with 1 channel remote control output	function) (Timer outputs: 8, PWM outputs: 7 Note 3)			
	16-bit timer KB2	3 channels (PWM outputs: 6)				
	Watchdog timer	1 channel				
	12-bit interval timer	1 channel				
	Real-time clock 2	1 channel				
	RTC output	1 1 Hz (subsystem clock: fsub = 32.768 kHz)				

Note 1. In the case of the 16 KB, this is about 15 KB when the self-programming function and data flash function are used (For details, see **CHAPTER 3** in the RL78/L1C User's Manual).

Note 2. In the PLL clock 48 MHz operation, the system clock is 2/4/8 dividing ratio.

Note 3. The number of outputs varies, depending on the setting of channels in use and the number of the master.

(2/2)

			()			
	Item	80/85-pin	100-pin			
	пеш	R5F110Mx/R5F110Nx (x = E to H, J)	R5F110Px (x = E to H, J)			
Clock output	/buzzer output	2	2			
		 2.44 kHz, 4.88 kHz, 9.76 kHz, 1.25 MHz, 2.5 M (Main system clock: fMAIN = 20 MHz operation) 256 Hz, 512 Hz, 1.024 kHz, 2.048 kHz, 4.096 k (Subsystem clock: fSUB = 32.768 kHz operation)) kHz, 8.192 kHz, 16.384 kHz, 32.768 kHz			
8/12-bit reso	lution A/D converter	9 channels	13 channels			
D/A converte	Pr	2 channels	2 channels			
Comparator		1 channel	2 channels			
Serial interface		Simplified SPI (CSI): 1 channel/UART (UART schannel Simplified SPI (CSI): 1 channel/UART: 1 channel Simplified SPI (CSI): 1 channel/UART: 1 channel Simplified SPI (CSI): 1 channel/UART: 1 channel	nel/simplified I ² C: 1 channel nel/simplified I ² C: 1 channel			
	I ² C bus	1 channel	1 channel			
USB	Function	1 cha	annel			
LCD controlle	er/driver	Internal voltage boosting method, capacitor split are switchable.	Internal voltage boosting method, capacitor split method, and external resistance division method are switchable.			
S	egment signal output	44 (40) Note 1	56 (52) Note 1			
С	ommon signal output	4 (8)	4 (8) Note 1			
Data transfer	r controller (DTC)	32 sources	33 sources			
Event link co	ontroller (ELC)	Event input: 30, Event trigger output: 22	Event input: 31, Event trigger output: 22			
Vectored inte	errupt Internal	36	37			
sources	External	9	9			
Key interrupt	t	8	8			
Reset		Reset by RESET pin Internal reset by watchdog timer Internal reset by power-on-reset Internal reset by voltage detector Internal reset by illegal instruction execution Note that the set by RAM parity error Internal reset by illegal-memory access	ote 2			
Power-on-res	set circuit	 Power-on-reset: 1.51 ± 0.03 V Power-down-reset: 1.50 ± 0.03 V 	• Power-on-reset: 1.51 ± 0.03 V			
Voltage dete	ctor	• Rising edge: 1.67 V to 3.13 V (12 stages) • Falling edge: 1.63 V to 3.06 V (12 stages)				
On-chip deb	ug function	Provided	Provided			
Power supply	y voltage	VDD = 1.6 to 3.6 V (TA = -40 to +85°C) VDD = 2.4 to 3.6 V (TA = -40 to +105°C)	, , , , , , , , , , , , , , , , , , ,			
Operating an	mbient temperature	TA = -40 to +85°C (A: Consumer applications), T	A = -40 to +105°C (G: Industrial applications)			

- **Note 1.** The number in parentheses indicates the number of signal outputs when 8 coms are used.
- Note 2. The illegal instruction is generated when instruction code FFH is executed.

 Reset by the illegal instruction execution not is issued by emulation with the in-circuit emulator or on-chip debug emulator.

[80/85-pin, 100-pin products (without USB)]

(1/2)

		80/85-pin	100-pin			
	Item	R5F111Mx/R5F111Nx (x = E to H, J)	R5F111Px (x = E to H, J)			
Code flash memory	(KB)	64 to 256	64 to 256			
Data flash memory (KB)	8	8			
RAM (KB)		8 to 16 Note 1	8 to 16 Note 1			
Memory space		1 MB				
Main system clock	High-speed system clock	X1 (crystal/ceramic) oscillation, external main sys 1 to 20 MHz: VDD = 2.7 to 3.6 V, 1 to 8 MHz: VD	. , ,			
	High-speed on-chip oscillator clock	HS (high-speed main) operation mode: 1 to 24 MHz (VDD = 2.7 to 3.6 V), HS (high-speed main) operation mode: 1 to 16 MHz (VDD = 2.4 to 3.6 V, LS (low-speed main) operation mode: 1 to 8 MHz (VDD = 1.8 to 3.6 V), LV (low-voltage main) operation mode: 1 to 4 MHz (VDD = 1.6 to 3.6 V)				
Subsystem clock		XT1 (crystal) oscillation, external subsystem clock 32.768 kHz (TYP.): VDD = 1.6 to 3.6 V	r input (EXCLKS)			
Low-speed on-chip of	oscillator clock	15 kHz (TYP.): VDD = 1.6 to 3.6 V				
General-purpose reg	gister	8 bits x 32 registers (8 bits x 8 registers x 4 banks)				
Minimum instruction	execution time	0.04167 μs (High-speed on-chip oscillator clock: fHOCO = fIH = 24 MHz operation)				
		0.05 μs (High-speed system clock: fмx = 20 MHz operation)				
		30.5 μs (Subsystem clock: fsuB = 32.768 kHz ope	eration)			
Instruction set		 Data transfer (8/16 bits) Adder and subtractor/logical operation (8/16 bits) Multiplication (8 bits × 8 bits, 16 bits × 16 bits), Division (16 bits ÷ 16 bits, 32 bits ÷ 32 bits) Multiplication and Accumulation (16 bits × 16 bits + 32 bits) Rotate, barrel shift, and bit manipulation (Set, reset, test, and Boolean operation), etc. 				
I/O port	Total	63	81			
	CMOS I/O	55	73			
	CMOS input	5	5			
	CMOS output	1	1			
	N-ch open-drain I/O (6 V tolerance)	2	2			
Timer	16-bit timer TAU	8 channels (with 1 channel remote control output f	function) (Timer outputs: 8, PWM outputs: 7 Note 2)			
	16-bit timer KB2	3 channels (PWM outputs: 6)				
	Watchdog timer	1 channel				
	12-bit interval timer	1 channel				
	Real-time clock 2	1 channel				
	RTC output	1 1 Hz (subsystem clock: fsub = 32.768 kHz)				

Note 1. In the case of the 16 KB, this is about 15 KB when the self-programming function and data flash function are used (For details, see **CHAPTER 3** in the RL78/L1C User's Manual).

Note 2. The number of outputs varies, depending on the setting of channels in use and the number of the master.

(2/2)

	Item	80/85-pin	100-pin		
	item	R5F111Mx/R5F111Nx (x = E to H, J)	R5F111Px (x = E to H, J)		
Clock output/buzzer	output	2	2		
		2.44 kHz, 4.88 kHz, 9.76 kHz, 1.25 MHz, 2.5 M (Main system clock: fmAIN = 20 MHz operation) 256 Hz, 512 Hz, 1.024 kHz, 2.048 kHz, 4.096 k (Subsystem clock: fsub = 32.768 kHz operation)	:Hz, 8.192 kHz, 16.384 kHz, 32.768 kHz		
8/12-bit resolution A/I	D converter	11 channels	13 channels		
D/A converter		2 channels	2 channels		
Comparator		1 channel	2 channels		
Serial interface		Simplified SPI (CSI): 1 channel/UART (UART supporting LIN-bus): 1 channel/simplified I ² C: 1 channel Simplified SPI (CSI): 1 channel/UART: 1 channel/simplified I ² C: 1 channel Simplified SPI (CSI): 1 channel/UART: 1 channel/simplified I ² C: 1 channel Simplified SPI (CSI): 1 channel/UART: 1 channel/simplified I ² C: 1 channel			
	I ² C bus	1 channel	1 channel		
LCD controller/driver		Internal voltage boosting method, capacitor split method, and external resistance division method are switchable.			
Segment s	signal output	44 (40) Note 1	56 (52) Note 1		
Common	signal output	4 (8) Note 1			
Data transfer controll	er (DTC)	30 sources	31 sources		
Event link controller (ELC)	Event input: 30, Event trigger output: 22	Event input: 31, Event trigger output: 22		
Vectored interrupt	Internal	32	33		
sources	External	9	9		
Key interrupt		8	8		
Reset		Reset by RESET pin Internal reset by watchdog timer Internal reset by power-on-reset Internal reset by voltage detector Internal reset by illegal instruction execution No Internal reset by RAM parity error Internal reset by illegal-memory access	te 2		
Power-on-reset circui	it	 Power-on-reset: 1.51 ± 0.03 V Power-down-reset: 1.50 ± 0.03 V Rising edge: 1.67 V to 3.13 V (12 stages) Falling edge: 1.63 V to 3.06 V (12 stages) 			
Voltage detector					
On-chip debug function	on	Provided			
Power supply voltage	;	VDD = 1.6 to 3.6 V (TA = -40 to +85°C) VDD = 2.4 to 3.6 V (TA = -40 to +105°C)			
Operating ambient te	mperature	TA = -40 to +85°C (A: Consumer applications), Ta	A = -40 to +105°C (G: Industrial applications)		

- **Note 1.** The number in parentheses indicates the number of signal outputs when 8 coms are used.
- Note 2. The illegal instruction is generated when instruction code FFH is executed.

 Reset by the illegal instruction execution not is issued by emulation with the in-circuit emulator or on-chip debug emulator.

2. ELECTRICAL SPECIFICATIONS (TA = -40 to +85°C)

This chapter describes the electrical specifications for the products A: Consumer applications (TA = -40 to +85°C) and G: Industrial applications (when used in the range of TA = -40 to +85°C).

- Caution 1. The RL78 microcontroller has an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.
- Caution 2. The pins mounted depend on the product. Refer to 2.1 Port Function to 2.2.1 With functions for each product in the RL78/L1C User's Manual.

2.1 Absolute Maximum Ratings

Absolute Maximum Ratings (TA = 25°C)

(1/3)

Parameter	Symbols	Conditions	Ratings	Unit
Supply voltage	Vdd		-0.5 to + 6.5	V
	UVBUS		-0.5 to + 6.5	V
	AVDD	AVDD ≤ VDD	-0.5 to + 4.6	V
REGC pin input voltage	VIREGC	REGC	-0.3 to + 2.8	V
			and -0.3 to VDD + 0.3 Note 1	
UREGC pin input voltage	VIUREGC	UREGC	-0.3 to UVBUS + 0.3 Note 2	V
Input voltage	VI1	P00 to P07, P10 to P17, P20 to P27, P30 to P37, P40 to P46, P50 to P57, P70 to P77, P80 to P83, P125 to P127, P137, P140 to P143, EXCLK, EXCLKS, RESET	-0.3 to VDD + 0.3 Note 3	V
	VI2	P60, P61 (N-ch open-drain)	-0.3 to + 6.5	V
	VI3	UDP, UDM	-0.3 to + 6.5	V
	VI4	P150 to P156	-0.3 to AVDD + 0.3 Note 4	V
Output voltage	VO1	P00 to P07, P10 to P17, P20 to P27, P30 to P37, P40 to P46, P50 to P57, P60, P61, P70 to P77, P80 to P83, P125 to P127, P130, P140 to P143	-0.3 to VDD + 0.3 Note 3	V
	VO2	P150 to P156	-0.3 to AVDD + 0.3 Note 3	V
	VO3	UDP, UDM	-0.3 to + 3.8	V
Analog input voltage	VAI1	ANI16 to ANI21	-0.3 to VDD + 0.3 and AVREF(+) + 0.3 Notes 3, 5	V
	VAI2	ANI0 to ANI6	-0.3 to AVDD + 0.3 and AVREF(+) + 0.3 Notes 3, 5	V

- Note 1. Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F). This value regulates the absolute maximum rating of the REGC pin. Do not use this pin with voltage applied to it.
- **Note 2.** Connect the UREGC pin to Vss via a capacitor (0.33 μF). This value regulates the absolute maximum rating of the UREGC pin. Do not use this pin with voltage applied to it.
- Note 3. Must be 6.5 V or lower.
- Note 4. Must be 4.6 V or lower.
- **Note 5.** Do not exceed AVREF(+) + 0.3 V in case of A/D conversion target pin.
- Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter.

 That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.
- Remark 1. Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.
- **Remark 2.** AVREF (+): + side reference voltage of the A/D converter.
- Remark 3. Vss: Reference voltage

Absolute Maximum Ratings (TA = 25°C)

(2/3)

Parameter	Symbols		Conditions	Ratings	Unit
LCD voltage	VLI1	VL1 input voltage N	Note 1	-0.3 to +2.8	V
	VLI2	VL2 input voltage N	2 input voltage Note 1		V
	VLI3	VL3 input voltage N	Note 1	-0.3 to +6.5	V
	VLI4	VL4 input voltage N	Note 1	-0.3 to +6.5	V
	VLI5	CAPL, CAPH inpu	t voltage ^{Note 1}	-0.3 to +6.5	V
	VLO1	V _{L1} output voltage	,	-0.3 to +2.8	V
	VLO2	VL2 output voltage	,	-0.3 to +6.5	V
	VLO3	VL3 output voltage	,	-0.3 to +6.5	V
	VLO4	VL4 output voltage	,	-0.3 to +6.5	V
	VLO5	CAPL, CAPH outp	out voltage	-0.3 to +6.5	V
	VLO6	COM0 to COM7	External resistance division method	-0.3 to VDD + 0.3 Note 2	V
		SEG0 to SEG55 output voltage	Capacitor split method	-0.3 to VDD + 0.3 Note 2	V
		output voltage	Internal voltage boosting method	-0.3 to VLI4 + 0.3 Note 2	V

- Note 1. This value only indicates the absolute maximum ratings when applying voltage to the VL1, VL2, VL3, and VL4 pins; it does not mean that applying voltage to these pins is recommended. When using the internal voltage boosting method or capacitance split method, connect these pins to Vss via a capacitor (0.47 ± 30%) and connect a capacitor (0.47 ± 30%) between the CAPL and CAPH pins.
- Note 2. Must be 6.5 V or lower.

Caution

Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

Absolute Maximum Ratings (TA = 25°C)

(3/3)

Parameter	Symbols		Conditions	Ratings	Unit
Output current, high	ІОН1	Per pin	P00 to P07, P10 to P17, P20 to P27, P30 to P37, P40 to P46, P50 to P57, P70 to P77, P80 to P83, P125 to P127, P130, P140 to P143	-40	mA
		Total of all	P40 to P46	-70	mA
		pins -170 mA	P00 to P07, P10 to P17, P20 to P27, P30 to P37, P50 to P57, P70 to P77, P80 to P83, P125 to P127, P130, P140 to P143	-100	mA
	IOH2	Per pin	P150 to P156	-0.1	mA
		Total of all pins		-0.7	mA
	Іонз	Per pin	UDP, UDM	-3	mA
Output current, low	IOL1	Per pin	P00 to P07, P10 to P17, P20 to P27, P30 to P37, P40 to P46, P50 to P57, P60, P61, P70 to P77, P80 to P83, P125 to P127, P130, P140 to P143	40	mA
		Total of all	P40 to P46	70	mA
		pins 170 mA	P00 to P07, P10 to P17, P20 to P27, P30 to P37, P50 to P57, P70 to P77, P80 to P83, P125 to P127, P130, P140 to P143	100	mA
	IOL2	Per pin	P150 to P156	0.4	mA
		Total of all pins		2.8	mA
	IOL3	Per pin	UDP, UDM	3	mA
Operating ambient temperature	ТА		pperation mode emory programming mode	-40 to +85	°C
Storage temperature	Tstg			-65 to +150	°C

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter.

That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

2.2 Oscillator Characteristics

2.2.1 X1 and XT1 oscillator characteristics

 $(TA = -40 \text{ to } +85^{\circ}C, 1.6 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Resonator	Conditions	MIN.	TYP.	MAX.	Unit
X1 clock oscillation frequency (fx)	Ceramic resonator/crystal resonator	2.7 V ≤ VDD ≤ 3.6 V	1.0		20.0	MHz
Note		2.4 V ≤ VDD < 2.7 V	1.0		16.0	
		1.8 V ≤ VDD < 2.4 V	1.0		8.0	
		1.6 V ≤ VDD < 1.8 V	1.0		4.0	
XT1 clock oscillation frequency (fxT) Note	Crystal resonator		32	32.768	35	kHz

Note Ind

Indicates only permissible oscillator frequency ranges. Refer to **AC Characteristics** for instruction execution time. Request evaluation by the manufacturer of the oscillator circuit mounted on a board to check the oscillator characteristics.

Caution

Since the CPU is started by the high-speed on-chip oscillator clock after a reset release, check the X1 clock oscillation stabilization time using the oscillation stabilization time counter status register (OSTC) by the user. Determine the oscillation stabilization time of the OSTC register and the oscillation stabilization time select register (OSTS) after sufficiently evaluating the oscillation stabilization time with the resonator to be used.

Remark When using the X1 and XT1 oscillator, refer to 5.4 System Clock Oscillator in the RL78/L1C User's Manual.

2.2.2 On-chip oscillator characteristics

 $(TA = -40 \text{ to } +85^{\circ}C, 1.6 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, \text{Vss} = 0 \text{ V})$

Oscillators	Parameters		Conditions	MIN.	TYP.	MAX.	Unit
High-speed on-chip oscillator clock frequency Notes 1, 2	fhoco			1		48	MHz
High-speed on-chip oscillator		-20 to +85°C	1.8 V ≤ VDD ≤ 3.6 V	-1.0		+1.0	%
clock frequency accuracy			1.6 V ≤ VDD ≤ 1.8 V	-5.0		+5.0	%
		-40 to -20°C	1.8 V ≤ VDD < 3.6 V	-1.5		+1.5	%
			1.6 V ≤ VDD ≤ 1.8 V	-5.5		+5.5	%
Low-speed on-chip oscillator clock frequency	fıL				15		kHz
Low-speed on-chip oscillator clock frequency accuracy				-15		+15	%

Note 1. High-speed on-chip oscillator frequency is selected with bits 0 to 4 of the option byte (000C2H) and bits 0 to 2 of the HOCODIV register.

2.2.3 PLL oscillator characteristics

$(TA = -40 \text{ to } +85^{\circ}C, 2.4 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, \text{Vss} = 0 \text{ V})$

Oscillators	Parameters	Conditions	MIN.	TYP.	MAX.	Unit
PLL input frequency Note	fPLLIN	High-speed system clock	6.00		16.00	MHz
PLL output frequency Note	fPLL			48.00		MHz

Note Indicates only oscillator characteristics. Refer to AC Characteristics for instruction execution time.

Note 2. This only indicates the oscillator characteristics. Refer to AC Characteristics for instruction execution time.

2.3 DC Characteristics

2.3.1 Pin characteristics

 $(TA = -40 \text{ to } +85^{\circ}C, 1.6 \text{ V} \le AVDD = VDD \le 3.6 \text{ V}, VSS = 0 \text{ V})$

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, high Note 1	Іон1	Per pin for P00 to P07, P10 to P17, P20 to P27, P30 to P37, P40 to P46, P50 to P57, P70 to P77, P80 to P83, P125 to P127, P130, P140 to P143				-10.0 Note 2	mA
		Total of P00 to P07, P10 to P17, P20 to P27,	2.7 V ≤ VDD ≤ 3.6 V			-15.0	mA
		P30 to P37, P40 to P46, P50 to P57, P70 to P77, P80 to P83, P125 to P127, P130,	1.8 V ≤ VDD < 2.7 V			-7.0	mA
		P140 to P143 (When duty $\leq 70\%$ Note 3)	1.6 V ≤ VDD < 1.8 V			-3.0	mA
	IOH2	Per pin for P150 to P156	1.6 V ≤ VDD ≤ 3.6 V			-0.1 Note 2	mA
		Total of all pins	1.6 V ≤ VDD ≤ 3.6 V			-0.7	mA

- Note 1. Value of current at which the device operation is guaranteed even if the current flows from the VDD pin to an output pin.
- Note 2. However, do not exceed the total current value.
- **Note 3.** Specification under conditions where the duty factor $\leq 70\%$.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

• Total output current of pins = $(IOH \times 0.7)/(n \times 0.01)$

<Example> Where n = 80% and IOH = -10.0 mA

Total output current of pins = $(-10.0 \times 0.7)/(80 \times 0.01) \approx -8.7$ mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

Caution P00 to P02, P10 to P12, P24 to P26, P33 to P35, and P42 to P44 do not output high level in N-ch open-drain mode.

 $(TA = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{AVDD} = \text{VDD} \le 3.6 \text{ V}, \text{VSS} = 0 \text{ V})$

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, low Note 1	IOL1	Per pin for P00 to P07, P10 to P17, P20 to P27, P30 to P37, P40 to P46, P50 to P57, P70 to P77, P80 to P83, P125 to P127, P130, P140 to P143				20.0 Note 2	mA
		Per pin for P60 and P61				15.0 Note 2	mA
		Total of P40 to P46, P130	2.7 V ≤ VDD ≤ 3.6 V			15.0	mA
		(When duty ≤ 70% Note 3)	1.8 V ≤ VDD < 2.7 V			9.0	mA
			1.6 V ≤ VDD < 1.8 V			4.5	mA
		Total of P00 to P07, P10 to P17, P20 to P27,	2.7 V ≤ VDD ≤ 3.6 V			35.0	mA
		P30 to P37, P50 to P57, P60, P61,	1.8 V ≤ VDD < 2.7 V			20.0	mA
		P70 to P77, P80 to P83, P125 to P127, P140 to P143 (When duty ≤ 70% Note 3)	1.6 V ≤ VDD < 1.8 V			10.0	mA
		Total of all pins (When duty ≤ 70% ^{Note 3})				50.0	mA
	IOL2	Per pin for P150 to P156				0.4 Note 2	mA
		Total of all pins	1.6 V ≤ VDD ≤ 3.6 V			2.8	mA

- Note 1. Value of current at which the device operation is guaranteed even if the current flows from an output pin to the Vss pin.
- Note 2. However, do not exceed the total current value.
- **Note 3.** Specification under conditions where the duty factor $\leq 70\%$.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression

(when changing the duty factor from 70% to n%).

- Total output current of pins = (IoL \times 0.7)/(n \times 0.01)
 - <Example> Where n = 80% and IOL = 10.0 mA

Total output current of pins = $(10.0 \times 0.7)/(80 \times 0.01) \approx 8.7 \text{ mA}$

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

(TA = -40 to +85°C, 1.6 V \leq AVDD = VDD \leq 3.6 V, Vss = 0 V)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Input voltage, high	VIH1	P00 to P07, P10 to P17, P20 to P27, P30 to P37, P40 to P46, P50 to P57, P70 to P77, P80 to P83, P125 to P127, P140 to P143	Normal input buffer	0.8 VDD		VDD	V
	VIH2	P00, P01, P10, P11, P24, P25, P33, P34, P43, P44	TTL input buffer 3.3 V ≤ VDD ≤ 3.6 V	2.0		VDD	V
			TTL input buffer 1.6 V ≤ VDD < 3.3 V	1.50		VDD	V
	VIH3	P150 to P156	1	0.7 AVDD		AVDD	V
	VIH4	P60, P61		0.7 VDD		6.0	V
	VIH5	P121 to P124, P137, EXCLK, EXCLKS,	RESET	0.8 VDD		VDD	V
Input voltage, low	VIL1	P00 to P07, P10 to P17, P20 to P27, P30 to P37, P40 to P46, P50 to P57, P70 to P77, P80 to P83, P125 to P127, P140 to P143	Normal input buffer	0		0.2 VDD	V
	VIL2	P00, P01, P10, P11, P24, P25, P33, P34, P43, P44	TTL input buffer 3.3 V ≤ VDD ≤ 3.6 V	0		0.5	V
			TTL input buffer 1.6 V ≤ VDD < 3.3 V	0		0.32	V
	VIL3	P150 to P156		0		0.3 AVDD	V
	VIL4	P60, P61		0		0.3 VDD	V
	VIL5	P121 to P124, P137, EXCLK, EXCLKS,	RESET	0		0.2 VDD	V

Caution The maximum value of VIH of pins P00 to P02, P10 to P12, P24 to P26, P33 to P35, and P42 to P44 is VDD, even in the N-ch open-drain mode.

(TA = -40 to +85°C, 1.6 V \leq AVDD = VDD \leq 3.6 V, Vss = 0 V)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output voltage, high	VOH1	P00 to P07, P10 to P17, P20 to P27, P30 to P37, P40 to P46, P50 to P57, P70 to P77, P80 to P83, P125 to P127, P130, P140 to P143	$2.7 \text{ V} \le \text{VDD} \le 3.6 \text{ V},$ $\text{IOH1} = -2.0 \text{ mA}$ $1.8 \text{ V} \le \text{VDD} \le 3.6 \text{ V},$ $\text{IOH1} = -1.5 \text{ mA}$ $1.6 \text{ V} \le \text{VDD} < 3.6 \text{ V}.$	VDD - 0.6 VDD - 0.5			V
			IOH1 = -1.0 mA				-
	VOH2	P150 to P156	$1.6 \text{ V} \leq \text{VDD} \leq 3.6 \text{ V},$ $10\text{H2} = -100 \mu\text{A}$	AVDD - 0.5			V
Output voltage, low	VOL1	P00 to P07, P10 to P17, P20 to P27, P30 to P37, P40 to P46, P50 to P57,	$2.7 \text{ V} \le \text{VDD} \le 3.6 \text{ V},$ IOL1 = 3.0 mA			0.6	>
		D400 D440 to D440	$2.7 \text{ V} \le \text{VDD} \le 3.6 \text{ V},$ IOL1 = 1.5 mA			0.4	V
			$1.8 \text{ V} \le \text{VDD} \le 3.6 \text{ V},$ IOL1 = 0.6 mA			0.4	V
			1.6 V ≤ VDD < 1.8 V, IOL1 = 0.3 mA			0.4	V
	VOL2	P150 to P156	1.6 V ≤ VDD ≤ 3.6 V, IOL2 = 400 µA			0.4	V
	VOL3	P60, P61	$2.7 \text{ V} \le \text{VDD} \le 3.6 \text{ V},$ IOL3 = 3.0 mA			0.4	V
			1.8 V ≤ VDD ≤ 3.6 V, IOL3 = 2.0 mA			0.4	٧
			1.6 V ≤ VDD ≤ 1.8 V, IOL3 = 1.0 mA			0.4	V

Caution P00 to P02, P10 to P12, P24 to P26, P33 to P35, and P42 to P44 do not output high level in N-ch open-drain mode.

(TA = -40 to +85°C, 1.6 V \leq AVDD = VDD \leq 3.6 V, Vss = 0 V)

Items	Symbol	Conditio	ns		MIN.	TYP.	MAX.	Unit
Input leakage current, high	ILIH1	P00 to P07, P10 to P17, P20 to P27, P30 to P37, P40 to P46, P50 to P57, P60, P61, P70 to P77, P80 to P83, P125 to P127, P137, P140 to P143, RESET	VI = VDD				1	μА
	ILIH2	P20, P21, P140 to P143	VI = VDD				1	μΑ
	ILIH3	P121 to P124 (X1, X2, EXCLK, XT1, XT2, EXCLKS)	VI = VDD	In input port or external clock input			1	μΑ
				In resonator connection			10	μΑ
	ILIH4	P150 to P156	VI = AVDI)			1	μΑ
Input leakage current, low	ILIL1	P00 to P07, P10 to P17, P20 to P27, P30 to P37, P40 to P46, P50 to P57, P60, P61, P70 to P77, P80 to P83, P125 to P127, P137, P140 to P143, RESET	VI = VSS				-1	μА
	ILIL2	P20, P21, P140 to P143	VI = VSS				-1	μΑ
	ILIL3	P121 to P124 (X1, X2, EXCLK, XT1, XT2, EXCLKS)	VI = VSS	In input port or external clock input			-1	μΑ
				In resonator connection			-10	μΑ
	ILIL4	P150 to P156	VI = AVSS	3			-1	μΑ
On-chip pull-up	Ru1	P00 to P07, P10 to P17, P20 to P27,	VI = VSS	2.4 V ≤ VDD ≤ 3.6 V	10	20	100	kΩ
resistance		P30 to P37, P50 to P57, P70 to P77, P140 to P143, P125 to P127		1.6 V ≤ VDD ≤ 2.4 V	10	30	100	
	Ru2	P40 to P46, P80 to P83	VI = VSS		10	20	100	kΩ

2.3.2 Supply current characteristics

 $(TA = -40 \text{ to } +85^{\circ}C, 1.6 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, \text{Vss} = 0 \text{ V})$

(1/2)

Parameter	Symbol			Conditions			MIN.	TYP.	MAX.	Unit		
Supply	IDD1	Operating	HS	fHOCO = 48 MHz Note 3,	Basic	VDD = 3.6 V		2.2	2.8	mA		
urrent Note 1		mode	(high-speed main)	fIH = 24 MHz Note 3	operation	VDD = 3.0 V		2.2	2.8			
			mode Note 5		Normal	VDD = 3.6 V		4.4	8.5			
					operation	VDD = 3.0 V		4.4	8.5			
				fHOCO = 24 MHz Note 3,	Basic	VDD = 3.6 V		2.0	2.6			
				fIH = 24 MHz Note 3	operation	VDD = 3.0 V		2.0	2.6			
					Normal	VDD = 3.6 V		4.2	6.8			
					operation	VDD = 3.0 V		4.2	6.8			
				fHOCO = 16 MHz Note 3,	Normal	VDD = 3.6 V		3.1	4.9			
				fIH = 16 MHz Note 3	operation	VDD = 3.0 V		3.1	4.9			
			LS	fHOCO = 8 MHz Note 3,	Normal	VDD = 3.0 V		1.4	2.2	mA		
		(low-speed main) mode Note 5	fIH = 8 MHz Note 3	operation	VDD = 2.0 V		1.4	2.2				
			LV	fHOCO = 4 MHz Note 3,	Normal	VDD = 3.0 V		1.3	1.8	mA		
					(low-voltage main) mode Note 5	fIH = 4 MHz Note 3	operation	VDD = 2.0 V		1.3	1.8	
			HS	fMX = 20 MHz Note 2,	Normal	Square wave input		3.5	5.5	mA		
		(high-speed main)	VDD = 3.6 V	operation	Resonator connection		3.6	5.7				
		mode Note 5	fMX = 20 MHz Note 2,	Normal	Square wave input		3.5	5.5				
				VDD = 3.0 V	operation	Resonator connection		3.6	5.7			
				fMX = 16 MHz Note 2,	Normal	Square wave input		2.9	4.5			
		VDD = 3.6 V	operation	Resonator connection		3.1	4.6					
				fMX = 16 MHz Note 2,	Normal	Square wave input		2.9	4.5			
				VDD = 3.0 V	operation	Resonator connection		3.1	4.6			
				fMX = 10 MHz Note 2,	Normal	Square wave input		2.1	3.2			
				VDD = 3.6 V	operation	Resonator connection		2.2	3.2			
				fMX = 10 MHz Note 2,	Normal	Square wave input		2.1	3.2			
				VDD = 3.0 V	operation	Resonator connection		2.2	3.2			
			LS	fmx = 8 MHz Note 2,	Normal	Square wave input		1.2	2.0	mA		
			(low-speed main)	VDD = 3.6 V	operation	Resonator connection		1.3	2.0	.0		
			mode Note 5	fmx = 8 MHz Note 2,	Normal	Square wave input		1.2	2.1			
				VDD = 3.0 V	operation	Resonator connection		1.3	2.2			
			HS	fPLL = 48 MHz,	Normal	VDD = 3.6 V		4.7	7.5	mA		
			(High-speed main)	fCLK = 24 MHz Note 2	operation	VDD = 3.0 V		4.7	7.5			
			mode (PLL operation)	fPLL = 48 MHz,	Normal	VDD = 3.6 V		3.1	5.1			
			(FLL operation)	fCLK = 12 MHz Note 2	operation	VDD = 3.0 V		3.1	5.1			
				fPLL = 48 MHz,	Normal	VDD = 3.6 V		2.3	3.9			
				fCLK = 6 MHz Note 2	operation	VDD = 3.0 V		2.3	3.9			
			Subsystem clock	fSUB = 32.768 kHz Note 4	Normal	Square wave input		4.6	6.9	μA		
			operation	TA = -40°C	operation	Resonator connection		4.7	6.9			
				fSUB = 32.768 kHz ^{Note 4}	Normal	Square wave input		4.9	7.0			
			TA = +25°C	operation	Resonator connection		5.0	7.2				
			fsub = 32.768 kHz ^{Note 4}	Normal	Square wave input		5.2	7.6				
			TA = +50°C	operation	Resonator connection		5.2	7.7				
				fsub = 32.768 kHz ^{Note 4}	Normal	Square wave input		5.5	9.3			
				TA = +70°C	operation	Resonator connection		5.6	9.4			
				fsub = 32.768 kHz ^{Note 4}	Normal	Square wave input		6.2	13.3			
			TA = +85°C	operation	Resonator connection		6.2	13.4				

(Notes and Remarks are listed on the next page.)



- Note 1. Total current flowing into VDD, including the input leakage current flowing when the level of the input pin is fixed to VDD, or VSS. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the LCD controller/driver, A/D converter, D/A converter, comparator, LVD circuit, USB 2.0 function module, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
- **Note 2.** When high-speed on-chip oscillator and subsystem clock are stopped.
- **Note 3.** When high-speed system clock and subsystem clock are stopped.
- **Note 4.** When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the real-time clock 2, 12-bit interval timer, and watchdog timer.
- Note 5. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: 2.7 V ≤ VDD ≤ 3.6 V@1 MHz to 24 MHz

 $2.4 \text{ V} \leq \text{VDD} \leq 3.6 \text{ V}@1 \text{ MHz}$ to 16 MHz

LS (low-speed main) mode: 1.8 V \leq VDD \leq 3.6 V@1 MHz to 8 MHz LV (low-voltage main) mode 1.6 V \leq VDD \leq 3.6 V@1 MHz to 4 MHz

- Remark 1. fMX: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
- Remark 2. fHOCO: High-speed on-chip oscillator clock frequency (48 MHz max.)
- Remark 3. fil: Main system clock source frequency when the high-speed on-chip oscillator clock divided 1, 2, 4, or 8, or the PLL

clock divided by 2, 4, or 8 is selected (24 MHz max.)

- Remark 4. fSUB: Subsystem clock frequency (XT1 clock oscillation frequency)
- Remark 5. Except subsystem clock operation, temperature condition of the TYP. value is TA = 25°C

$(TA = -40 \text{ to } +85^{\circ}C, 1.6 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, \text{Vss} = 0 \text{ V})$

(2/2)

	1		00 2 3.0 V, V33 = 0	,		MAINI	TVD	MANY	(2)
Parameter	Symbol	Conditions	LIC (bink and and in)		\/p= 0.0\/	MIN.	TYP.	MAX.	Unit
Supply current	IDD2 Note 2	HALT mode	HS (high-speed main) mode Note 7	fHOCO = 48 MHz Note 4, fIH = 24 MHz Note 4	VDD = 3.6 V		0.77	2.70	mA
lote 1			mode		VDD = 3.0 V		0.77	2.70	1
				fHOCO = 24 MHz Note 4, fIH = 24 MHz Note 4	VDD = 3.6 V		0.55	1.91	
					VDD = 3.0 V		0.55	1.90	
				fHOCO = 16 MHz Note 4, fIH = 16 MHz Note 4	VDD = 3.6 V		0.48	1.41	
					VDD = 3.0 V		0.47	1.41	<u> </u>
			LS (low-speed main) mode Note 7	fHOCO = 8 MHz Note 4,	VDD = 3.0 V		300	770	μΑ
				fIH = 8 MHz Note 4	VDD = 2.0 V		300	770	<u> </u>
			LV (low-voltage main) mode Note 7	fHOCO = 4 MHz Note 4,	VDD = 3.0 V		440	770	μA
				fIH = 4 MHz Note 4	VDD = 2.0 V		440	770	ļ
			HS (high-speed main)	fmx = 20 MHz Note 3,	Square wave input		0.35	1.63	m/
			mode Note 7	VDD = 3.6 V	Resonator connection		0.51	1.68	
				fMX = 20 MHz Note 3,	Square wave input		0.34	1.63	
				VDD = 3.0 V	Resonator connection		0.51	1.68	
				fMX = 16 MHz Note 3,	Square wave input		0.30	1.22	
		VDD = 3.6 V	Resonator connection		0.45	1.39			
		fmx = 16 MHz Note 3,	Square wave input		0.29	1.20			
	_	VDD = 3.0 V	Resonator connection		0.45	1.38			
				fmx = 10 MHz Note 3,	Square wave input		0.23	0.82	
				VDD = 3.6 V	Resonator connection		0.30	0.90	
				fmx = 10 MHz Note 3,	Square wave input		0.22	0.81	
				VDD = 3.0 V	Resonator connection		0.30	0.89	
			LS (low-speed main)	fmx = 8 MHz Note 3,	Square wave input		120	510	μ
		mode Note 7	VDD = 3.0 V	Resonator connection		170	560		
				fmx = 8 MHz Note 3,	Square wave input		130	520	
				VDD = 2.0 V	Resonator connection		170	570	
			HS	fmx = 48 MHz,	VDD = 3.6 V		0.99	2.89	m.
			(High-speed main)	form Od MI I – Note 3	VDD = 3.0 V		0.99	2.88	
			mode	fmx = 48 MHz,	VDD = 3.6 V		0.89	2.48	
			(PLL operation)	fCLK = 12 MHz Note 3	VDD = 3.0 V		0.89	2.47	
				fmx = 48 MHz,	VDD = 3.6 V		0.84	2.27	
				fCLK = 6 MHz Note 3	VDD = 3.0 V		0.84	2.27	
			Subsystem clock	fSUB = 32.768 kHz Note 5	Square wave input		0.32	0.61	μ/
			operation	TA = -40°C	Resonator connection		0.51	0.80	
				fsub = 32.768 kHz Note 5			0.41	0.74	
				TA = +25°C	Resonator connection		0.62	0.91	
				fsub = 32.768 kHz Note 5			0.52	2.30	
				TA = +50°C	Resonator connection		0.75	2.49	
				fSUB = 32.768 kHz Note 5			0.82	4.03	
				TA = +70°C	Resonator connection	-	1.08	4.03	
						 			
			fsub = 32.768 kHz Note 5 TA = +85°C			1.38	8.04		
	CTOD =: '	T. 4000		Resonator connection		1.62	8.23	 	
	IDD3 Note 6	STOP mode Note 8	T _A = -40°C				0.18	0.52	μA
			T _A = +25°C				0.25	0.52	
			Ta = +50°C				0.34	2.21	
			T _A = +70°C				0.64	3.94	
			T _A = +85°C				1.18	7.95	ł

(Notes and Remarks are listed on the next page.)



- Note 1. Total current flowing into VDD, including the input leakage current flowing when the level of the input pin is fixed to VDD or VSS. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the LCD controller/driver, A/D converter, D/A converter, comparator, LVD circuit, USB 2.0 function module, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
- Note 2. During HALT instruction execution by flash memory.
- Note 3. When high-speed on-chip oscillator and subsystem clock are stopped.
- Note 4. When high-speed system clock and subsystem clock are stopped.
- Note 5. When high-speed on-chip oscillator and high-speed system clock are stopped. When RTCLPC = 1 and setting ultra-low current consumption (AMPHS1 = 1). The current flowing into the real-time clock 2 is included. However, not including the current flowing into the 12-bit interval timer and watchdog timer.
- Note 6. Not including the current flowing into the real-time clock 2, 12-bit interval timer, and watchdog timer.
- Note 7. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: 2.7 V ≤ VDD ≤ 3.6 V@1 MHz to 24 MHz

 $2.4 \text{ V} \leq \text{VDD} \leq 3.6 \text{ V}@1 \text{ MHz}$ to 16 MHz

LS (low-speed main) mode: 1.8 V \leq VDD \leq 3.6 V@1 MHz to 8 MHz LV (low-voltage main) mode 1.6 V \leq VDD \leq 3.6 V@1 MHz to 4 MHz

- Note 8. Regarding the value for current to operate the subsystem clock in STOP mode, refer to that in HALT mode.
- Remark 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
- Remark 2. fHoco: High-speed on-chip oscillator clock frequency (48 MHz max.)
- Remark 3. fin: Main system clock source frequency when the high-speed on-chip oscillator clock divided 1, 2, 4, or 8, or the PLL
 - clock divided by 2, 4, or 8 is selected (24 MHz max.)
- Remark 4. fSUB: Subsystem clock frequency (XT1 clock oscillation frequency)
- Remark 5. Except subsystem clock operation, temperature condition of the TYP. value is TA = 25°C

$(TA = -40 \text{ to } +85^{\circ}C, 1.6 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol		Condition	ns		MIN.	TYP.	MAX.	Unit
Low-speed on-chip oscillator operating current	IFIL Note 1						0.20		μA
RTC2 operating current	IRTC Notes 1, 3						0.02		μA
12-bit interval timer operating current	ITMKA Notes 1, 2, 4						0.02		μΑ
Watchdog timer operating current	IWDT Notes 1, 2, 5	fIL = 15 kHz					0.22		μA
A/D converter operating current	IADC Notes 6, 7	AVDD = 3.0 V, whe	n conversion at maximur	n speed			422	720	μA
AVREF (+) current	lavref	AVDD = 3.0 V, ADR	D = 3.0 V, ADREFP1 = 0, ADREFP0 = 0 Note 7				14.0	25.0	μA
	Note 8	AVREFP = 3.0 V, AI	P = 3.0 V, ADREFP1 = 0, ADREFP0 = 1 Note 10				14.0	25.0	
		ADREFP1 = 1, AD	FP1 = 1, ADREFP0 = 0 Note 1				14.0	25.0	
A/D converter reference voltage current	IADREF Notes 1, 9	VDD = 3.0 V					75.0		μA
Temperature sensor operating current	ITMPS Note 1						78		μА
D/A converter operating current	IDAC Notes 1, 11	Per D/A converter	channel				0.53	1.5	mA
Comparator	ІСМР	VDD = 3.6 V,	Window mode				12.5		μA
operating current	Notes 1, 12	Regulator output voltage = 2.1 V	Comparator high-speed	d mode			4.5		μΑ
			Comparator low-speed	mode			1.2		μΑ
		VDD = 3.6 V,	Window mode				7.05		μA
		Regulator output voltage = 1.8 V	Comparator high-speed	d mode			2.2		μA
			Comparator low-speed	mode			0.9		μA
LVD operating current	ILVI Notes 1, 13						0.06		μA
Self-programming operating current	IFSP Notes 1, 14						2.50	12.20	mA
BGO operating current	IBGO Notes 1, 15						1.68	12.20	mA
SNOOZE	ISNOZ Note 1	ADC operation	The mode is performed	Note 16			0.34	1.10	mA
operating current			The A/D conversion op voltage mode, AVREFP		erformed, Low		0.53	2.04	
		Simplified SPI (CS	I)/UART operation				0.70	1.54	mA
LCD operating current	ILCD1 Notes 17, 18	External resistance division method	fLCD = fSUB LCD clock = 128 Hz	1/3 bias 4-time slice	VDD = 3.6 V, LV4 = 3.6 V		0.14		μA
	ILCD2 Note 17	Internal voltage boosting method	fLCD = fSUB LCD clock = 128 Hz	1/3 bias 4-time slice	VDD = 3.0 V, LV4 = 3.0 V (VLCD = 04H)		0.61		μА
	ILCD3 Note 17	Capacitor split method	fLCD = fSUB LCD clock = 128 Hz	1/3 bias 4-time slice	VDD = 3.0 V, LV4 = 3.0 V		0.12		μА
USB current	IUSB Note 20	Operating current	during USB communicati	on			4.88		mA
Note 19	IUSB Note 21	Operating current i	n the USB suspended st	ate			0.04		mA

(Notes and Remarks are listed on the next page.)



- Note 1. Current flowing to VDD.
- Note 2. When high speed on-chip oscillator and high-speed system clock are stopped.
- Note 3. Current flowing only to the real-time clock 2 (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IRTC, when the real-time clock 2 operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, IFIL should be added. IDD2 subsystem clock operation includes the operational current of the real-time clock 2.
- Note 4. Current flowing only to the 12-bit interval timer (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and ITMKA, when the 12-bit interval timer operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, IFIL should be added. IDD2 subsystem clock operation includes the operational current of the 12-bit interval timer.
- Note 5. Current flowing only to the watchdog timer (including the operating current of the low-speed on-chip oscillator). The current value of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and IWDT when the watchdog timer operates in STOP mode
- Note 6. Current flowing only to the A/D converter. The supply current of the RL78 microcontrollers is the sum of IDD1 or IDD2 and IADC, IAVREF, IADREF when the A/D converter operates in an operation mode or the HALT mode.
- **Note 7.** Current flowing to the AVDD.
- **Note 8.** Current flowing from the reference voltage source of A/D converter.
- **Note 9.** Operation current flowing to the internal reference voltage.
- Note 10. Current flowing to the AVREFP.
- **Note 11.** Current flowing only to the D/A converter. The current value of the RL78 microcontrollers is the sum of IDD1 or IDD2 and IDA when the D/A converter operates in an operation mode or the HALT mode.
- **Note 12.** Current flowing only to the comparator circuit. The current value of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and ICMP when the comparator circuit operates in the Operating, HALT or STOP mode.
- Note 13. Current flowing only to the LVD circuit. The current value of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and ILVI when the LVD circuit operates in the Operating, HALT or STOP mode.
- Note 14. Current flowing only during self-programming.
- Note 15. Current flowing only during data flash rewrite.
- Note 16. For shift time to the SNOOZE mode, see 23.3.3 SNOOZE mode in the RL78/L1C User's Manual.
- Note 17. Current flowing only to the LCD controller/driver (VDD pin). The current value of the RL78 microcontrollers is the sum of the LCD operating current (ILCD1, ILCD2 or ILCD3) to the supply current (IDD1, or IDD2) when the LCD controller/driver operates in an operation mode or HALT mode. Not including the current that flows through the LCD panel.
- Note 18. Not including the current that flows through the external divider resistor divider resistor.
- Note 19. Current flowing to the UVBUS.
- **Note 20.** Including the operating current when fPLL = 48 MHz.
- **Note 21.** Including the current supplied from the pull-up resistor of the UDP pin to the pull-down resistor of the host device, in addition to the current consumed by this MCU during the suspended state.
- Remark 1. fil: Low-speed on-chip oscillator clock frequency
- Remark 2. fSUB: Subsystem clock frequency (XT1 clock oscillation frequency)
- Remark 3. fclk: CPU/peripheral hardware clock frequency
- Remark 4. Temperature condition of the TYP. value is TA = 25°C



2.4 AC Characteristics

2.4.1 Basic operation

(TA = -40 to +85°C, 1.6 V \leq AVDD = VDD \leq 3.6 V, Vss = 0 V)

(1/2)

Items	Symbol		Conditions		MIN.	TYP.	MAX.	Unit
Instruction cycle	TCY	Main system	HS (high-speed main)	2.7 V ≤ VDD ≤ 3.6 V	0.0417		1	μs
(minimum instruction		clock (fMAIN)	mode	2.4 V ≤ VDD < 2.7 V	0.0625		1	μs
execution time)		operation	LS (low-speed main) mode	1.8 V ≤ VDD ≤ 3.6 V	0.125		1	μs
			LV (low-voltage main) mode	1.6 V ≤ VDD ≤ 3.6 V	0.25		1	μs
		Subsystem clo	ock (fSUB) operation	1.8 V ≤ VDD ≤ 3.6 V	28.5	30.5	31.3	μs
		In the self-	HS (high-speed main)	2.7 V ≤ VDD ≤ 3.6 V	0.0417		1	μs
		programming	mode	2.4 V ≤ VDD < 2.7 V	0.0625		1	μs
		mode	LS (low-speed main) mode	1.8 V ≤ VDD ≤ 3.6 V	0.125		1	μs
			LV (low-voltage main) mode	1.8 V ≤ VDD ≤ 3.6 V	0.25		1	μs
External main system	fEX	2.7 V ≤ VDD ≤	3.6 V		1.0		20.0	MHz
clock frequency		2.4 V ≤ VDD <	2.7 V		1.0		16.0	MHz
		1.8 V ≤ VDD <	2.4 V		1.0		8.0	MHz
		1.6 V ≤ VDD <	1.8 V		1.0		4.0	MHz
	fEXT				32		35	kHz
External main system	texH,	2.7 V ≤ VDD ≤	3.6 V		24			ns
clock input high-level	tEXL	2.4 V ≤ VDD <	2.7 V		30			ns
width, low-level width		1.8 V ≤ VDD <	2.4 V		60			ns
		1.6 V ≤ VDD <	1.8 V		120			ns
	tEXHS,				13.7			μs
TI00 to TI07 input high-level width, low-level width	ttih, ttil				1/fмск + 10			ns

Remark fMCK: Timer array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of timer mode register mn (TMRmn). m: Unit number (m = 0),

n: Channel number (n = 0 to 7))

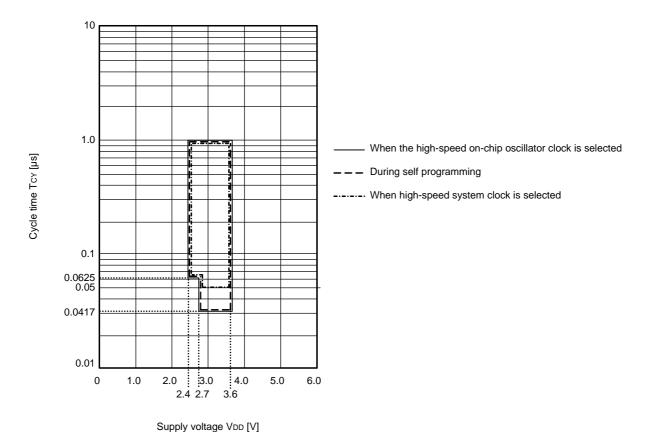
(TA = -40 to +85°C, 1.6 V \leq AVDD = VDD \leq 3.6 V, Vss = 0 V)

(2/2)

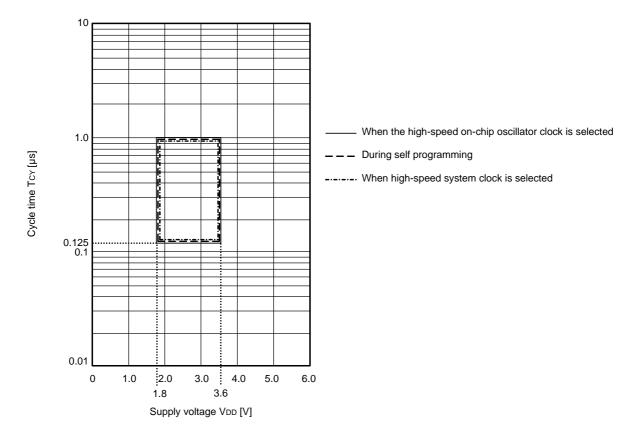
Items	Symbol	Condition	ns	MIN.	TYP.	MAX.	Unit
TO00 to TO07, TKBO00,	fTO	HS (high-speed main) mode	2.7 V ≤ VDD ≤ 3.6 V			8	MHz
TKBO01, TKBO10, TKBO11,			2.4 V ≤ VDD < 2.7 V			8	MHz
TKBO20, TKBO21 output frequency		LS (low-speed main) mode	1.8 V ≤ VDD ≤ 3.6 V			4	MHz
output nequency		LV (low-voltage main) mode	1.6 V ≤ VDD ≤ 3.6 V			2	MHz
PCLBUZ0, PCLBUZ1 output	fPCL	HS (high-speed main) mode	2.7 V ≤ VDD ≤ 3.6 V			8	MHz
frequency			2.4 V ≤ VDD < 2.7 V			8	MHz
		LS (low-speed main) mode	1.8 V ≤ VDD ≤ 3.6 V			4	MHz
		LV (low-voltage main) mode	1.8 V ≤ VDD ≤ 3.6 V			2	MHz
Interrupt input high-level width, low-level width	tinth, tintl	INTP0 to INTP7	1.6 V ≤ VDD ≤ 3.6 V	1			μs
Key interrupt input low-level	tkr	1.8 V ≤ VDD ≤ 3.6 V		250			ns
width		1.6 V ≤ VDD < 1.8 V		1			μs
TMKB2 forced output stop input	tihr	INTP0 to INTP7	fclk > 16 MHz	125			ns
high-level width			fc∟K ≤ 16 MHz	2			fclk
RESET low-level width	trsl			10			μs

Minimum Instruction Execution Time during Main System Clock Operation

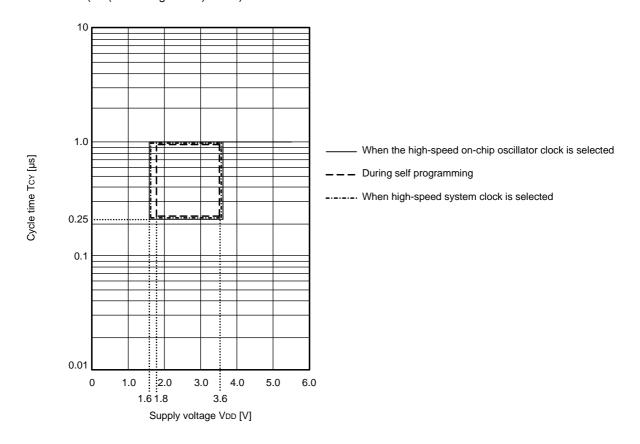
TCY vs VDD (HS (high-speed main) mode)



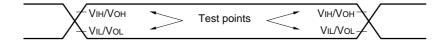
TCY vs VDD (LS (low-speed main) mode)



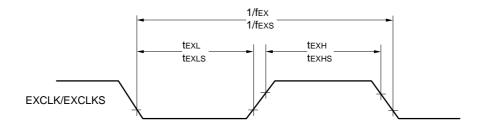
TCY vs VDD (LV (low-voltage main) mode)



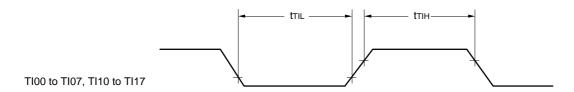
AC Timing Test Points

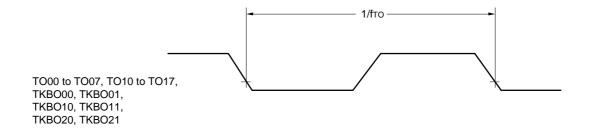


External System Clock Timing

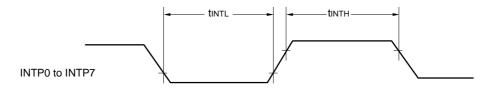


TI/TO Timing

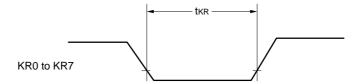




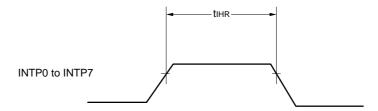
Interrupt Request Input Timing



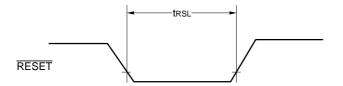
Key Interrupt Input Timing



Timer KB2 Input Timing

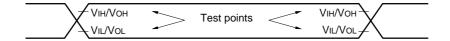


RESET Input Timing



2.5 Peripheral Functions Characteristics

AC Timing Test Points



2.5.1 Serial array unit

(1) During communication at same potential (UART mode)

 $(TA = -40 \text{ to } +85^{\circ}C, 1.6 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	` `	h-speed main) Mode	`	r-speed main) Mode	LV (low-vol	Unit	
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer		2.7 V ≤ VDD ≤ 3.6 V		fMCK/6 Note 2		fmck/6		fмск/6	bps
rate Note 1		Theoretical value of the maximum transfer rate fMCK = fCLK Note 3		4.0		1.3		0.6	Mbps
		2.4 V ≤ VDD ≤ 3.6 V		fMCK/6 Note 2		fMCK/6		fMCK/6	bps
		Theoretical value of the maximum transfer rate fMCK = fCLK Note 3		2.6		1.3		0.6	Mbps
		1.8 V ≤ VDD ≤ 3.6 V		<u> </u>		fMCK/6 Note 2		fmck/6	bps
		Theoretical value of the maximum transfer rate fMCK = fCLK Note 3		_		1.3		0.6	Mbps
		1.6 V ≤ VDD ≤ 3.6 V		_		_		fмск/6	bps
		Theoretical value of the maximum transfer rate fMCK = fCLK Note 3		_		_		0.6	Mbps

Note 1. Transfer rate in the SNOOZE mode is 4800 bps only.

Note 2. The following conditions are required for low voltage interface.

 $2.4 \text{ V} \le \text{VDD} < 2.7 \text{ V}$: MAX. 2.6 Mbps $1.8 \text{ V} \le \text{VDD} < 2.4 \text{ V}$: MAX. 1.3 Mbps

1.6 V ≤ VDD < 1.8 V: MAX. 0.6 Mbps

Note 3. The maximum operating frequencies of the CPU/peripheral hardware clock (fclk) are:

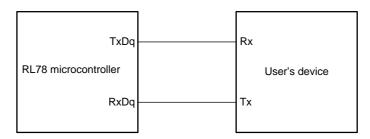
HS (high-speed main) mode: 24 MHz (2.7 V ≤ VDD ≤ 3.6 V)

16 MHz (2.4 V ≤ VDD ≤ 3.6 V)

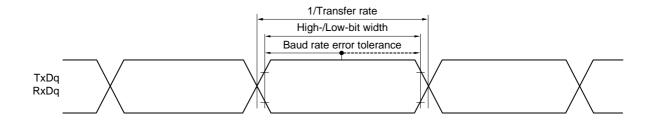
LS (low-speed main) mode: 8 MHz (1.8 V \leq VDD \leq 3.6 V) LV (low-voltage main) mode: 4 MHz (1.6 V \leq VDD \leq 3.6 V)

Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

UART mode connection diagram (during communication at same potential)



UART mode bit width (during communication at same potential) (reference)



Remark 1. q: UART number (q = 0 to 3), g: PIM and POM number (g = 0 to 3)

Remark 2. fMCK: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00 to 03, 10 to 13))

(2) During communication at same potential (Simplified SPI (CSI) mode) (master mode, SCKp... internal clock output, corresponding CSI00 only)

 $(TA = -40 \text{ to } +85^{\circ}C, 2.7 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tKCY1	tkcy1 ≥ fclk/2	2.7 V ≤ V _{DD} ≤ 3.6 V	167		250		500		ns
SCKp high-/ low-level width	tKL1	2.7 V ≤ V _{DD} ≤ 3	3.6 V	tKCY1/2 - 10		tKCY1/2 - 50		tKCY1/2 - 50		ns
SIp setup time (to SCKp↑) Note 1	tsik1	2.7 V ≤ V _{DD} ≤ 3	3.6 V	33		110		110		ns
SIp hold time (from SCKp↑) Note 2	tKSI1	2.7 V ≤ V _{DD} ≤ 3	3.6 V	10		10		10		ns
Delay time from SCKp↓ to SOp output Note 3	tKSO1	C = 20 pF Note 4	ı		10		10		10	ns

- Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 4. C is the load capacitance of the SCKp and SOp output lines.
- Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).
- Remark 1. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM number (g = 2)
- Remark 2. fMCK: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00))

(3) During communication at same potential (Simplified SPI (CSI) mode) (master mode, SCKp... internal clock output)

 $(TA = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Sym	C	onditions	HS (high-spee Mode	,	LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
	DOI			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tKCY1	tkCY1 ≥ fCLK/4	2.7 V ≤ VDD ≤ 3.6 V	167		500		1000		ns
			2.4 V ≤ VDD ≤ 3.6 V	250		500		1000		ns
			1.8 V ≤ VDD ≤ 3.6 V	_		500		1000		ns
			1.6 V ≤ VDD ≤ 3.6 V	_		_		1000		ns
SCKp high-/	tKH1,	2.7 V ≤ VDD ≤ 3	3.6 V	tKCY1/2 - 18		tKCY1/2 - 50		tKCY1/2 - 50		ns
low-level width	tKL1	2.4 V ≤ VDD ≤ 3.6 V		tKCY1/2 - 38		tKCY1/2 - 50		tKCY1/2 - 50		ns
		1.8 V ≤ VDD ≤ 3	3.6 V	_		tKCY1/2 - 50		tKCY1/2 - 50		ns
		1.6 V ≤ VDD ≤ 3	3.6 V	_		_		tKCY1/2 - 100		ns
SIp setup time	tSIK1	2.7 V ≤ VDD ≤ 3	3.6 V	44		110		110		ns
(to SCKp↑) Note 1		2.4 V ≤ VDD ≤ 3	3.6 V	75		110		110		ns
		1.8 V ≤ VDD ≤ 3	3.6 V	_		110		110		ns
		1.6 V ≤ VDD ≤ 3	3.6 V	_		_		220		ns
SIp hold time	tKSI1	2.4 V ≤ VDD ≤ 3	3.6 V	19		19		19		ns
(from SCKp↑) Note 2		1.8 V ≤ VDD ≤ 3	3.6 V	_		19		19		ns
		1.6 V ≤ VDD ≤ 3	3.6 V	_		_		19		ns
Delay time from	tKSO1	C = 30 pF	2.7 V ≤ VDD ≤ 3.6 V		25		50		50	ns
SCKp↓ to SOp output Note 3		Note 4	2.4 V ≤ VDD ≤ 3.6 V		25		50		50	ns
Note 3			1.8 V ≤ VDD ≤ 3.6 V		_		50		50	ns
			1.6 V ≤ VDD ≤ 3.6 V		_		_		50	ns

- Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp†" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 4. C is the load capacitance of the SCKp and SOp output lines.
- Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).
- **Remark 1.** p: CSI number (p = 00, 10, 20, 30), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM number (g = 0 to 3)
- Remark 2. fmck: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))

(4) During communication at same potential (Simplified SPI (CSI) mode) (slave mode, SCKp... external clock input)

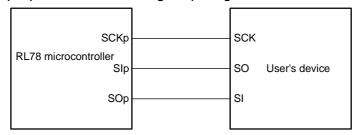
$(TA = -40 \text{ to } +85^{\circ}C, 1.6 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Cond	litions	HS (high- main) M	•	LS (low-spee	,	LV (low-voltage Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle	tKCY2	2.7 V ≤ VDD < 3.6 V	fMCK > 16 MHz	8/fmck		_		_		ns
time Note 5			fMCK ≤ 16 MHz	6/fmck		6/fmck		6/fmck		ns
		2.4 V ≤ VDD < 3.6 V		6/fмск and 500		6/fмск and 500		6/fмск and 500		ns
		1.8 V ≤ VDD < 3.6 V		_		6/fмск and 750		6/fмск and 750		ns
		1.6 V ≤ VDD < 3.6 V		_		_		6/fмск and 1500		ns
SCKp high-/	tKH2, tKL2	2.7 V ≤ VDD ≤ 3.6 V		tKCY2/2 - 8		tKCY2/2 - 8		tKCY2/2 - 8		ns
low-level width		1.8 V ≤ VDD ≤ 3.6 V		_		tKCY2/2 - 18		tKCY2/2 - 18		ns
		1.6 V ≤ VDD ≤ 3.6 V		_		_		tKCY1/2 - 66		ns
SIp setup time	tSIK2	2.7 V ≤ VDD ≤ 3.6 V		1/fмск + 20		1/fmck + 30		1/fmck + 30		ns
(to SCKp↑) Note 1		2.4 V ≤ VDD ≤ 3.6 V		1/fmck + 30		1/fmck + 30		1/fmck + 30		ns
11010 1		1.8 V ≤ VDD < 3.6 V		_		1/fmck + 30		1/fmck + 30		ns
		1.6 V ≤ VDD < 3.6 V		_		_		1/fmck + 40		ns
SIp hold time	tKSI2	2.4 V ≤ VDD < 3.6 V		1/fмск + 31		1/fMCK + 31		1/fMCK + 31		ns
(from SCKp↑) Note 2		1.8 V ≤ VDD < 3.6 V		_		1/fmck + 31		1/fmck + 31		ns
		1.6 V ≤ VDD < 3.6 V		_		_		1/fmck + 250		ns
Delay time from SCKp↓ to	tKSO2	C = 30 pF Note 4	2.7 V ≤ VDD ≤ 3.6 V		2/fMCK + 44		2/fмск + 110		2/fMCK + 110	ns
SOp output Note 3			2.4 V ≤ VDD < 3.6 V		2/fMCK + 75		2/fмск + 110		2/fмcк + 110	ns
			1.8 V ≤ VDD < 3.6 V		_		2/fмск + 110		2/fмcк + 110	ns
			1.6 V ≤ VDD < 3.6 V		_		_		2/fмск + 220	ns

- Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp1" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 4. C is the load capacitance of the SOp output lines.
- Note 5. The maximum transfer rate when using the SNOOZE mode is 1 Mbps.
- Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).
- **Remark 1.** p: CSI number (p = 00, 10, 20, 30), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM number (g = 0 to 3)
- Remark 2. fMCK: Serial array unit operation clock frequency
 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,
 n: Channel number (mn = 00 to 03, 10 to 13))



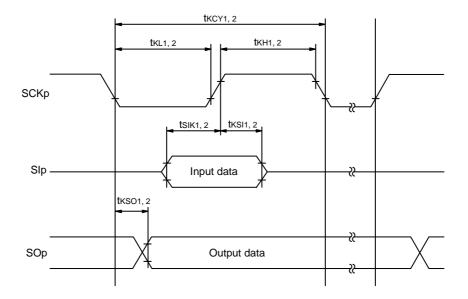
Simplified SPI (CSI) mode connection diagram (during communication at same potential)



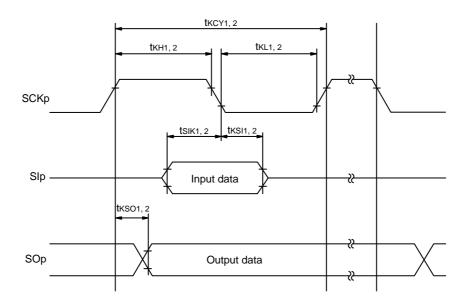
Remark 1. p: CSI number (p = 00, 10, 20, 30)

Remark 2. m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13)

Simplified SPI (CSI) mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



Simplified SPI (CSI) mode serial transfer timing (during communication at same potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remark 1. p: CSI number (p = 00, 10, 20, 30)

Remark 2. m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13)

(5) During communication at same potential (simplified I²C mode)

$(TA = -40 \text{ to } +85^{\circ}C, 1.6 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	HS (high-spec		LS (low-spee Mode		LV (low-voltag	-	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLr clock frequency	fscL	$2.7 \text{ V} \le \text{VDD} \le 3.6 \text{ V},$ Cb = 50 pF, Rb = 2.7 k Ω		1000 Note 1		400 Note 1		400 Note 1	kHz
		1.8 V ≤ VDD ≤ 3.6 V, Cb = 100 pF, Rb = 3 kΩ		400 Note 1		400 Note 1		400 Note 1	kHz
		1.8 V ≤ VDD < 2.7 V, Cb = 100 pF, Rb = 5 kΩ		300 Note 1		300 Note 1		300 Note 1	kHz
		1.6 V \leq VDD $<$ 1.8 V, Cb = 100 pF, Rb = 5 kΩ		_				250	kHz
Hold time when SCLr = "L"	tLOW	$2.7 \text{ V} \le \text{VDD} \le 3.6 \text{ V},$ Cb = 50 pF, Rb = 2.7 kΩ	475		1150		1150		ns
		1.8 V ≤ VDD ≤ 3.6 V, Cb = 100 pF, Rb = 3 kΩ	1150		1150		1150		ns
		1.8 V ≤ VDD < 2.7 V, Cb = 100 pF, Rb = 5 kΩ	1550		1550		1550		ns
		1.6 V ≤ VDD < 1.8 V, Cb = 100 pF, Rb = 5 kΩ	_		_		1850		ns
Hold time when SCLr = "H"	tHIGH	$2.7 \text{ V} \le \text{VDD} \le 3.6 \text{ V},$ Cb = 50 pF, Rb = 2.7 kΩ	475		1150		1150		ns
		1.8 V ≤ VDD ≤ 3.6 V, Cb = 100 pF, Rb = 3 kΩ	1150		1150		1150		ns
		1.8 V ≤ VDD < 2.7 V, Cb = 100 pF, Rb = 5 kΩ	1550		1550		1550		ns
		1.6 V ≤ VDD < 1.8 V, Cb = 100 pF, Rb = 5 kΩ	_		_		1850		ns
Data setup time (reception)	tsu: DAT	$2.7 \text{ V} \le \text{VDD} \le 3.6 \text{ V},$ Cb = 50 pF, Rb = 2.7 kΩ	1/fMCK + 85 Note 2		1/fMCK + 145 Note 2		1/fMCK + 145 Note 2		ns
		1.8 V ≤ VDD ≤ 3.6 V, Cb = 100 pF, Rb = 3 kΩ	1/fMCK + 145 Note 2		1/fMCK + 145 Note 2		1/fMCK + 145 Note 2		ns
		1.8 V ≤ VDD < 2.7 V, Cb = 100 pF, Rb = 5 kΩ	1/fMCK + 230 Note 2		1/fMCK + 230 Note 2		1/fMCK + 230 Note 2		ns
		1.6 V ≤ VDD < 1.8 V, Cb = 100 pF, Rb = 5 kΩ	_		_		1/fMCK + 290 Note 2		ns
Data hold time (transmission)	thd: dat	2.7 V \leq VDD \leq 3.6 V, Cb = 50 pF, Rb = 2.7 kΩ	0	305	0	305	0	305	ns
		1.8 V ≤ VDD ≤ 3.6 V, Cb = 100 pF, Rb = 3 kΩ	0	355	0	355	0	355	ns
		1.8 V ≤ VDD < 2.7 V, Cb = 100 pF, Rb = 5 kΩ	0	405	0	405	0	405	ns
		1.6 V ≤ VDD < 1.8 V, Cb = 100 pF, Rb = 5 kΩ	_		_		0	405	ns

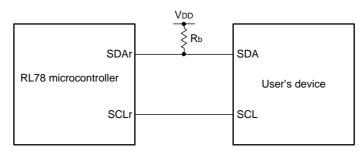
Note 1. The value must be equal to or less than fMCK/4.

Note 2. Set the fMCK value to keep the hold time of SCLr = "L" and SCLr = "H".

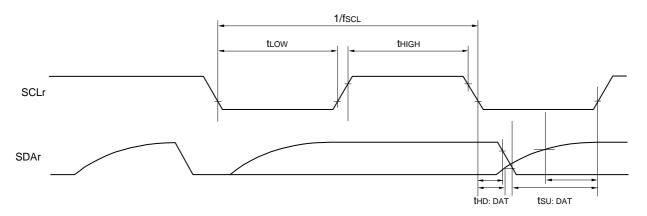
Caution Select the normal input buffer and the N-ch open drain output (VDD tolerance) mode for the SDAr pin and the normal output mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register h (POMh).



Simplified I²C mode connection diagram (during communication at same potential)



Simplified I²C mode serial transfer timing (during communication at same potential)



Remark 1. $Rb[\Omega]$: Communication line (SDAr) pull-up resistance, Cb[F]: Communication line (SDAr, SCLr) load capacitance

Remark 2. r: IIC number (r = 00, 10, 20, 30), g: PIM number (g = 0 to 3), h: POM number (h = 0 to 3)

Remark 3. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0, 1),

n: Channel number (n = 0 to 3), mn = 00 to 03, 10 to 13)

(6) Communication at different potential (1.8 V, 2.5 V) (UART mode)

$(TA = -40 \text{ to } +85^{\circ}C, 1.8 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, \text{Vss} = 0 \text{ V})$

(1/2)

Parameter	Parameter Symbol		Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low	Unit	
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate Notes 1, 2		reception	2.7 V ≤ VDD ≤ 3.6 V, 2.3 V ≤ Vb ≤ 2.7 V		fMCK/6 Note 1		fMCK/6 Note 1		fMCK/6 Note 1	bps
			Theoretical value of the maximum transfer rate fMCK = fCLK Note 4		4.0		1.3		0.6	Mbps
			1.8 V ≤ VDD < 3.3 V, 1.6 V ≤ Vb ≤ 2.0 V		fMCK/6 Notes 1, 2, 3		fMCK/6 Notes 1, 2, 3		fMCK/6 Notes 1, 2, 3	bps
			Theoretical value of the maximum transfer rate fMCK = fCLK Note 4		4.0		1.3		0.6	Mbps

- Note 1. Transfer rate in the SNOOZE mode is 4,800 bps only.
- **Note 2.** Use it with $VDD \ge Vb$.
- **Note 3.** The following conditions are required for low voltage interface.

 $2.4 \text{ V} \le \text{VDD} < 2.7 \text{ V}:$ MAX. 2.6 Mbps $1.8 \text{ V} \le \text{VDD} < 2.4 \text{ V}:$ MAX. 1.3 Mbps $1.6 \text{ V} \le \text{VDD} < 1.8 \text{ V}:$ MAX. 0.6 Mbps

Note 4. The maximum operating frequencies of the CPU/peripheral hardware clock (fclk) are:

HS (high-speed main) mode: $24 \text{ MHz} (2.7 \text{ V} \leq \text{VDD} \leq 3.6 \text{ V})$

16 MHz (2.4 V \leq VDD \leq 3.6 V)

LS (low-speed main) mode: 8 MHz (1.8 V \leq VDD \leq 3.6 V) LV (low-voltage main) mode: 4 MHz (1.6 V \leq VDD \leq 3.6 V)

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

- Remark 1. Vb[V]: Communication line voltage
- Remark 2. q: UART number (q = 0 to 3), g: PIM and POM number (g = 0 to 3)
- Remark 3. fMCK: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00 to 03, 10 to 13))

(6) Communication at different potential (1.8 V, 2.5V) (UART mode)

$(TA = -40 \text{ to } +85^{\circ}C, 1.8 \le VDD \le 3.6 \text{ V}, VSS = 0 \text{ V})$

(2/2)

Parameter	Symbol		Conditions	` `	HS (high-speed main) Mode		LS (low-speed main) Mode		voltage main) Mode	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate Note 2		transmission	2.7 V ≤ V _{DD} ≤ 3.6 V, 2.3 V ≤ V _b ≤ 2.7 V		Note 1		Note 1		Note 1	bps
			Theoretical value of the maximum transfer rate $C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega, \\ V_b = 2.3 \text{ V}$		1.2 Note 2		1.2 Note 2		1.2 Note 2	Mbps
			1.8 V ≤ V _{DD} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V		Notes 3, 4		Notes 3, 4		Notes 3, 4	bps
			Theoretical value of the maximum transfer rate $Cb=50 \ pF, \ Rb=5.5 \ k\Omega,$ $Vb=1.6 \ V$		0.43 Note 5		0.43 Note 5		0.43 Note 5	Mbps

Note 1. The smaller maximum transfer rate derived by using fMCK/6 or the following expression is the valid maximum transfer rate. Expression for calculating the transfer rate when $2.7 \text{ V} \le \text{VDD} < 3.6 \text{ V}$ and $2.3 \text{ V} \le \text{Vb} \le 2.7 \text{ V}$

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{2.0}{V_b})\} \times 3}$$
 [bps]

Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.0}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}}$$

- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- **Note 2.** This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 1 above to calculate the maximum transfer rate under conditions of the customer.
- **Note 3.** Use it with $VDD \ge Vb$.
- Note 4. The smaller maximum transfer rate derived by using fMCK/6 or the following expression is the valid maximum transfer rate. Expression for calculating the transfer rate when 1.8 V \leq VDD < 3.3 V and 1.6 V \leq Vb \leq 2.0 V

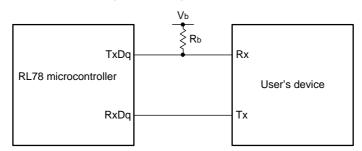
Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{1.5}{V_b})\} \times 3}$$
 [bps]

Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln (1 - \frac{1.5}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}}$$

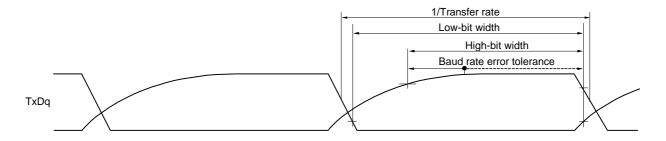
- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- **Note 5.** This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 4 above to calculate the maximum transfer rate under conditions of the customer.
- Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

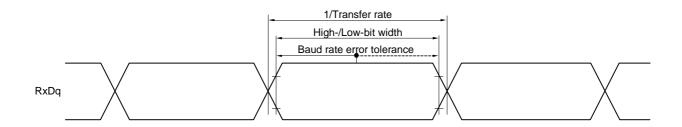


UART mode connection diagram (during communication at different potential)



UART mode bit width (during communication at different potential) (reference)





- Remark 1. $Rb[\Omega]$: Communication line (TxDq) pull-up resistance, Cb[F]: Communication line (TxDq) load capacitance, Vb[V]: Communication line voltage
- Remark 2. q: UART number (q = 0 to 3), g: PIM and POM number (g = 0 to 3)
- Remark 3. fmck: Serial array unit operation clock frequency
 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,
 n: Channel number (mn = 00 to 03, 10 to 13))

(7) Communication at different potential (2.5 V) (Simplified SPI (CSI) mode) (master mode, SCKp... internal clock output, corresponding CSI00 only)

 $(TA = -40 \text{ to } +85^{\circ}C, 2.7 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol		Conditions	HS (high-spee Mode	d main)	LS (low-speed Mode	d main)	LV (low-voltage Mode	e main)	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tKCY1	tkCY1 ≥ fCLK/2	$2.7V \le VDD < 3.6 V$, $2.3 V \le Vb \le 2.7 V$, $Cb = 20 pF$, $Rb = 2.7 k\Omega$	300		1150		1150		ns
SCKp high-level width	tKH1	2.7 V ≤ VDD < 2.3 V ≤ Vb ≤ 2 Cb = 20 pF, Rb	2.7 V,	tkCY1/2 - 120		tkCY1/2 - 120		tKCY1/2 - 120		ns
SCKp low-level width	tKL1	$2.7 \text{ V} \le \text{VDD} <$ $2.3 \text{ V} \le \text{Vb} \le 2$ Cb = 20 pF, Rb	2.7 V,	tKCY1/2 - 10		tKCY1/2 - 50		tKCY1/2 - 50		ns
SIp setup time (to SCKp↑) Note 1	tSIK1	2.7 V ≤ VDD < 2.3 V ≤ Vb ≤ 2 Cb = 20 pF, Rb	2.7 V,	121		479		479		ns
SIp hold time (from SCKp↑) Note 1	tKSI1	2.7 V ≤ VDD < 2.3 V ≤ Vb ≤ 2 Cb = 20 pF, Rb	2.7 V,	10		10		10		ns
Delay time from SCKp↓ to SOp output Note 1	tKSO1	$2.7 \text{ V} \le \text{VDD} <$ $2.3 \text{ V} \le \text{Vb} \le 2$ Cb = 20 pF, Rb	2.7 V,		130		130		130	ns
SIp setup time (to SCKp↓) Note 2	tsiK1	2.7 V ≤ VDD < 2.3 V ≤ Vb ≤ 2. Cb = 20 pF, Rb	7 V,	33		110		110		ns
SIp hold time (from SCKp↓) Note 2	tKSI1	2.7 V ≤ VDD < 2.3 V ≤ Vb ≤ 2. Cb = 20 pF, Rb	7 V,	10		10		10		ns
Delay time from SCKp↑ to SOp output Note 2	tKSO1	2.7 V ≤ VDD < 2.3 V ≤ Vb ≤ 2. Cb = 20 pF, Rb	7 V,		10		10		10	ns

Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

Note 2. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

Remark 1. $Rb[\Omega]$: Communication line (SCKp, SOp) pull-up resistance, Cb[F]: Communication line (SCKp, SOp) load capacitance, Vb[V]: Communication line voltage

Remark 2. p: CSI number (p = 00), m: Unit number (m = 0),

n: Channel number (n = 0), g: PIM and POM number (g = 2)

Remark 3. fmck: Serial array unit operation clock frequency

 $(Operation \ clock \ to \ be \ set \ by \ the \ CKSmn \ bit \ of \ serial \ mode \ register \ mn \ (SMRmn). \ m: \ Unit \ number,$

n: Channel number (mn = 00))

(8) Communication at different potential (1.8 V, 2.5 V) (Simplified SPI (CSI) mode) (master mode, SCKp... internal clock output)

 $(TA = -40 \text{ to } +85^{\circ}C, 1.8 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, \text{Vss} = 0 \text{ V})$

(1/2)

Parameter	Symbol	bol Conditions			HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode	
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tKCY1	tKCY1 ≥ fCLK/4	$2.7V \le VDD < 3.6 \text{ V}, 2.3 \text{ V} \le Vb \le 2.7 \text{ V},$ Cb = 30 pF, Rb = 2.7 k Ω	500 Note		1150		1150		ns
			$1.8 \text{ V} \le \text{VDD} < 3.3 \text{ V}, 1.6 \text{ V} \le \text{Vb} \le 1.8 \text{ V},$ $Cb = 30 \text{ pF}, Rb = 5.5 \text{ k}Ω$	1150 Note		1150		1150		ns
SCKp high- level width	tKH1	2.7 V ≤ V _{DD} ≤ C _b = 30 pF, R _b	$3.6 \text{ V}, 2.3 \text{ V} \le \text{Vb} \le 2.7 \text{ V},$ $p = 2.7 \text{ k}Ω$	tKCY1/2 - 170		tKCY1/2 - 170		tKCY1/2 - 170		ns
		1.8 V ≤ VDD < Cb = 30 pF, Rb	3.3 V, 1.6 V ≤ V _b ≤ 2.0 V, 0.5 = 5.5 kΩ	tKCY1/2 - 458		tKCY1/2 - 458		tKCY1/2 - 458		ns
SCKp low- level width	tKL1	2.7 V ≤ V _{DD} ≤ C _b = 30 pF, R _b	$63.6 \text{ V}, 2.3 \text{ V} \leq \text{Vb} \leq 2.7 \text{ V},$ $60 = 2.7 \text{ k}\Omega$	tKCY1/2 - 18		tKCY1/2 - 50		tKCY1/2 - 50		ns
		1.8 V ≤ V _{DD} < C _b = 30 pF, R _b	3.3 V, 1.6 V ≤ V _b ≤ 2.0 V, $0 = 5.5 \text{ k}\Omega$	tKCY1/2 - 50		tKCY1/2 - 50		tKCY1/2 - 50		ns

Note Use it with $VDD \ge Vb$.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the page after the next page.)

(8) Communication at different potential (1.8 V, 2.5 V) (Simplified SPI (CSI) mode) (master mode, SCKp... internal clock output)

 $(TA = -40 \text{ to } +85^{\circ}C, 1.8 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, \text{Vss} = 0 \text{ V})$

(2/2)

Parameter	Symbol	Conditions	, , ,	h-speed Mode	LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SIp setup time (to SCKp↑) Note 1	tSIK1	$2.7 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, 2.3 \text{ V} \le \text{Vb} \le 2.7 \text{ V},$ $\text{Cb} = 30 \text{ pF}, \text{Rb} = 2.7 \text{ k}\Omega$	177		479		479		ns
		1.8 V \leq VDD $<$ 3.3 V, 1.6 V \leq Vb \leq 2.0 V Note 3, Cb = 30 pF, Rb = 5.5 kΩ	479		479		479		ns
SIp hold time (from SCKp↑) Note 1	tKSI1	$2.7 \text{ V} \le \text{V}_{DD} \le 3.6 \text{ V}, 2.3 \text{ V} \le \text{V}_{b} \le 2.7 \text{ V},$ $C_{b} = 30 \text{ pF}, R_{b} = 2.7 \text{ k}\Omega$	19		19		19		ns
		1.8 V \leq VDD $<$ 3.3 V, 1.6 V \leq Vb \leq 2.0 V Note 3, Cb = 30 pF, Rb = 5.5 kΩ	19		19		19		ns
Delay time from SCKp↓ to SOp	tKSO1	$2.7 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, 2.3 \text{ V} \le \text{Vb} \le 2.7 \text{ V},$ Cb = 30 pF, Rb = 2.7 k Ω		195		195		195	ns
output Note 1		1.8 V \leq VDD $<$ 3.3 V, 1.6 V \leq Vb \leq 2.0 V Note 3, Cb = 30 pF, Rb = 5.5 kΩ		483		483		483	ns
SIp setup time (to SCKp↓) Note 2	tSIK1	$2.7 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, 2.3 \text{ V} \le \text{Vb} \le 2.7 \text{ V},$ $\text{Cb} = 30 \text{ pF}, \text{Rb} = 2.7 \text{ k}\Omega$	44		110		110		ns
		1.8 V \leq VDD $<$ 3.3 V, 1.6 V \leq Vb \leq 2.0 V Note 3, Cb = 30 pF, Rb = 5.5 kΩ	110		110		110		ns
SIp hold time (from SCKp↓) Note 2	tKSI1	$2.7 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, 2.3 \text{ V} \le \text{Vb} \le 2.7 \text{ V},$ $\text{Cb} = 30 \text{ pF}, \text{Rb} = 2.7 \text{ k}\Omega$	19		19		19		ns
		1.8 V \leq VDD $<$ 3.3 V, 1.6 V \leq Vb \leq 2.0 V Note 3, Cb = 30 pF, Rb = 5.5 kΩ	19		19		19		ns
Delay time from SCKp↑ to SOp	tKSO1	$2.7 \text{ V} \le \text{V}_{DD} \le 3.6 \text{ V}, 2.3 \text{ V} \le \text{V}_{b} \le 2.7 \text{ V},$ $C_{b} = 30 \text{ pF}, R_{b} = 2.7 \text{ k}\Omega$		25		25		25	ns
output Note 2		1.8 V \leq VDD $<$ 3.3 V, 1.6 V \leq Vb \leq 2.0 V Note 3, Cb = 30 pF, Rb = 5.5 kΩ		25		25		25	ns

Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

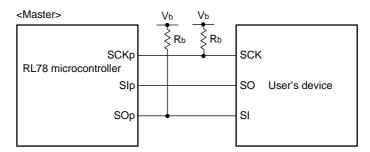
Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the next page.)

Note 2. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 3. Use it with $VDD \ge Vb$.

Simplified SPI (CSI) mode connection diagram (during communication at different potential)

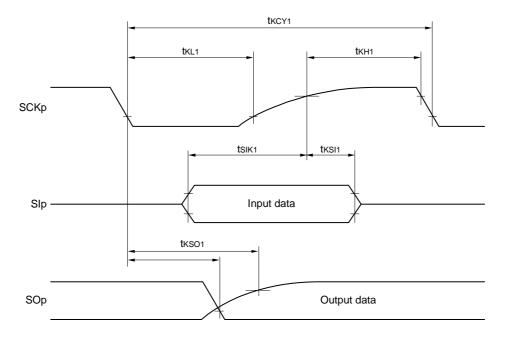


- Remark 1. $Rb[\Omega]$: Communication line (SCKp, SOp) pull-up resistance, Cb[F]: Communication line (SCKp, SOp) load capacitance, Vb[V]: Communication line voltage
- **Remark 2.** p: CSI number (p = 00, 10, 20, 30), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM and POM number (g = 0 to 3)
- Remark 3. fMCK: Serial array unit operation clock frequency

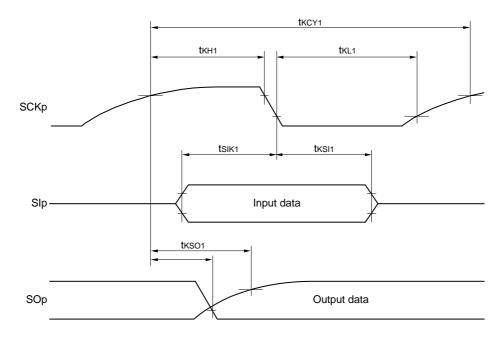
 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

 n: Channel number (mn = 00))

Simplified SPI (CSI) mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



Simplified SPI (CSI) mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remark p: CSI number (p = 00, 10, 20, 30), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM and POM number (g = 0 to 3)

(9) Communication at different potential (1.8 V, 2.5 V) (Simplified SPI (CSI) mode) (slave mode, SCKp... external clock input)

 $(TA = -40 \text{ to } +85^{\circ}C, 1.8 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, \text{Vss} = 0 \text{ V})$

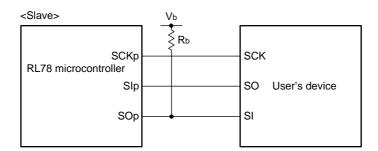
Parameter	Symbol	Con	ditions	HS (high main)		LS (low main)		LV (low- main)	•	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle	tKCY2	2.7 V ≤ VDD ≤ 3.6 V,	20 MHz < fMCK ≤ 24 MHz	16/fмск		_		_		ns
time Note 1		2.3 V ≤ Vb ≤ 2.7 V	16 MHz < fMCK ≤ 20 MHz	14/fmck		_		_		ns
			8 MHz < fMCK ≤ 16 MHz	12/fмск		_		_		ns
			4 MHz < fMCK ≤ 8 MHz	8/fмск		16/fмск		_		ns
			fMCK ≤ 4 MHz	6/fмск		10/fмск		10/fмск		ns
		1.8 V ≤ VDD < 3.3 V,	20 MHz < fMCK ≤ 24 MHz	36/fмск		_		_		ns
		1.6 V ≤ Vb ≤ 2.0 V Note 2	16 MHz < fмcк ≤ 20 MHz	32/fMCK		_		_		ns
			8 MHz < fMCK ≤ 16 MHz	26/fmck		_		_		ns
			4 MHz < fMCK ≤ 8 MHz	16/fmck		16/fмск		_		ns
			fMCK ≤ 4 MHz	10/fmck		10/fmck		10/fмск		ns
SCKp high-/ low-level width	tKH2, tKL2	2.7 V ≤ VDD ≤ 3.6 V, 2.3 \	/ ≤ V _b ≤ 2.7 V	tKCY2/2 - 18		tKCY2/2 - 50		tKCY2/2 - 50		ns
		1.8 V ≤ VDD < 3.3 V, 1.6 V	/ ≤ Vb ≤ 2.0 V Note 2	tKCY2/2 - 50		tKCY2/2 - 50		tKCY2/2 - 50		ns
SIp setup time (to SCKp↑)	tSIK2	2.7 V ≤ VDD ≤ 3.6 V		1/fмск + 20		1/fMCK + 30		1/fмск + 30		ns
Note 3		1.8 V ≤ VDD < 3.3 V		1/fмск + 30		1/fмск + 30		1/fмск + 30		ns
SIp hold time (from SCKp†) Note 4	tKSI2					1/fMCK + 31		1/fMCK + 31		ns
Delay time from SCKp↓ to SOp	tKSO2	$2.7 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, 2.3 \text{ V}$ Cb = 30 pF, Rb = 2.7 k Ω	/ ≤ V _b ≤ 2.7 V		2/fмск + 214		2/fмск + 573		2/fмск + 573	ns
output Note 5	output Note 5 $1.8 \text{ V} \leq \text{VDD} < 3.3 \text{ V}, 1.6 \text{ N}$ $C_b = 30 \text{ pF}, \text{ Rb} = 5.5 \text{ k}\Omega$		/ ≤ V _b ≤ 2.0 V Note 2		2/fмск + 573	_	2/fмск + 573	_	2/fмск + 573	ns

- Note 1. Transfer rate in the SNOOZE mode: MAX. 1 Mbps
- **Note 2.** Use it with $VDD \ge Vb$.
- Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 4. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 5. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Caution Select the TTL input buffer for the SIp pin and SCKp pin and the N-ch open drain output (VDD tolerance) mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

($\ensuremath{\textit{Remarks}}$ are listed on the next page.)

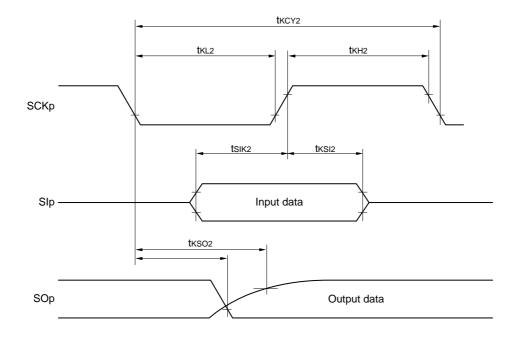


Simplified SPI (CSI) mode connection diagram (during communication at different potential)

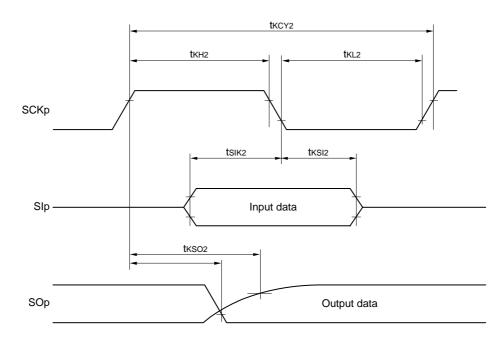


- Remark 1. $Rb[\Omega]$: Communication line (SOp) pull-up resistance, Cb[F]: Communication line (SOp) load capacitance, Vb[V]: Communication line voltage
- **Remark 2.** p: CSI number (p = 00, 10, 20, 30), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM and POM number (g = 0 to 3)
- Remark 3. fMCK: Serial array unit operation clock frequency
 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,
 n: Channel number (mn = 00, 02, 10, 12))

Simplified SPI (CSI) mode serial transfer timing (slave mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



Simplified SPI (CSI) mode serial transfer timing (slave mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remark p: CSI number (p = 00, 10, 20, 30), m: Unit number (m = 0, 1),

n: Channel number (n = 0 to 3), g: PIM and POM number (g = 0 to 3)

(10) Communication at different potential (1.8 V, 2.5 V) (simplified I^2C mode)

 $(TA = -40 \text{ to } +85^{\circ}C, 1.8 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	HS (high-s Mo	oeed main) ode	, ,	peed main) ode	,	ltage main) ode	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX. 300 Note 1 300 Note 1 300 Note 1	
SCLr clock frequency	fscl	$2.7 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, 2.3 \text{ V} \le \text{Vb} < 2.7 \text{ V},$ $\text{Cb} = 50 \text{ pF}, \text{Rb} = 2.7 \text{ k}\Omega$		1000 Note 1		300 Note 1		300 Note 1	kHz
		$2.7 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, 2.3 \text{ V} \le \text{Vb} < 2.7 \text{ V},$ Cb = 100 pF, Rb = 2.7 k Ω		400 Note 1		300 Note 1		300 Note 1	kHz
		$1.8 \text{ V} \leq \text{VDD} < 3.3 \text{ V}, 1.6 \text{ V} \leq \text{Vb} \leq 2.0 \text{ V} \text{ Note 2}, \\ \text{Cb} = 100 \text{ pF}, \text{Rb} = 5.5 \text{ k}\Omega$		400 Note 1		300 Note 1		300 Note 1	kHz
Hold time when SCLr	tLOW	$2.7 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, 2.3 \text{ V} \le \text{Vb} < 2.7 \text{ V},$ $\text{Cb} = 50 \text{ pF}, \text{Rb} = 2.7 \text{ k}\Omega$	475		1550		1550		ns
= "L"		$2.7 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, 2.3 \text{ V} \le \text{Vb} < 2.7 \text{ V},$ $\text{Cb} = 100 \text{ pF}, \text{Rb} = 2.7 \text{ k}\Omega$	1150		1550		1550		ns
		$1.8 \text{ V} \le \text{VDD} < 3.3 \text{ V}, 1.6 \text{ V} \le \text{Vb} \le 2.0 \text{ V}$ Note 2, Cb = 100 pF, Rb = 5.5 kΩ	1550		1550		1550		ns
Hold time when SCLr	tHIGH	$2.7 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, 2.3 \text{ V} \le \text{Vb} < 2.7 \text{ V},$ $\text{Cb} = 50 \text{ pF}, \text{Rb} = 2.7 \text{ k}\Omega$	200		610		610		ns
= "H"		$2.7 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, 2.3 \text{ V} \le \text{Vb} < 2.7 \text{ V},$ $\text{Cb} = 100 \text{ pF}, \text{Rb} = 2.7 \text{ k}\Omega$	600		610		610		ns
		$1.8 \text{ V} \le \text{VDD} < 3.3 \text{ V}, 1.6 \text{ V} \le \text{Vb} \le 2.0 \text{ V}$ Note 2, Cb = 100 pF, Rb = 5.5 kΩ	610		610		610		ns
Data setup time	tsu:dat	$2.7 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, 2.3 \text{ V} \le \text{Vb} < 2.7 \text{ V},$ Cb = 50 pF, Rb = 2.7 k Ω	1/fMCK + 135 Note 3		1/fMCK + 190 Note 3		1/fMCK + 190 Note 3		ns
(reception)		$2.7 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, 2.3 \text{ V} \le \text{Vb} < 2.7 \text{ V},$ Cb = 100 pF, Rb = 2.7 k Ω	1/fMCK + 190 Note 3		1/fMCK + 190 Note 3		1/fMCK + 190 Note 3		ns
		1.8 V \leq VDD $<$ 3.3 V, 1.6 V \leq Vb \leq 2.0 V Note 2, Cb = 100 pF, Rb = 5.5 kΩ	1/fMCK + 190 Note 3		1/fMCK + 190 Note 3		1/fMCK + 190 Note 3		ns
Data hold time	tHD:DAT	$2.7 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, 2.3 \text{ V} \le \text{Vb} < 2.7 \text{ V},$ $\text{Cb} = 50 \text{ pF}, \text{Rb} = 2.7 \text{ k}\Omega$	0	305	0	305	0	305	ns
(transmission)		$2.7 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, 2.3 \text{ V} \le \text{Vb} < 2.7 \text{ V},$ $Cb = 100 \text{ pF}, Rb = 2.7 \text{ k}\Omega$	0	355	0	355	0	355	ns
		$1.8 \text{ V} \leq \text{VDD} < 3.3 \text{ V}, 1.6 \text{ V} \leq \text{Vb} \leq 2.0 \text{ V} \text{ Note 2}, \\ \text{Cb} = 100 \text{ pF}, \text{Rb} = 5.5 \text{ k}\Omega$	0	405	0	405	0	405	ns

Note 1. The value must be equal to or less than fMCK/4.

Note 2. Use it with $VDD \ge Vb$.

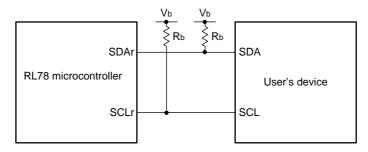
Note 3. Set the fMCK value to keep the hold time of SCLr = "L" and SCLr = "H".

Caution Select the TTL input buffer and the N-ch open drain output (VDD tolerance) mode for the SDAr pin and the N-ch open drain output (VDD tolerance) mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

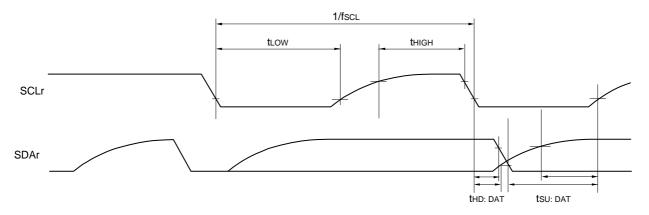
(Remarks are listed on the next page.)



Simplified I²C mode connection diagram (during communication at different potential)



Simplified I²C mode serial transfer timing (during communication at different potential)



Remark 1. Rb[Ω]: Communication line (SDAr, SCLr) pull-up resistance, Cb[F]: Communication line (SDAr, SCLr) load capacitance, Vb[V]: Communication line voltage

Remark 2. r: IIC number (r = 00, 10, 20, 30), g: PIM, POM number (g = 0 to 3)

Remark 3. fmck: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0, 1), n: Channel number (n = 0, 2), mn = 00, 02, 10, 12)

2.5.2 Serial interface IICA

(1) I²C standard mode

 $(TA = -40 \text{ to } +85^{\circ}C, 1.6 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Co	nditions	, ,	peed main) ode	, ,	peed main) ode		ltage main) ode	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLA0 clock	fSCL	Standard mode:	2.7 V ≤ VDD ≤ 3.6 V	0	100	0	100	0	100	kHz
frequency		fCLK ≥ 1 MHz	1.8 V ≤ VDD ≤ 3.6 V	_	_	0	100	0	100	kHz
			1.6 V ≤ VDD ≤ 3.6 V	_	_	_	_	0	100	kHz
Setup time of	tsu: sta	2.7 V ≤ VDD ≤ 3.6	V	4.7		4.7		4.7		μs
restart condition		1.8 V ≤ VDD ≤ 3.6	V	_	_	4.7		4.7		μs
		1.6 V ≤ VDD ≤ 3.6	V	_	_	-	_	4.7		μs
Hold time Note 1	thd: STA	2.7 V ≤ VDD ≤ 3.6	V	4.0		4.0		4.0		μs
		1.8 V ≤ VDD ≤ 3.6	V	_	_	4.0		4.0		μs
		1.6 V ≤ VDD ≤ 3.6	V	-	_	-	_	4.0		μs
Hold time when	tLOW	2.7 V ≤ VDD ≤ 3.6	V	4.7		4.7		4.7		μs
SCLA0 = "L"		1.8 V ≤ VDD ≤ 3.6	V	-	_	4.7		4.7		μs
		1.6 V ≤ VDD ≤ 3.6	V	-	_	-	_	4.7		μs
Hold time when	tHIGH	2.7 V ≤ VDD ≤ 3.6	V	4.0		4.0		4.0		μs
SCLA0 = "H"		1.8 V ≤ VDD ≤ 3.6	V	-	_	4.0		4.0		μs
		1.6 V ≤ VDD ≤ 3.6	V	-	_	-	_	4.0		μs
Data setup time	tsu: dat	2.7 V ≤ VDD ≤ 3.6	V	250		250		250		ns
(reception)		1.8 V ≤ VDD ≤ 3.6	V	-	_	250		250		ns
		1.6 V ≤ VDD ≤ 3.6	V	-	_	-	_	250		ns
Data hold time	thd: dat	2.7 V ≤ VDD ≤ 3.6	V	0	3.45	0	3.45	0	3.45	μs
(transmission) Note 2		1.8 V ≤ VDD ≤ 3.6	V	_	_	0	3.45	0	3.45	μs
11010 2		1.6 V ≤ VDD ≤ 3.6	V	_	_	_	_	0	3.45	μs
Setup time of stop	tsu: sto	2.7 V ≤ VDD ≤ 3.6	V	4.0		4.0		4.0		μs
condition		1.8 V ≤ VDD ≤ 3.6	V	_	_	4.0		4.0		μs
		1.6 V ≤ VDD ≤ 3.6	V	-	_	-	.	4.0		μs
Bus-free time	tBUF	2.7 V ≤ VDD ≤ 3.6	V	4.7		4.7		4.7		μs
		1.8 V ≤ VDD ≤ 3.6	V	-	_	4.7		4.7		μs
		1.6 V ≤ VDD ≤ 3.6	V	-	_	-	-	4.7		μs

Note 1. The first clock pulse is generated after this period when the start/restart condition is detected.

Note 2. The maximum value (MAX.) of thd:Dat is during normal transfer and a clock stretch state is inserted in the ACK (acknowledge) timing.

Remark The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

Standard mode: $C_b = 400 \text{ pF}$, $R_b = 2.7 \text{ k}\Omega$

(2) I2C fast mode

(TA = -40 to +85°C, 1.8 V \leq VDD \leq 3.6 V, Vss = 0 V)

Parameter	Symbol	Conditions		, ,	peed main) ode	٠.	peed main) ode	`	ltage main) ode	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLA0 clock	fSCL	Fast mode:	2.7 V ≤ VDD ≤ 3.6 V	0	400	0	400	0	400	kHz
frequency		fclk ≥ 3.5 MHz	1.8 V ≤ VDD ≤ 3.6 V	0	400	0	400	0	400	kHz
Setup time of restart	tsu: sta	2.7 V ≤ VDD ≤ 3.	6 V	0.6		0.6		0.6		μs
condition		1.8 V ≤ VDD ≤ 3.	6 V	0.6		0.6		0.6		μs
Hold time Note 1	tHD: STA	2.7 V ≤ VDD ≤ 3.	6 V	0.6		0.6		0.6		μs
		1.8 V ≤ VDD ≤ 3.	6 V	0.6		0.6		0.6		μs
Hold time when	tLOW	2.7 V ≤ VDD ≤ 3.	2.7 V ≤ VDD ≤ 3.6 V			1.3		1.3		μs
SCLA0 = "L"		1.8 V ≤ VDD ≤ 3.	6 V	1.3		1.3		1.3		μs
Hold time when	tHIGH	2.7 V ≤ VDD ≤ 3.	6 V	0.6		0.6		0.6		μs
SCLA0 = "H"		1.8 V ≤ VDD ≤ 3.	6 V	0.6		0.6		0.6		μs
Data setup time	tsu: DAT	2.7 V ≤ VDD ≤ 3.	6 V	100		100		100		ns
(reception)		1.8 V ≤ VDD ≤ 3.	6 V	100		100		100		ns
Data hold time	thd: dat	2.7 V ≤ VDD ≤ 3.	6 V	0	0.9	0	0.9	0	0.9	μs
(transmission) Note 2		1.8 V ≤ VDD ≤ 3.	6 V	0	0.9	0	0.9	0	0.9	μs
Setup time of stop	tsu: sto	2.7 V ≤ VDD ≤ 3.	6 V	0.6		0.6		0.6		μs
condition		1.8 V ≤ VDD ≤ 3.6 V		0.6		0.6		0.6		μs
Bus-free time	tBUF	2.7 V ≤ VDD ≤ 3.	6 V	1.3		1.3		1.3		μs
		1.8 V ≤ VDD ≤ 3.	6 V	1.3		1.3		1.3		μs

Note 1. The first clock pulse is generated after this period when the start/restart condition is detected.

Note 2. The maximum value (MAX.) of thd: DAT is during normal transfer and a clock stretch state is inserted in the ACK (acknowledge) timing.

Remark

The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

Fast mode: Cb = 320 pF, $Rb = 1.1 \text{ k}\Omega$

(3) I²C fast mode plus

$(TA = -40 \text{ to } +85^{\circ}C, 2.7 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, \text{Vss} = 0 \text{ V})$

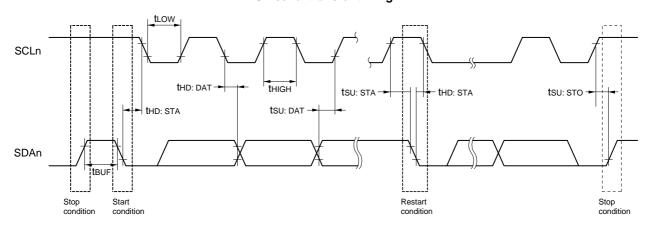
Parameter	Symbol	Cor	nditions	HS (high-sp Mo	,	LS (low-sp Mo	,	LV (low-vol Mo	,	Unit		
				MIN.	MAX.	MIN. MAX.		MIN.	MAX.			
SCLA0 clock frequency	fscl	Fast mode plus: fcLK ≥ 10 MHz	LK ≥ 10 MHz		1000	_		_		kHz		
Setup time of restart condition	tsu: sta	2.7 V ≤ VDD ≤ 3.6	V ≤ VDD ≤ 3.6 V			_		-	_	μs		
Hold time Note 1	thd: STA	2.7 V ≤ VDD ≤ 3.6	V ≤ VDD ≤ 3.6 V			_		_		μs		
Hold time when SCLA0 = "L"	tLOW	2.7 V ≤ VDD ≤ 3.6	7 V ≤ VDD ≤ 3.6 V			-	_	-	_	μs		
Hold time when SCLA0 = "H"	tHIGH	2.7 V ≤ VDD ≤ 3.6	S V	0.26		_	=	_	_	μs		
Data setup time (reception)	tsu: dat	2.7 V ≤ VDD ≤ 3.6	S V	50		_		_	_	ns		
Data hold time (transmission) Note 2	thd: dat	2.7 V ≤ VDD ≤ 3.6	7 V ≤ VDD ≤ 3.6 V		2.7 V ≤ VDD ≤ 3.6 V		0.45	_		-	_	μs
Setup time of stop condition	tsu: sto	2.7 V ≤ VDD ≤ 3.6	7 V ≤ VDD ≤ 3.6 V			_		_	_	μs		
Bus-free time	tBUF	2.7 V ≤ VDD ≤ 3.6	7 V ≤ VDD ≤ 3.6 V			_	-	_	_	μs		

- Note 1. The first clock pulse is generated after this period when the start/restart condition is detected.
- **Note 2.** The maximum value (MAX.) of thd: DAT is during normal transfer and a clock stretch state is inserted in the ACK (acknowledge) timing.

Remark The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

Fast mode plus: Cb = 120 pF, Rb = 1.1 k Ω

IICA serial transfer timing



2.5.3 USB

(1) Electrical specifications

(TA = -40 to +85°C, 2.4 V \leq VDD \leq 3.6 V, VSS = 0 V, HS (High-speed main) mode only)

	Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
UREGC	UREGC output voltage characteristic	UREGC	UVBUS = 4.0 to 5.5 V, PXXCON = VDDUSBE = 1	3.0	3.3	3.6	V
UVBUS	UVBUS input voltage characteristic	UVBUS	Function	4.35 (4.02 ^{Note})	5.00	5.25	V

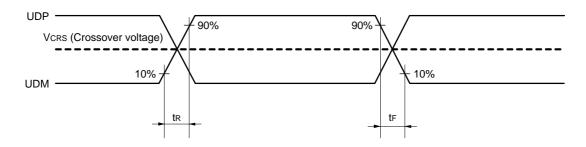
Note Value of instantaneous voltage

(TA = -40 to +85°C, 4.35 V \leq UVBUS \leq 5.25 V, 2.4 V \leq VDD \leq 3.6 V, VSS = 0 V, HS (High-speed main) mode only)

	Parameter		Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Input	Input voltag	ge	VIH		2.0			V
Input characteristic (FS/LS receiver) Output characteristic (FS driver) Output characteristic (FS driver) Output Characteristic (FS driver) Output Characteristic (LS driver) Transi time Match Crosse Output Characteristic (LS driver) Transi time Match Note Crosse			VIL				0.8	V
`	Difference sensitivity	input	VDI	UDP voltage - UDM voltage	0.2	2.5 3.6 0.3 20 20 111.1 2.0 44 3.6 0.3 300 300 125 2.0 24.80 1.575 3.09	V	
	Difference mode rang		Vсм		0.8		2.5	V
1	Output volt	age	Vон	IOH = -200 μA	2.8	0 0.8 2 0.8 3 2.5 3 3.6 0.3 20 20 20 111.1 3 2.0 3 44 3 3.6 0.3 6 300 6 300 6 300 6 125 3 2.0 2 24.80 9 1.575 2 5 3.09	3.6	V
			VoL	IOL = 2 mA	0	0.8 2 3 3.6 3.6 0.3 20 20 20 111.1 3 2.0 3 44 3 3.6 0.3 300 5 300 6 300 6 25 24.80 9 1.575 25 3.09	V	
(FS driver)	Transition	Rising	tFR	Rising: From 10% to 90% of amplitude,	4		20	ns
	time	Falling	tFF	Falling: From 90% to 10% of amplitude,	4		20	ns
	Matching (TFR/TFF)	VFRFM	CL = 50 pF	90		111.1	%
	Crossover	voltage	VFCRS		1.3		2.0	V
	Output Imp	edance	ZDRV		28		44	Ω
Output Output voltage VOH	Vон		2.8		3.6	V		
			VoL		0		0.3	V
(LS driver)	Transition	Rising	tLR	Rising: From 10% to 90% of amplitude,	75		300	ns
	time	Falling	tLF	Falling: From 90% to 10% of amplitude,	75		300	ns
	Matching (TFR/TFF)	VLTFM	CL = 250 pF to 750 pF The UDP and UDM pins are individually pulled	80		125	%
	Crossover	voltage Note	VLCRS	down via 15 k Ω	1.3		2.0	V
Pull-up,	Pull-down	resistor	RPD		14.25		24.80	kΩ
Pull-down	Pull-up	Idle	Rpui		0.9		1.575	kΩ
	resistor	Reception	RPUA		1.425		3.09	kΩ
UVBUS	UVBUS pull resistor	-down	Rvbus	UVBUS voltage = 5.5 V		1000		kΩ
	UVBUS inpu	ut voltage	VIH		3.20	20 20 111.1 2.0 44 3.6 0.3 300 300 125 2.0 24.80 1.575 3.09	V	
			VIL				0.8	V

Note Excludes the first signal transition from the idle state.

Timing of UDP and UDM



(2) BC standard

(TA = -40 to +85°C, 4.35 V \leq UVBUS \leq 5.25 V, 2.4 V \leq VDD \leq 3.6 V, VSS = 0 V, HS (High-speed main) mode only)

	Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
USB	UDP sink current	IDP_SINK		25	100	175	μA
standard	UDM sink current	IDM_SINK		25	100	175	μΑ
BC1.2	DCD source current	IDP_SRC		7	10	13	μΑ
	Data detection voltage	VDAT_REF		0.25	0.325	0.4	V
	UDP source voltage	VDP_SRC	Output current 250 µA	0.5	0.6	0.7	V
	UDM source voltage	VDM_SRC	Output current 250 µA	0.5	0.6	0.7	V

(3) BC option standard

(TA = -40 to +85°C, 4.35 V \leq UVBUS \leq 5.25 V, 2.4 V \leq VDD \leq 3.6 V, Vss = 0 V, HS (High-speed main) mode only)

Para	meter		Symbol	Conditions	MIN.	TYP.	MAX.	Unit
UDP/UDM input reference	VDSELi [3: 0]	0000	VDDET0		27	32	37	%UVBUS
voltage	(i = 0, 1)	0001	VDDET1		29	34	39	%UVBUS
(UVBUS divider ratio)		0010	VDDET2		32	37	42	%UVBUS
(Function)		0011	VDDET3		35	40	45	%UVBUS
		0100	VDDET4		38	43	48	%UVBUS
		0101	VDDET5		41	46	51	%UVBUS
		0110	VDDET6		44	49	54	%UVBUS
		0111	VDDET7		47	52	57	%UVBUS
		1000	VDDET8		51	56	61	%UVBUS
		1001	VDDET9		55	60	65	%UVBUS
		1010	VDDET10		59	64	69	%UVBUS
		1011	VDDET11		63	68	73	%UVBUS
		1100	VDDET12		67	72	73	%UVBUS
		1101	VDDET13		71	76	81	%UVBUS
		1110	VDDET14		75	80	85	%UVBUS
		1111	VDDET15		79	84	89	%UVBUS

2.6 Analog Characteristics

2.6.1 A/D converter characteristics

Classification of A/D converter characteristics

Reference Voltage Input Channel	Reference voltage (+) = AVREFP Reference voltage (-) = AVREFM	Reference voltage (+) = AVDD Reference voltage (-) = AVSS	Reference voltage (+) = Internal reference voltage Reference voltage (-) = AVss
High-accuracy channel; ANI0 to ANI6 (input buffer power supply: AVDD)	Refer to 2.6.1 (1) . Refer to 2.6.1 (2) .	Refer to 2.6.1 (3) .	Refer to 2.6.1 (6) .
Standard channel; ANI16 to ANI21 (input buffer power supply: VDD)	Refer to 2.6.1 (4) .	Refer to 2.6.1 (5) .	
Internal reference voltage, Temperature sensor output voltage	Refer to 2.6.1 (4) .	Refer to 2.6.1 (5) .	_

(1) When reference voltage (+) = AVREFP/ANIO (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target for conversion: ANI2 to ANI6

 $(TA = -40 \text{ to } +85^{\circ}\text{C}, 2.4 \text{ V} \le \text{AVREFP} \le \text{AVDD} = \text{VDD} \le 3.6 \text{ V}, \text{Vss} = 0 \text{ V}, \text{AVss} = 0 \text{ V}, \text{reference voltage (+)} = \text{AVREFP}, \text{reference voltage (-)} = \text{AVREFM} = 0 \text{ V}, \text{HALT mode)}$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Resolution	RES				12	bit
Overall error Notes 1, 2, 3	AINL	12-bit resolution		±1.7	±3.3	LSB
Conversion time	tCONV	ADTYP = 0, 12-bit resolution	3.375			μs
Zero-scale error Notes 1, 2, 3	Ezs	12-bit resolution		±1.3	±3.2	LSB
Full-scale error Notes 1, 2, 3	EFS	12-bit resolution		±0.7	±2.9	LSB
Integral linearity error Notes 1, 2, 3	ILE	12-bit resolution		±1.0	±1.4	LSB
Differential linearity error Notes 1, 2, 3	DLE	12-bit resolution		±0.9	±1.2	LSB
Analog input voltage	Vain		0		AVREFP	V

- Note 1. TYP. Value is the average value at AVDD = AVREFP = 3 V and TA = 25°C. MAX. value is the average value ±3σ at normalized distribution.
- Note 2. These values are the results of characteristic evaluation and are not checked for shipment.
- Note 3. Excludes quantization error (±1/2 LSB).
- Caution 1. Route the wiring so that noise will not be superimposed on each power line and ground line, and insert a capacitor to suppress noise.
 - In addition, separate the reference voltage line of AVREFP from the other power lines to keep it free from the influences of noise.
- Caution 2. During A/D conversion, keep a pulse, such as a digital signal, that abruptly changes its level from being input to or output from the pins adjacent to the converter pins and P150 to P156.



(2) When reference voltage (+) = AVREFP/ANIO (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), conversion target: ANI2 to ANI6

(TA = -40 to +85°C, 1.6 V \leq AVREFP \leq AVDD = VDD \leq 3.6 V, Vss = 0 V, AVss = 0 V, Reference voltage (+) = AVREFP, Reference voltage (-) = AVREFM = 0 V)

Parameter	Symbol		Conditions	MIN.	TYP.	MAX.	Unit
Resolution	Res		2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V	8		12	bit
			1.8 V ≤ AVREFP ≤ AVDD ≤ 3.6 V	8		10 Note 1	
			1.6 V ≤ AVREFP ≤ AVDD ≤ 3.6 V		8 Note 2	2	
Overall error Note 3	AINL	12-bit resolution	2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±6.0	LSB
		10-bit resolution	1.8 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±5.0	
		8-bit resolution	1.6 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±2.5	
Conversion time	tCONV	ADTYP = 0, 12-bit resolution	2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V	3.375			μs
		ADTYP = 0, 10-bit resolution Note 1	1.8 V ≤ AVREFP ≤ AVDD ≤ 3.6 V	6.75			
		ADTYP = 0, 8-bit resolution Note 2	1.6 V ≤ AVREFP ≤ AVDD ≤ 3.6 V	13.5			
		ADTYP = 1,	2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V	2.5625			
		8-bit resolution	1.8 V ≤ AVREFP ≤ AVDD ≤ 3.6 V	5.125			
			1.6 V ≤ AVREFP ≤ AVDD ≤ 3.6 V	10.25			
Zero-scale error Note 3	Ezs	12-bit resolution	2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±4.5	LSB
		10-bit resolution	1.8 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±4.5	
		8-bit resolution	1.6 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±2.0	
Full-scale error Note 3	EFS	12-bit resolution	2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±4.5	LSB
		10-bit resolution	1.8 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±4.5	
		8-bit resolution	1.6 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±2.0	
Integral linearity error	ILE	12-bit resolution	2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±2.0	LSB
Note 3		10-bit resolution	1.8 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±1.5	
		8-bit resolution	1.6 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±1.0	
Differential linearity error	DLE	12-bit resolution	2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±1.5	LSB
Note 3		10-bit resolution	1.8 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±1.5	
		8-bit resolution	1.6 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±1.0	
Analog input voltage	VAIN			0		AVREFP	V

Note 1. Cannot be used for lower 2 bit of ADCR register

Note 2. Cannot be used for lower 4 bit of ADCR register

Note 3. Excludes quantization error (±1/2 LSB).

Caution Always use AVDD pin with the same potential as the VDD pin.



(3) When reference voltage (+) = AVDD (ADREFP1 = 0, ADREFP0 = 0), reference voltage (-) = AVSS (ADREFM = 0), conversion target: ANI0 to ANI6

(TA = -40 to +85°C, 1.6 V \leq AVDD = VDD \leq 3.6 V, Vss = 0 V, AVss = 0 V, Reference voltage (+) = AVDD, Reference voltage (-) = AVss = 0 V)

Parameter	Symbol	Cor	ditions	MIN.	TYP.	MAX.	Unit
Resolution	RES		2.4 V ≤ AVDD ≤ 3.6 V	8		12	bit
			1.8 V ≤ AVDD ≤ 3.6 V	8		10 Note 1	
			1.6 V ≤ AVDD ≤ 3.6 V		8 Note 2		
Overall error Note 3	AINL	12-bit resolution	2.4 V ≤ AVDD ≤ 3.6 V			±7.5	LSB
		10-bit resolution	1.8 V ≤ AVDD ≤ 3.6 V			±5.5	
		8-bit resolution	1.6 V ≤ AVDD ≤ 3.6 V			±3.0	
Conversion time	tCONV	ADTYP = 0, 12-bit resolution	2.4 V ≤ AVDD ≤ 3.6 V	3.375			μs
		ADTYP = 0, 10-bit resolution Note 1	1.8 V ≤ AVDD ≤ 3.6 V	6.75			
		ADTYP = 0, 8-bit resolution Note 2	1.6 V ≤ AVDD ≤ 3.6 V	13.5			
		ADTYP = 1,	2.4 V ≤ AVDD ≤ 3.6 V	2.5625			
		8-bit resolution	1.8 V ≤ AVDD ≤ 3.6 V	5.125			
			1.6 V ≤ AVDD ≤ 3.6 V	10.25			
Zero-scale error Note 3	Ezs	12-bit resolution	2.4 V ≤ AVDD ≤ 3.6 V			±6.0	LSB
		10-bit resolution	1.8 V ≤ AVDD ≤ 3.6 V			±5.0	
		8-bit resolution	1.6 V ≤ AVDD ≤ 3.6 V			±2.5	
Full-scale error Note 3	EFS	12-bit resolution	2.4 V ≤ AVDD ≤ 3.6 V			±6.0	LSB
		10-bit resolution	1.8 V ≤ AVDD ≤ 3.6 V			±5.0	
		8-bit resolution	1.6 V ≤ AVDD ≤ 3.6 V			±2.5	
Integral linearity error	ILE	12-bit resolution	2.4 V ≤ AVDD ≤ 3.6 V			±3.0	LSB
Note 3		10-bit resolution	1.8 V ≤ AVDD ≤ 3.6 V			±2.0	
		8-bit resolution	1.6 V ≤ AVDD ≤ 3.6 V			±1.5	
Differential linearity error	DLE	12-bit resolution	2.4 V ≤ AVDD ≤ 3.6 V			±2.0	LSB
Note 3		10-bit resolution	1.8 V ≤ AVDD ≤ 3.6 V			±2.0	
		8-bit resolution	1.6 V ≤ AVDD ≤ 3.6 V			±1.5	
Analog input voltage	VAIN	ANI0 to ANI6		0		AVDD	V

Note 1. Cannot be used for lower 2 bit of ADCR register
Note 2. Cannot be used for lower 4 bit of ADCR register
Note 3. Excludes quantization error (±1/2 LSB).

Caution Always use AVDD pin with the same potential as the VDD pin.



(4) When reference voltage (+) = AVREFP/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), conversion target: ANI16 to ANI21, internal reference voltage, temperature sensor output voltage

(TA = -40 to +85°C, 1.6 V \leq VDD \leq 3.6 V, 1.6 V \leq AVREFP \leq AVDD = VDD \leq 3.6 V, Vss = 0 V, AVss = 0 V, Reference voltage (+) = AVREFP, Reference voltage (-) = AVREFM = 0 V)

Parameter	Symbol		Conditions	MIN.	TYP.	MAX.	Unit
Resolution	RES		2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V	8		12	bit
			1.8 V ≤ AVREFP ≤ AVDD ≤ 3.6 V	8		10 Note 1	
			1.6 V ≤ AVREFP ≤ AVDD ≤ 3.6 V		8 Note 2		
Overall error Note 3	AINL	12-bit resolution	2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±7.0	LSB
		10-bit resolution	1.8 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±5.5	
		8-bit resolution	1.6 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±3.0	
Conversion time	tCONV	ADTYP = 0, 12-bit resolution	2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V	4.125			μs
		ADTYP = 0, 10-bit resolution Note 1	1.8 V ≤ AVREFP ≤ AVDD ≤ 3.6 V	9.5			
		ADTYP = 0, 8-bit resolution Note 2	1.6 V ≤ AVREFP ≤ AVDD ≤ 3.6 V	57.5			
		ADTYP = 1,	2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V	3.3125			
		8-bit resolution	1.8 V ≤ AVREFP ≤ AVDD ≤ 3.6 V	7.875			
			1.6 V ≤ AVREFP ≤ AVDD ≤ 3.6 V	54.25			
Zero-scale error Note 3	Ezs	12-bit resolution	2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±5.0	LSB
		10-bit resolution	1.8 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±5.0	
		8-bit resolution	1.6 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±2.5	
Full-scale error Note 3	EFS	12-bit resolution	2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±5.0	LSB
		10-bit resolution	1.8 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±5.0	
		8-bit resolution	1.6 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±2.5	
Integral linearity error	ILE	12-bit resolution	2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±3.0	LSB
Note 3		10-bit resolution	1.8 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±2.0	
		8-bit resolution	1.6 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±1.5	
Differential linearity error	DLE	12-bit resolution	2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±2.0	LSB
Note 3		10-bit resolution	1.8 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±2.0	
		8-bit resolution	1.6 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±1.5	
Analog input voltage	VAIN			0		AVREFP	V
		Internal reference voltage (2.4 V ≤ VDD ≤ 3.6 V, HS (high-speed main) mode)		,	VBGR Note	e 4	
		Temperature sensor ou (2.4 V ≤ VDD ≤ 3.6 V, H	tput voltage IS (high-speed main) mode)	V	TMP25 No	te 4	

Note 1. Cannot be used for lower 2 bits of ADCR register

Caution Always use AVDD pin with the same potential as the VDD pin.



Note 2. Cannot be used for lower 4 bits of ADCR register

Note 3. Excludes quantization error (±1/2 LSB).

Note 4. Refer to 2.6.2 Temperature sensor, internal reference voltage output characteristics.

(5) When reference voltage (+) = AVDD (ADREFP1 = 0, ADREFP0 = 0), reference voltage (-) = AVSS (ADREFM = 0), conversion target: ANI16 to ANI21, internal reference voltage, temperature sensor output voltage

(TA = -40 to +85°C, 1.6 V \leq VDD \leq 3.6 V, 1.6 V \leq AVDD = VDD \leq 3.6 V, VSS = 0 V, AVSS = 0 V, Reference voltage (+) = AVDD, Reference voltage (-) = AVSS = 0 V)

Parameter	Symbol	Cor	ditions	MIN.	TYP.	MAX.	Unit
Resolution	RES		2.4 V ≤ AVDD ≤ 3.6 V	8		12	bit
			1.8 V ≤ AVDD ≤ 3.6 V	8		10 Note 1	
			1.6 V ≤ AVDD ≤ 3.6 V		8 Note 2		
Overall error Note 3	AINL	12-bit resolution	2.4 V ≤ AVDD ≤ 3.6 V			±8.5	LSB
		10-bit resolution	1.8 V ≤ AVDD ≤ 3.6 V			±6.0	
		8-bit resolution	1.6 V ≤ AVDD ≤ 3.6 V			±3.5	
Conversion time	tCONV	ADTYP = 0, 12-bit resolution	2.4 V ≤ AVDD ≤ 3.6 V	4.125			μs
		ADTYP = 0, 10-bit resolution Note 1	1.8 V ≤ AVDD ≤ 3.6 V	9.5			
		ADTYP = 0, 8-bit resolution Note 2	1.6 V ≤ AVDD ≤ 3.6 V	57.5			
		ADTYP = 1,	2.4 V ≤ AVDD ≤ 3.6 V	3.3125			
		8-bit resolution	1.8 V ≤ AVDD ≤ 3.6 V	7.875			
			1.6 V ≤ AVDD ≤ 3.6 V	54.25			
Zero-scale error Note 3	Ezs	12-bit resolution	2.4 V ≤ AVDD ≤ 3.6 V			±8.0	LSB
		10-bit resolution	1.8 V ≤ AVDD ≤ 3.6 V			±5.5	
		8-bit resolution	1.6 V ≤ AVDD ≤ 3.6 V			±3.0	
Full-scale error Note 3	EFS	12-bit resolution	2.4 V ≤ AVDD ≤ 3.6 V			±8.0	LSB
		10-bit resolution	1.8 V ≤ AVDD ≤ 3.6 V			±5.5	
		8-bit resolution	1.6 V ≤ AVDD ≤ 3.6 V			±3.0	
Integral linearity error	ILE	12-bit resolution	2.4 V ≤ AVDD ≤ 3.6 V			±3.5	LSB
Note 3		10-bit resolution	1.8 V ≤ AVDD ≤ 3.6 V			±2.5	
		8-bit resolution	1.6 V ≤ AVDD ≤ 3.6 V			±1.5	
Differential linearity error	DLE	12-bit resolution	2.4 V ≤ AVDD ≤ 3.6 V			±2.5	LSB
Note 3		10-bit resolution	1.8 V ≤ AVDD ≤ 3.6 V			±2.5	
		8-bit resolution	1.6 V ≤ AVDD ≤ 3.6 V			±2.0	
Analog input voltage	VAIN		•	0		AVDD	V
	Internal reference voltage (2.4 V ≤ VDD ≤ 3.6 V, HS (high-speed main) mode		•	VBGR Note 4			
		Temperature sensor out (2.4 V ≤ VDD ≤ 3.6 V, HS	put voltage 6 (high-speed main) mode)	V	TMP25 Note	: 4	

Note 1. Cannot be used for lower 2 bits of ADCR register

Caution Always use AVDD pin with the same potential as the VDD pin.



Note 2. Cannot be used for lower 4 bits of ADCR register

Note 3. Excludes quantization error (±1/2 LSB).

Note 4. Refer to 2.6.2 Temperature sensor, internal reference voltage output characteristics.

(6) When reference voltage (+) = Internal reference voltage (1.45 V) (ADREFP1 = 1, ADREFP0 = 0), reference voltage (-) = AVSS (ADREFM = 0), conversion target: ANI0 to ANI6, ANI16 to ANI21

(TA = -40 to +85°C, 2.4 V \leq VDD \leq 3.6 V, 1.6 V \leq VDD, 1.6 V \leq AVDD = VDD, Vss = 0 V, AVss = 0 V, Reference voltage (+) = internal reference voltage, Reference voltage (-) = AVss = 0 V, HS (high-speed main) mode)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Resolution	Res			8		bit
Conversion time	tCONV	8-bit resolution	16			μs
Zero-scale error Note	Ezs	8-bit resolution			±4.0	LSB
Integral linearity error Note	ILE	8-bit resolution			±2.0	LSB
Differential linearity error Note	DLE	8-bit resolution			±2.5	LSB
Reference voltage (+)	AVREF(+)	= Internal reference voltage (VBGR)	1.38	1.45	1.5	V
Analog input voltage	Vain		0		VBGR	V

Note Excludes quantization error (±1/2 LSB).

Caution Always use AVDD pin with the same potential as the VDD pin.

2.6.2 Temperature sensor, internal reference voltage output characteristics

(TA = -40 to +85°C, 2.4 V \leq VDD \leq 3.6 V, Vss = 0 V (HS (high-speed main) mode))

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Temperature sensor output voltage	VTMPS25	Setting ADS register = 80H, TA = +25°C		1.05		V
Internal reference voltage	VBGR	Setting ADS register = 81H	1.38	1.45	1.5	V
Temperature coefficient	FVTMPS	Temperature sensor output voltage that depends on the temperature		-3.6		mV/°C
Operation stabilization wait time	tamp		10			μs

2.6.3 D/A converter characteristics

 $(TA = -40 \text{ to } +85^{\circ}C, 1.6 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Cor	MIN.	TYP.	MAX.	Unit	
Resolution	RES					8	bit
Overall error	AINL	Rload = 4 MΩ	1.8 V ≤ VDD ≤ 3.6 V			±2.5	LSB
		Rload = 8 MΩ	1.8 V ≤ VDD ≤ 3.6 V			±2.5	LSB
Settling time	tSET	Cload = 20 pF	2.7 V ≤ VDD ≤ 3.6 V			3	μs
			1.6 V ≤ VDD < 2.7 V			6	μs



2.6.4 Comparator

 $(TA = -40 \text{ to } +85^{\circ}C, 1.6 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Cor	nditions	MIN.	TYP.	MAX.	Unit
Input voltage range	Ivref			0		VDD - 1.4	V
	Ivcmp			-0.3		VDD + 0.3	V
Output delay	td	VDD = 3.0 V Input slew rate > 50 mV/µs	High-speed comparator mode, standard mode			1.2	μs
			High-speed comparator mode, window mode			2.0	μs
			Low-speed comparator mode, standard mode		3	5.0	μs
High-electric-potential judgment voltage	VTW+	High-speed comparator mod	de, window mode		0.76 VDD		V
Low-electric-potential judgment voltage	VTW-	High-speed comparator mod	de, window mode		0.24 VDD		V
Operation stabilization wait time	tCMP			100			μs
Internal reference voltage Note	VBGR			1.38	1.45	1.50	V

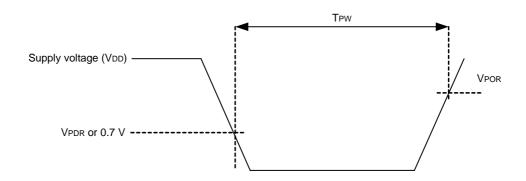
Note Stope Not usable in LS (low-speed main) mode, LV (low-voltage main) mode, sub-clock operation, or STOP mode.

2.6.5 POR circuit characteristics

 $(TA = -40 \text{ to } +85^{\circ}C, Vss = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	VPOR	Power supply rise time	1.47	1.51	1.55	V
	VPDR	Power supply fall time Note	1.46	1.50	1.54	V
Minimum pulse width	TPW		300			μs

Minimum time required for a POR reset when VDD exceeds below VPDR. This is also the minimum time required for a POR reset from when VDD exceeds below 0.7 V to when VDD exceeds VPOR while STOP mode is entered or the main system clock is stopped through setting bit 0 (HIOSTOP) and bit 7 (MSTOP) in the clock operation status control register (CSC).



2.6.6 LVD circuit characteristics

(TA = -40 to +85°C, VPDR \leq VDD \leq 3.6 V \leq VSS = 0 V)

	Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection	Supply voltage level	VLVD2	Power supply rise time	3.07	3.13	3.19	V
voltage			Power supply fall time	3.00	3.06	3.12	V
		VLVD3	Power supply rise time	2.96	3.02	3.08	V
			Power supply fall time	2.90	2.96	3.02	V
		VLVD4	Power supply rise time	2.86	2.92	2.97	V
			Power supply fall time	2.80	2.86	2.91	V
		VLVD5	Power supply rise time	2.76	2.81	2.87	V
			Power supply fall time	2.70	2.75	2.81	V
		VLVD6	Power supply rise time	2.66	2.71	2.76	V
			Power supply fall time	2.60	2.65	2.70	V
		VLVD7	Power supply rise time	2.56	2.61	2.66	V
			Power supply fall time	2.50	2.55	2.60	V
		VLVD8	Power supply rise time	2.45	2.50	2.55	V
			Power supply fall time	2.40	2.45	2.50	V
		VLVD9	Power supply rise time	2.05	2.09	2.13	V
			Power supply fall time	2.00	2.04	2.08	V
		VLVD10	Power supply rise time	1.94	1.98	2.02	V
			Power supply fall time	1.90	1.94	1.98	V
		VLVD11	Power supply rise time	1.84	1.88	1.91	V
			Power supply fall time	1.80	1.84	1.87	V
		VLVD12	Power supply rise time	1.74	1.77	1.81	V
			Power supply fall time	1.70	1.73	1.77	V
		VLVD13	Power supply rise time	1.64	1.67	1.70	V
			Power supply fall time	1.60	1.63	1.66	V
Minimum pul	se width	tLW		300			μs
Detection de						300	μs

Caution Set the detection voltage (VLVD) to be within the operating voltage range. The operating voltage range depends on the setting of the user option byte (000C2H/010C2H). The following shows the operating voltage range.

HS (high-speed main) mode: VDD = 2.7 to 3.6 V at 1 MHz to 24 MHz

VDD = 2.4 to 3.6 V at 1 MHz to 16 MHz

LS (low-speed main) mode: VDD = 1.8 to 3.6 V at 1 MHz to 8 MHz LV (low-voltage main) mode: VDD = 1.6 to 3.6 V at 1 MHz to 4 MHz

LVD Detection Voltage of Interrupt & Reset Mode (TA = -40 to +85°C, VPDR \leq VDD \leq 3.6 V, Vss = 0 V)

Parameter	Symbol		Cor	ditions	MIN.	TYP.	MAX.	Unit
Interrupt and reset	VLVDA0	VPOC0	VPOC1, VPOC2 = 0, 0, 0,	falling reset voltage: 1.6 V	1.60	1.63	1.66	V
mode	VLVDA1		LVIS0, LVIS1 = 1, 0	Rising release reset voltage	1.74	1.77	1.81	V
				Falling interrupt voltage	1.70	1.73	1.77	V
	VLVDA2		LVIS0, LVIS1 = 0, 1	Rising release reset voltage	1.84	1.88	1.91	V
				Falling interrupt voltage	1.80	1.84	1.87	V
	VLVDA3		LVIS0, LVIS1 = 0, 0	Rising release reset voltage	2.86	2.92	2.97	V
				Falling interrupt voltage	2.80	2.86	2.91	V
	VLVDB0	VPOC0	VPOC1, VPOC2 = 0, 0, 1,	falling reset voltage: 1.8 V	1.80	1.84	1.87	V
	VLVDB1		LVIS0, LVIS1 = 1, 0	Rising release reset voltage	1.94	1.98	2.02	V
				Falling interrupt voltage	1.90	1.94	1.98	V
VLVDB2	VLVDB2		LVIS0, LVIS1 = 0, 1	Rising release reset voltage	2.05	2.09	2.13	V
				Falling interrupt voltage	2.00	2.04	2.08	V
	VLVDB3		LVIS0, LVIS1 = 0, 0	Rising release reset voltage	3.07	3.13	3.19	V
				Falling interrupt voltage	3.00	3.06	3.12	V
	VLVDC0	VPOC0	, VPOC1, VPOC2 = 0, 1, 0, falling reset voltage: 2.4 V		2.40	2.45	2.50	V
	VLVDC1		LVIS0, LVIS1 = 1, 0	Rising release reset voltage	2.56	2.61	2.66	V
				Falling interrupt voltage	2.50	2.55	2.60	V
	VLVDC2		LVIS0, LVIS1 = 0, 1	Rising release reset voltage	2.66	2.71	2.76	V
				Falling interrupt voltage	2.60	2.65	2.70	V
VLVDD0	VPOC0	VPOC1, VPOC2 = 0, 1, 1,	falling reset voltage: 2.7 V	2.70	2.75	2.81	V	
	VLVDD1	1	LVIS0, LVIS1 = 1, 0	Rising release reset voltage	2.86	2.92	2.97	V
				Falling interrupt voltage	2.80	2.86	2.91	V
	VLVDD2	1	LVIS0, LVIS1 = 0, 1	Rising release reset voltage	2.96	3.02	3.08	V
				Falling interrupt voltage	2.90	2.96	3.02	V

2.7 Power supply voltage rising slope characteristics

$(TA = -40 \text{ to } +85^{\circ}C, Vss = 0 \text{ V})$

Parameter	Conditions	MIN.	TYP.	MAX.	Unit
Power supply voltage rising slope	SVDD			54	V/ms

Caution Make sure to keep the internal reset state by the LVD circuit or an external reset until VDD reaches the operating voltage range shown in 2.4 AC Characteristics.

2.8 LCD Characteristics

2.8.1 Resistance division method

(1) Static display mode

(TA = -40 to +85°C, VL4 (MIN.) \leq VDD \leq 3.6 V, VSS = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
LCD drive voltage	VL4		2.0		VDD	V

(2) 1/2 bias method, 1/4 bias method

(TA = -40 to +85°C, VL4 (MIN.) \leq VDD \leq 3.6 V, VSS = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
LCD drive voltage	VL4		2.7		VDD	V

(3) 1/3 bias method

(TA = -40 to +85°C, VL4 (MIN.) \leq VDD \leq 3.6 V, VSS = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
LCD drive voltage	VL4		2.5		VDD	V

2.8.2 Internal voltage boosting method

(1) 1/3 bias method

 $(TA = -40 \text{ to } +85^{\circ}C, 1.8 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Cond	litions	MIN.	TYP.	MAX.	Unit
LCD output voltage variation range	VL1	C1 to C4 Note 1	VLCD = 04H	0.90	1.00	1.08	V
		= 0.47 µF Note 2	VLCD = 05H	0.95	1.05	1.13	V
			VLCD = 06H	1.00	1.10	1.18	V
			VLCD = 07H	1.05	1.15	1.23	V
			VLCD = 08H	1.10	1.20	1.28	V
			VLCD = 09H	1.15	1.25	1.33	V
			VLCD = 0AH	1.20	1.30	1.38	V
			VLCD = 0BH	1.25	1.35	1.43	V
			VLCD = 0CH	1.30	1.40	1.48	V
			VLCD = 0DH	1.35	1.45	1.53	V
			VLCD = 0EH	1.40	1.50	1.58	V
			VLCD = 0FH	1.45	1.55	1.63	V
			VLCD = 10H	1.50	1.60	1.68	V
			VLCD = 11H	1.55	1.65	1.73	V
			VLCD = 12H	1.60	1.70	1.78	V
			VLCD = 13H	1.65	1.75	1.83	V
Doubler output voltage	VL2	C1 to C4 ^{Note 1} =	0.47 μF	2 V _{L1} - 0.1	2 VL1	2 VL1	V
Tripler output voltage	VL3	C1 to C4 ^{Note 1} = 0.47 µF		3 V _{L1} - 0.15	3 VL1	3 VL1	V
Reference voltage setup time Note 2	tvwait1			5			ms
Voltage boost wait time Note 3	tVWAIT2	C1 to C4 ^{Note 1} =	0.47µF	500			ms

Note 1. This is a capacitor that is connected between voltage pins used to drive the LCD.

- C1: A capacitor connected between CAPH and CAPL
- C2: A capacitor connected between VL1 and GND
- C3: A capacitor connected between VL2 and GND
- C4: A capacitor connected between VL4 and GND
- $C1 = C2 = C3 = C4 = 0.47 \mu F \pm 30\%$
- Note 2. This is the time required to wait from when the reference voltage is specified by using the VLCD register (or when the internal voltage boosting method is selected (by setting the MDSET1 and MDSET0 bits of the LCDM0 register to 01B) if the default value reference voltage is used) until voltage boosting starts (VLCON = 1).
- Note 3. This is the wait time from when voltage boosting is started (VLCON = 1) until display is enabled (LCDON = 1).

(2) 1/4 bias method

$(TA = -40 \text{ to } +85^{\circ}C, 1.8 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conc	ditions	MIN.	TYP.	MAX.	Unit
LCD output voltage variation range	VL1	C1 to C4 Note 1	VLCD = 04H	0.90	1.00	1.08	V
		= 0.47 µF Note 2	VLCD = 05H	0.95	1.05	1.13	V
			VLCD = 06H	1.00	1.10	1.18	V
			VLCD = 07H	1.05	1.15	1.23	V
			VLCD = 08H	1.10	1.20	1.28	V
			VLCD = 09H	1.15	1.25	1.33	V
			VLCD = 0AH	1.20	1.30	1.38	V
Doubler output voltage	VL2	C1 to C4 Note 1 =	= 0.47 μF	2 VL1 - 0.08	2 VL1	2 VL1	V
Tripler output voltage	VL3	C1 to C4 Note 1 =	= 0.47 μF	3 V _{L1} - 0.12	3 VL1	3 VL1	V
Quadruply output voltage	VL4	C1 to C5 Note 1 =	= 0.47 μF	4 VL1 - 0.16	4 VL1	4 VL1	V
Reference voltage setup time Note 2	tVWAIT1			5			ms
Voltage boost wait time Note 3	tVWAIT2	C1 to C5 Note 1 =	= 0.47µF	500			ms

- **Note 1.** This is a capacitor that is connected between voltage pins used to drive the LCD.
 - C1: A capacitor connected between CAPH and CAPL
 - C2: A capacitor connected between VL1 and GND
 - C3: A capacitor connected between VL2 and GND
 - C4: A capacitor connected between VL3 and GND
 - C5: A capacitor connected between VL4 and GND
 - $C1 = C2 = C3 = C4 = 0.47 \mu F \pm 30\%$
- Note 2. This is the time required to wait from when the reference voltage is specified by using the VLCD register (or when the internal voltage boosting method is selected (by setting the MDSET1 and MDSET0 bits of the LCDM0 register to 01B) if the default value reference voltage is used) until voltage boosting starts (VLCON = 1).
- Note 3. This is the wait time from when voltage boosting is started (VLCON = 1) until display is enabled (LCDON = 1).



2.8.3 Capacitor split method

(1) 1/3 bias method

 $(TA = -40 \text{ to } +85^{\circ}C, 2.2 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
VL4 voltage	VL4	C1 to C4 = 0.47 µF Note 2		VDD		V
VL2 voltage	VL2	C1 to C4 = 0.47 µF Note 2	2/3 V _{L4} - 0.1	2/3 VL4	2/3 V _{L4} + 0.1	V
VL1 voltage	VL1	C1 to C4 = 0.47 µF Note 2	1/3 VL4 - 0.1	1/3 VL4	1/3 V _{L4} + 0.1	V
Capacitor split wait time Note 1	tvwait		100			ms

Note 1. This is the wait time from when voltage bucking is started (VLCON = 1) until display is enabled (LCDON = 1).

Note 2. This is a capacitor that is connected between voltage pins used to drive the LCD.

C1: A capacitor connected between CAPH and CAPL

C2: A capacitor connected between VL1 and GND

C3: A capacitor connected between VL2 and GND

C4: A capacitor connected between VL4 and GND

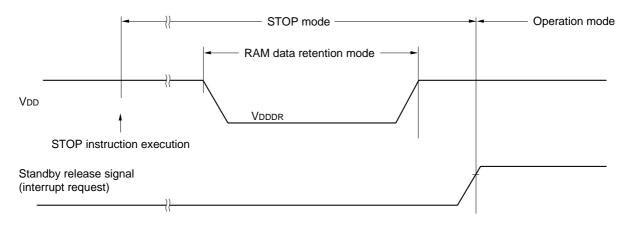
 $C1 = C2 = C3 = C4 = 0.47 \mu F \pm 30\%$

2.9 RAM Data Retention Characteristics

$(TA = -40 \text{ to } +85^{\circ}C, Vss = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	VDDDR		1.46 Note		3.6	V

Note This depends on the POR detection voltage. For a falling voltage, data in RAM are retained until the voltage reaches the level that triggers a POR reset but not once it reaches the level at which a POR reset is generated.



2.10 Flash Memory Programming Characteristics

$(TA = -40 \text{ to } +85^{\circ}C, 1.8 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
CPU/peripheral hardware clock frequency	fCLK	2.4 V ≤ VDD ≤ 3.6 V	1		24	MHz
Number of code flash rewrites Notes 1, 2, 3	Cerwr	Retained for 20 years TA = 85°C	1,000			Times
Number of data flash rewrites Notes 1, 2, 3		Retained for 1 year TA = 25°C		1,000,000		
		Retained for 5 years TA = 85°C	100,000			
		Retained for 20 years TA = 85°C	10,000			

- Note 1. 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the rewrite.
- Note 2. When using flash memory programmer and Renesas Electronics self programming library
- **Note 3.** These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.

2.11 Dedicated Flash Memory Programmer Communication (UART)

 $(TA = -40 \text{ to } +85^{\circ}C, 1.8 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, \text{VSS} = 0 \text{ V})$

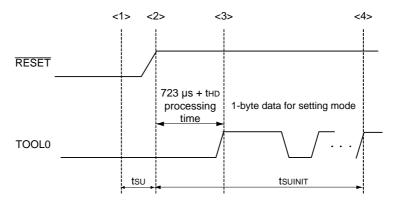
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115,200		1,000,000	bps



2.12 Timing of Entry to Flash Memory Programming Modes

 $(TA = -40 \text{ to } +85^{\circ}C, 1.8 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
How long from when an external reset ends until the initial communication settings are specified	tsuinit	POR and LVD reset must end before the external reset ends.			100	ms
How long from when the TOOL0 pin is placed at the low level until an external reset ends	tsu	POR and LVD reset must end before the external reset ends.	10			μs
Time to hold the TOOL0 pin at the low level after an external reset is released (excluding the processing time of the firmware to control the flash memory)	tHD	POR and LVD reset must end before the external reset ends.	1			ms



- <1> The low level is input to the TOOL0 pin.
- <2> The external reset ends (POR and LVD reset must end before the external reset ends.).
- <3> The TOOL0 pin is set to the high level.
- <4> Setting of the flash memory programming mode by UART reception and complete the baud rate setting.

Remark tsuinit: The segment shows that it is necessary to finish specifying the initial communication settings within 100 ms from when the resets end.

tsu: How long from when the TOOL0 pin is placed at the low level until a external reset ends

thd: How long to keep the TOOL0 pin at the low level from when the external and internal resets end (except soft processing time)

3. ELECTRICAL SPECIFICATIONS (G: INDUSTRIAL APPLICATIONS TA = - 40 to +105°C)

This chapter describes the following electrical specifications.

Target products G: Industrial applications TA = -40 to +105°C

R5F110xxGxx, R5F111xxGxx

- Caution 1. The RL78 microcontroller has an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.
- Caution 2. The pins mounted depend on the product. Refer to 2.1 Port Function to 2.2.1 With functions for each product in the RL78/L1C User's Manual.
- Caution 3. Please contact Renesas Electronics sales office for derating of operation under TA = +85°C to +105°C. Derating is the systematic reduction of load for the sake of improved reliability.
- Remark When the RL78 microcontroller is used in the range of TA = -40 to +85°C, see 2. ELECTRICAL SPECIFICATIONS (TA = -40 to +85°C).

The following functions differ between the products "G: Industrial applications ($TA = -40 \text{ to } +105^{\circ}\text{C}$)" and the products "A: Consumer applications and G: Industrial applications (when used in the range of $TA = -40 \text{ to } +85^{\circ}\text{C}$)".

Parameter	A: Consumer applications	G: Industrial applications
Operating ambient temperature	TA = -40 to +85°C	TA = -40 to +105°C
Operating mode Operating voltage range	HS (high-speed main) mode: 2.7 V ≤ VDD ≤ 3.6 V@1 MHz to 24 MHz 2.4 V ≤ VDD ≤ 3.6 V@1 MHz to 16 MHz LS (low-speed main) mode: 1.8 V ≤ VDD ≤ 3.6 V@1 MHz to 8 MHz LV (low-voltage main) mode: 1.6 V ≤ VDD ≤ 3.6 V@1 MHz to 4 MHz	HS (high-speed main) mode only: 2.7 V ≤ VDD ≤ 3.6 V@1 MHz to 24 MHz 2.4 V ≤ VDD ≤ 3.6 V@1 MHz to 16 MHz
High-speed on-chip oscillator clock accuracy	1.8 $V \le VDD \le 3.6 V$: ±1.0% @ TA = -20 to +85°C ±1.5% @ TA = -40 to -20°C 1.6 $V \le VDD \le 1.8 V$: ±5.0% @ TA = -20 to +85°C ±5.5% @ TA = -40 to -20°C	2.4 V ≤ VDD ≤ 3.6 V: ±2.0% @ TA = +85 to +105°C ±1.0% @ TA = -20 to +85°C ±1.5% @ TA = -40 to -20°C
Serial array unit	UART Simplified SPI (CSI): fcLk/4 Simplified I ² C communication	UART Simplified SPI (CSI): fcLk/4 Simplified I ² C communication
IICA	Normal mode Fast mode Fast mode plus	Normal mode Fast mode
Voltage detector	Rise detection: 1.67 V to 3.13 V (12 levels) Fall detection: 1.63 V to 3.06 V (12 levels)	Rise detection: 2.61 V to 3.13 V (6 levels) Fall detection: 2.55 V to 3.06 V (6 levels)

Remark The electrical characteristics of the products G: Industrial applications (TA = -40 to +105°C) are different from those of the products "A: Consumer applications". For details, refer to **3.1** to **3.12**.



3.1 Absolute Maximum Ratings

Absolute Maximum Ratings (TA = 25°C)

(1/3)

Parameter	Symbols	Conditions	Ratings	Unit
Supply voltage	VDD		-0.5 to + 6.5	V
	UVBUS		-0.5 to + 6.5	V
	AVDD	AVDD ≤ VDD	-0.5 to + 4.6	V
REGC pin input voltage	VIREGC	REGC	-0.3 to + 2.8	V
			and -0.3 to VDD + 0.3 Note 1	
UREGC pin input voltage	Viuregc	UREGC	-0.3 to UVBUS + 0.3 Note 2	V
Input voltage	VI1	P00 to P07, P10 to P17, P20 to P27, P30 to P37, P40 to P46, P50 to P57, P70 to P77, P80 to P83, P125 to P127, P137, P140 to P143, EXCLK, EXCLKS, RESET	-0.3 to VDD + 0.3 Note 3	V
	VI2	P60, P61 (N-ch open-drain)	-0.3 to + 6.5	V
	VI3	UDP, UDM	-0.3 to + 6.5	V
	VI4	P150 to P156	-0.3 to AVDD + 0.3 Note 4	V
Output voltage	VO1	P00 to P07, P10 to P17, P20 to P27, P30 to P37, P40 to P46, P50 to P57, P60, P61, P70 to P77, P80 to P83, P125 to P127, P130, P140 to P143	-0.3 to VDD + 0.3 Note 3	V
	VO2	P150 to P156	-0.3 to AVDD + 0.3 Note 3	V
	VO3	UDP, UDM	-0.3 to + 3.8	V
Analog input voltage	VAI1	ANI16 to ANI21	-0.3 to VDD + 0.3 and AVREF(+) + 0.3 Notes 3, 5	V
	VAI2	ANI0 to ANI6	-0.3 to AVDD + 0.3 and AVREF(+) + 0.3 Notes 3, 5	V

- Note 1. Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F). This value regulates the absolute maximum rating of the REGC pin. Do not use this pin with voltage applied to it.
- **Note 2.** Connect the UREGC pin to Vss via a capacitor (0.33 μF). This value regulates the absolute maximum rating of the UREGC pin. Do not use this pin with voltage applied to it.
- Note 3. Must be 6.5 V or lower.
- Note 4. Must be 4.6 V or lower.
- **Note 5.** Do not exceed AVREF(+) + 0.3 V in case of A/D conversion target pin.
- Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter.

 That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.
- Remark 1. Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.
- Remark 2. AVREF (+): + side reference voltage of the A/D converter.
- Remark 3. Vss: Reference voltage

Absolute Maximum Ratings (TA = 25°C)

(2/3)

Parameter	Symbols		Conditions	Ratings	Unit
LCD voltage	VLI1	VL1 input voltage ¹	Note 1	-0.3 to +2.8	V
	VLI2	VL2 input voltage ¹	Note 1	-0.3 to +6.5	V
	VLI3	VL3 input voltage ¹	Note 1	-0.3 to +6.5	V
	VLI4	VL4 input voltage 1	Note 1	-0.3 to +6.5	V
	VLI5	CAPL, CAPH inpu	t voltage ^{Note 1}	-0.3 to +6.5	V
	VLO1	V _L 1 output voltage	,	-0.3 to +2.8	V
	VLO2	VL2 output voltage	,	-0.3 to +6.5	V
	VLO3	VL3 output voltage		-0.3 to +6.5	V
	VLO4	VL4 output voltage		-0.3 to +6.5	V
	VLO5	CAPL, CAPH outp	out voltage	-0.3 to +6.5	V
	VLO6	COM0 to COM7	External resistance division method	-0.3 to VDD + 0.3 Note 2	V
		SEG0 to SEG55 output voltage	Capacitor split method	-0.3 to VDD + 0.3 Note 2	V
		output voltage	Internal voltage boosting method	-0.3 to VLI4 + 0.3 Note 2	V

- Note 1. This value only indicates the absolute maximum ratings when applying voltage to the VL1, VL2, VL3, and VL4 pins; it does not mean that applying voltage to these pins is recommended. When using the internal voltage boosting method or capacitance split method, connect these pins to Vss via a capacitor (0.47 ± 30%) and connect a capacitor (0.47 ± 30%) between the CAPL and CAPH pins.
- Note 2. Must be 6.5 V or lower.

Caution

Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

Absolute Maximum Ratings (TA = 25°C)

(3/3)

Parameter	Symbols		Conditions	Ratings	Unit
Output current, high	IOH1	Per pin	P00 to P07, P10 to P17, P20 to P27, P30 to P37, P40 to P46, P50 to P57, P70 to P77, P80 to P83, P125 to P127, P130, P140 to P143	-40	mA
		Total of all	P40 to P46	-70	mA
		pins -170 mA	P00 to P07, P10 to P17, P20 to P27, P30 to P37, P50 to P57, P70 to P77, P80 to P83, P125 to P127, P130, P140 to P143	-100	mA
	IOH2	Per pin	P150 to P156	-0.1	mA
		Total of all pins		-0.7	mA
	Іонз	Per pin	UDP, UDM	-3	mA
Output current, low	IOL1	Per pin	P00 to P07, P10 to P17, P20 to P27, P30 to P37, P40 to P46, P50 to P57, P60, P61, P70 to P77, P80 to P83, P125 to P127, P130, P140 to P143	40	mA
		Total of all	P40 to P46	70	mA
		pins 170 mA	P00 to P07, P10 to P17, P20 to P27, P30 to P37, P50 to P57, P70 to P77, P80 to P83, P125 to P127, P130, P140 to P143	100	mA
	IOL2	Per pin	P150 to P156	0.4	mA
		Total of all pins		2.8	mA
	IOL3	Per pin	UDP, UDM	3	mA
Operating ambient	ТА	In normal of	operation mode	-40 to +105	°C
temperature		In flash me	mory programming mode	-40 to +105	
Storage temperature	Tstg			-65 to +150	°C

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter.

That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

3.2 Oscillator Characteristics

3.2.1 X1 and XT1 oscillator characteristics

$(TA = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Resonator	Conditions	MIN.	TYP.	MAX.	Unit
X1 clock oscillation frequency (fx)	Ceramic resonator/crystal resonator	2.7 V ≤ VDD ≤ 3.6 V	1.0		20.0	MHz
Note		2.4 V ≤ VDD < 2.7 V	1.0		16.0	
XT1 clock oscillation frequency	Crystal resonator		32	32.768	35	kHz
(fxr) Note						

Note Indicates only permissible oscillator frequency ranges. Refer to AC Characteristics for instruction execution time.

Request evaluation by the manufacturer of the oscillator circuit mounted on a board to check the oscillator characteristics.

Caution Since the CPU is started by the high-speed on-chip oscillator clock after a reset release, check the X1 clock oscillation stabilization time using the oscillation stabilization time counter status register (OSTC) by the user.

Determine the oscillation stabilization time of the OSTC register and the oscillation stabilization time select register (OSTS) after sufficiently evaluating the oscillation stabilization time with the resonator to be used.

Remark When using the X1 and XT1 oscillator, refer to 5.4 System Clock Oscillator in the RL78/L1C User's Manual.

3.2.2 On-chip oscillator characteristics

$(TA = -40 \text{ to } +105^{\circ}C, 2.4 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, \text{Vss} = 0 \text{ V})$

Oscillators	Parameters	Conditions	MIN.	TYP.	MAX.	Unit
High-speed on-chip oscillator clock frequency Notes 1, 2	fHOCO		1		24	MHz
High-speed on-chip oscillator		-20 to +85°C	-1.0		+1.0	%
clock frequency accuracy		-40 to -20°C	-1.5		+1.5	%
		+85 to +105°C	-2.0		+2.0	%
Low-speed on-chip oscillator clock frequency	fiL			15		kHz
Low-speed on-chip oscillator clock frequency accuracy			-15		+15	%

Note 1. High-speed on-chip oscillator frequency is selected with bits 0 to 4 of the option byte (000C2H) and bits 0 to 2 of the HOCODIV register.

3.2.3 PLL oscillator characteristics

$(TA = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, \text{Vss} = 0 \text{ V})$

Oscillators	Parameters	Conditions	MIN.	TYP.	MAX.	Unit
PLL input frequency Note	fPLLIN	High-speed system clock	6.00		16.00	MHz
PLL output frequency Note	fPLL			48.00		MHz

Note Indicates only oscillator characteristics. Refer to AC Characteristics for instruction execution time.

Note 2. This only indicates the oscillator characteristics. Refer to AC Characteristics for instruction execution time.

3.3 DC Characteristics

3.3.1 Pin characteristics

$(TA = -40 \text{ to } +105^{\circ}C, 2.4 \text{ V} \le AVDD = VDD \le 3.6 \text{ V}, VSS = 0 \text{ V})$

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, high Note 1	IOH1	Per pin for P00 to P07, P10 to P17, P20 to P27, P30 to P37, P40 to P46, P50 to P57, P70 to P77, P80 to P83, P125 to P127, P130, P140 to P143				-3.0 Note 2	mA
		Total of P00 to P07, P10 to P17, P20 to P27, P30 to P37, P40 to P46, P50 to P57, P70 to P77, P80 to P83, P125 to P127, P130, P140 to P143	2.7 V ≤ VDD ≤ 3.6 V 2.4 V ≤ VDD < 2.7 V			-15.0 -7.0	mA mA
	ЮН2	(When duty ≤ 70% Note 3) Per pin for P150 to P156 Total of all pins	2.4 V ≤ VDD ≤ 3.6 V			-0.1 Note 2	mA mA

- **Note 1.** Value of current at which the device operation is guaranteed even if the current flows from the VDD pin to an output pin.
- Note 2. However, do not exceed the total current value.
- **Note 3.** Specification under conditions where the duty factor $\leq 70\%$.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

- Total output current of pins = $(IOH \times 0.7)/(n \times 0.01)$
- <Example> Where n = 80% and IOH = -10.0 mA

Total output current of pins = $(-10.0 \times 0.7)/(80 \times 0.01) \approx -8.7 \text{ mA}$

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

Caution P00 to P02, P10 to P12, P24 to P26, P33 to P35, and P42 to P44 do not output high level in N-ch open-drain mode.

 $(TA = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{AVDD} = \text{VDD} \le 3.6 \text{ V}, \text{Vss} = 0 \text{ V})$

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, low Note 1	IOL1	Per pin for P00 to P07, P10 to P17, P20 to P27, P30 to P37, P40 to P46, P50 to P57, P70 to P77, P80 to P83, P125 to P127, P130, P140 to P143				8.5 Note 2	mA
		Per pin for P60 and P61				15.0 Note 2	mA
		Total of P40 to P46, P130	2.7 V ≤ VDD ≤ 3.6 V			15.0	mA
		(When duty ≤ 70% Note 3)	2.4 V ≤ VDD < 2.7 V			9.0	mA
		Total of P00 to P07, P10 to P17, P20 to P27,	2.7 V ≤ VDD ≤ 3.6 V			35.0	mA
		P30 to P37, P50 to P57, P60, P61, P70 to P77, P80 to P83, P125 to P127, P140 to P143 (When duty ≤ 70% Note 3)	2.4 V ≤ VDD < 2.7 V			20.0	mA
		Total of all pins (When duty ≤ 70% ^{Note 3})				50.0	mA
	IOL2	Per pin for P150 to P156				0.4 Note 2	mA
		Total of all pins	2.4 V ≤ VDD ≤ 3.6 V			2.8	mA

- Note 1. Value of current at which the device operation is guaranteed even if the current flows from an output pin to the Vss pin.
- **Note 2.** However, do not exceed the total current value.
- **Note 3.** Specification under conditions where the duty factor $\leq 70\%$.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression

(when changing the duty factor from 70% to n%).

• Total output current of pins = $(IOL \times 0.7)/(n \times 0.01)$

<Example> Where n = 80% and IOL = 10.0 mA

Total output current of pins = $(10.0 \times 0.7)/(80 \times 0.01) \approx 8.7$ mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

(TA = -40 to +105°C, 2.4 V \leq AVDD = VDD \leq 3.6 V, Vss = 0 V)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Input voltage, high	VIH1	P00 to P07, P10 to P17, P20 to P27, P30 to P37, P40 to P46, P50 to P57, P70 to P77, P80 to P83, P125 to P127, P140 to P143	Normal input buffer	0.8 VDD		VDD	V
	VIH2	P00, P01, P10, P11, P24, P25, P33, P34, P43, P44	TTL input buffer 3.3 V ≤ VDD ≤ 3.6 V	2.0		VDD	V
			TTL input buffer 2.4 V ≤ VDD < 3.3 V	1.50		VDD	V
	VIH3	P150 to P156		0.7 AVDD		AVdd	V
	VIH4	P60, P61		0.7 VDD		6.0	V
	VIH5	P121 to P124, P137, EXCLK, EXCLKS,	0.8 VDD		Vdd	V	
Input voltage, low	VIL1	P00 to P07, P10 to P17, P20 to P27, P30 to P37, P40 to P46, P50 to P57, P70 to P77, P80 to P83, P125 to P127, P140 to P143	Normal input buffer	0		0.2 VDD	V
	VIL2	P00, P01, P10, P11, P24, P25, P33, P34, P43, P44	TTL input buffer 3.3 V ≤ VDD ≤ 3.6 V	0		0.5	V
			TTL input buffer 2.4 V ≤ VDD < 3.3 V	0		0.32	V
	VIL3	P150 to P156		0		0.3 AVDD	V
	VIL4	P60, P61		0		0.3 VDD	V
	VIL5	P121 to P124, P137, EXCLK, EXCLKS,	RESET	0		0.2 VDD	V

Caution The maximum value of VIH of pins P00 to P02, P10 to P12, P24 to P26, P33 to P35, and P42 to P44 is VDD, even in the N-ch open-drain mode.

(TA = -40 to +105°C, 2.4 V \leq AVDD = VDD \leq 3.6 V, Vss = 0 V)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output voltage, high	VoH1	P00 to P07, P10 to P17, P20 to P27, P30 to P37, P40 to P46, P50 to P57,	$2.7 \text{ V} \le \text{VDD} \le 3.6 \text{ V},$ IOH1 = -2.0 mA	VDD - 0.6			٧
		P70 to P77, P80 to P83, P125 to P127, P130, P140 to P143	2.4 V ≤ VDD ≤ 3.6 V, IOH1 = -1.5 mA	VDD - 0.5			٧
	VOH2	P150 to P156	$2.4 \text{ V} \leq \text{VDD} \leq 3.6 \text{ V},$ $\text{IOH2} = -100 \mu\text{A}$	AVDD - 0.5			V
Output voltage, low	VOL1	P00 to P07, P10 to P17, P20 to P27, P30 to P37, P40 to P46, P50 to P57,	$2.7 \text{ V} \le \text{VDD} \le 3.6 \text{ V},$ IOL1 = 3.0 mA			0.6	V
	P70 to P77, P80 to P83, P125 to P12 P130, P140 to P143	$2.4 \text{ V} \le \text{VDD} \le 3.6 \text{ V},$ IOL1 = 1.5 mA			0.4	V	
			$2.4 \text{ V} \le \text{VDD} \le 3.6 \text{ V},$ IOL1 = 0.6 mA			0.4	V
	VOL2	P150 to P156	$2.4 \text{ V} \leq \text{VDD} \leq 3.6 \text{ V},$ $\text{IOL2} = 400 \mu\text{A}$			0.4	V
	VOL3	P60, P61	$2.7 \text{ V} \le \text{VDD} \le 3.6 \text{ V},$ IOL3 = 3.0 mA			0.4	٧
			$2.4 \text{ V} \le \text{VDD} \le 3.6 \text{ V},$ IOL3 = 2.0 mA			0.4	٧

Caution P00 to P02, P10 to P12, P24 to P26, P33 to P35, and P42 to P44 do not output high level in N-ch open-drain mode.

(TA = -40 to +105°C, 2.4 V \leq AVDD = VDD \leq 3.6 V, Vss = 0 V)

Items	Symbol	Conditio	ns		MIN.	TYP.	MAX.	Unit
Input leakage current, high	ILIH1	P00 to P07, P10 to P17, P20 to P27, P30 to P37, P40 to P46, P50 to P57, P60, P61, P70 to P77, P80 to P83, P125 to P127, P137, P140 to P143, RESET	VI = VDD				1	μА
	ILIH2	P20, P21, P140 to P143	VI = VDD				1	μΑ
	ILIH3	P121 to P124 (X1, X2, EXCLK, XT1, XT2, EXCLKS)	VI = VDD	In input port or external clock input			1	μΑ
				In resonator connection			10	μΑ
	ILIH4	P150 to P156	VI = AVDI)			1	μA
Input leakage current, low	ILIL1	P00 to P07, P10 to P17, P20 to P27, P30 to P37, P40 to P46, P50 to P57, P60, P61, P70 to P77, P80 to P83, P125 to P127, P137, P140 to P143, RESET	VI = VSS				-1	μА
	ILIL2	P20, P21, P140 to P143	VI = VSS				-1	μΑ
	ILIL3	P121 to P124 (X1, X2, EXCLK, XT1, XT2, EXCLKS)	VI = VSS	In input port or external clock input			-1	μΑ
				In resonator connection			-10	μΑ
	ILIL4	P150 to P156	VI = AVSS	3			-1	μΑ
On-chip pull-up resistance	Ru1	P00 to P07, P10 to P17, P20 to P27, P30 to P37, P50 to P57, P70 to P77, P140 to P143, P125 to P127	VI = VSS	2.4 V ≤ VDD ≤ 3.6 V	10	20	100	kΩ
	Ru2	P40 to P46, P80 to P83	Vı = Vss		10	20	100	kΩ

3.3.2 Supply current characteristics

(TA = -40 to +105°C, 2.4 V \leq VDD \leq 3.6 V, Vss = 0 V)

(1/2)

Parameter	Symbol			Conditions			MIN.	TYP.	MAX.	Unit
Supply	IDD1	Operating	HS	fHOCO = 48 MHz Note 3,	Basic	VDD = 3.6 V		2.2	2.9	mA
current Note 1		mode	(high-speed main)	fIH = 24 MHz Note 3	operation	VDD = 3.0 V		2.2	2.9	
			mode Note 5		Normal	VDD = 3.6 V		4.4	9.2	
					operation	VDD = 3.0 V		4.4	9.2	
				fHOCO = 24 MHz Note 3,	Basic	VDD = 3.6 V		2.0	2.6	
				fIH = 24 MHz Note 3	operation	VDD = 3.0 V		2.0	2.6	
					Normal	VDD = 3.6 V		4.2	7.0	
					operation	VDD = 3.0 V		4.2	7.0	
				fHOCO = 16 MHz Note 3,	Normal	VDD = 3.6 V		3.1	5.0	
				fIH = 16 MHz Note 3	operation	VDD = 3.0 V		3.1	5.0	
			HS	fMX = 20 MHz Note 2,	Normal	Square wave input		3.5	5.9	mA
			(high-speed main)	VDD = 3.6 V	operation	Resonator connection		3.6	6.0	
			mode Note 5	fMX = 20 MHz Note 2,	Normal	Square wave input		3.5	5.9	
				VDD = 3.0 V	operation	Resonator connection		3.6	6.0	
				fMX = 16 MHz Note 2,	Normal	Square wave input		2.9	4.5	
				VDD = 3.6 V	operation	Resonator connection		3.1	4.6	
				fMX = 16 MHz Note 2,	Normal	Square wave input		2.9	4.5	
				VDD = 3.0 V	operation	Resonator connection		3.1	4.6	
				fMX = 10 MHz Note 2,	Normal	Square wave input		2.1	3.5	
				· ·	operation	Resonator connection		2.2	3.5	
				fMX = 10 MHz Note 2,	Normal	Square wave input		2.1	3.5	
				VDD = 3.0 V	operation	Resonator connection		2.2	3.5	
			HS	fPLL = 48 MHz,	Normal	VDD = 3.6 V		4.7	7.6	mA
			(High-speed main)	fCLK = 24 MHz Note 2	operation	VDD = 3.0 V		4.7	7.6	
			mode (PLL operation)	fPLL = 48 MHz,	Normal	VDD = 3.6 V		3.1	5.2	
			(== == ===============================	fCLK = 12 MHz Note 2	operation	VDD = 3.0 V		3.1	5.1	
				fPLL = 48 MHz,	Normal	VDD = 3.6 V		2.3	3.9	
				fCLK = 6 MHz Note 2	operation	VDD = 3.0 V		2.3	3.9	
			Subsystem clock	fSUB = 32.768 kHz Note 4	Normal	Square wave input		4.6	6.9	μΑ
			operation	TA = -40°C	operation	Resonator connection		4.7	6.9	
				fSUB = 32.768 kHz Note 4	Normal	Square wave input		4.9	7.0	
				TA = +25°C	operation	Resonator connection		5.0	7.2	
				fSUB = 32.768 kHz Note 4	Normal	Square wave input		5.2	7.6	
				TA = +50°C	operation	Resonator connection		5.2	7.7	
				fSUB = 32.768 kHz Note 4	Normal	Square wave input		5.5	9.3	
			TA = +70°C	operation	Resonator connection		5.6	9.4		
				Normal	Square wave input		6.2	13.3		
				operation	Resonator connection		6.2	13.4		
				fSUB = 32.768 kHz Note 4	Normal	Square wave input		8.3	46.0	
				TA = +105°C	operation	Resonator connection		8.4	46.0	

(Notes and Remarks are listed on the next page.)

- Note 1. Total current flowing into VDD, including the input leakage current flowing when the level of the input pin is fixed to VDD, or VSS. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the LCD controller/driver, A/D converter, D/A converter, comparator, LVD circuit, USB 2.0 function module, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
- **Note 2.** When high-speed on-chip oscillator and subsystem clock are stopped.
- **Note 3.** When high-speed system clock and subsystem clock are stopped.
- **Note 4.** When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the real-time clock 2, 12-bit interval timer, and watchdog timer.
- Note 5. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below. HS (high-speed main) mode: $2.7 \text{ V} \le \text{VDD} \le 3.6 \text{ V} @ 1 \text{ MHz}$ to 24 MHz $2.4 \text{ V} \le \text{VDD} \le 3.6 \text{ V} @ 1 \text{ MHz}$ to 16 MHz
- Remark 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
- Remark 2. fHOCO: High-speed on-chip oscillator clock frequency (48 MHz max.)
- Remark 3. fil: Main system clock source frequency when the high-speed on-chip oscillator clock divided 1, 2, 4, or 8, or the PLL clock divided by 2, 4, or 8 is selected (24 MHz max.)
- Remark 4. fSUB: Subsystem clock frequency (XT1 clock oscillation frequency)
- Remark 5. Except subsystem clock operation, temperature condition of the TYP. value is TA = 25°C

$(TA = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, \text{Vss} = 0 \text{ V})$

(2/2)

Parameter	Symbol	Conditions				MIN.	TYP.	MAX.	Unit
Supply	IDD2	HALT mode	HS (high-speed main)	fHOCO = 48 MHz Note 4,	VDD = 3.6 V		0.77	3.4	mA
current	Note 2		mode Note 7	fIH = 24 MHz Note 4	VDD = 3.0 V		0.77	3.4	
Note 1				fHOCO = 24 MHz Note 4,	VDD = 3.6 V		0.55	2.7	
				fiH = 24 MHz Note 4	VDD = 3.0 V		0.55	2.7	
				fHOCO = 16 MHz Note 4,	VDD = 3.6 V		0.48	1.9	
				fIH = 16 MHz Note 4	VDD = 3.0 V		0.47	1.9	
			HS (high-speed main)	fmx = 20 MHz Note 3,	Square wave input		0.35	2.10	mA
			mode Note 7	VDD = 3.6 V	Resonator connection		0.51	2.20	
				fmx = 20 MHz Note 3,	Square wave input		0.34	2.10	
				VDD = 3.0 V	Resonator connection		0.51	2.20	
				fmx = 16 MHz Note 3,	Square wave input		0.30	1.25	
				VDD = 3.6 V	Resonator connection		0.45	1.41	
				fmx = 16 MHz Note 3,	Square wave input		0.29	1.23	
				VDD = 3.0 V	Resonator connection		0.45	1.41	
				fmx = 10 MHz Note 3,	Square wave input		0.23	1.10	
				VDD = 3.6 V	Resonator connection		0.30	1.20	
				fmx = 10 MHz Note 3,	Square wave input		0.22	1.10	
				VDD = 3.0 V	Resonator connection		0.30	1.20	
			HS	fmx = 48 MHz,	VDD = 3.6 V		0.99	2.93	mA
			(High-speed main)	fCLK = 24 MHz Note 3	VDD = 3.0 V		0.99	2.92	
			mode (PLL operation)	fmx = 48 MHz,	VDD = 3.6 V		0.89	2.51	
			(i LL oporation)	fCLK = 12 MHz Note 3	VDD = 3.0 V		0.89	2.50	
				fmx = 48 MHz,	VDD = 3.6 V		0.84	2.30	
				fCLK = 6 MHz Note 3	VDD = 3.0 V		0.84	2.29	
			Subsystem clock	fSUB = 32.768 kHz Note 5	Square wave input		0.32	0.61	μΑ
			operation	TA = -40°C	Resonator connection		0.51	0.80	
				fSUB = 32.768 kHz Note 5	Square wave input		0.41	0.74	
				TA = +25°C	Resonator connection		0.62	0.91	
				fSUB = 32.768 kHz Note 5	Square wave input		0.52	2.30	
				TA = +50°C	Resonator connection		0.75	2.49	
				fSUB = 32.768 kHz Note 5	Square wave input		0.82	4.03	
				TA = +70°C	Resonator connection		1.08	4.22	
				fSUB = 32.768 kHz Note 5	Square wave input		1.38	8.04	
				TA = +85°C	Resonator connection		1.62	8.23	
				fsub = 32.768 kHz Note 5	Square wave input		3.29	41.00	
				TA = +105°C	Resonator connection		3.63	41.00	
	IDD3	STOP mode	T _A = -40°C	•	-		0.18	0.52	μΑ
	Note 6	Note 8	T _A = +25°C				0.25	0.52	
			T _A = +50°C				0.34	2.21	
			T _A = +70°C				0.64	3.94	
			T _A = +85°C				1.18	7.95	
			T _A = +105°C				2.92	40.00	

(Notes and Remarks are listed on the next page.)

- Note 1. Total current flowing into VDD, including the input leakage current flowing when the level of the input pin is fixed to VDD or VSS. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the LCD controller/driver, A/D converter, D/A converter, comparator, LVD circuit, USB 2.0 function module, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
- Note 2. During HALT instruction execution by flash memory.
- Note 3. When high-speed on-chip oscillator and subsystem clock are stopped.
- Note 4. When high-speed system clock and subsystem clock are stopped.
- Note 5. When high-speed on-chip oscillator and high-speed system clock are stopped. When RTCLPC = 1 and setting ultra-low current consumption (AMPHS1 = 1). The current flowing into the real-time clock 2 is included. However, not including the current flowing into the 12-bit interval timer and watchdog timer.
- Note 6. Not including the current flowing into the real-time clock 2, 12-bit interval timer, and watchdog timer.
- Note 7. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

 HS (high-speed main) mode: 2.7 V ≤ VDD ≤ 3.6 V@1 MHz to 24 MHz
 - $2.4 \text{ V} \leq \text{VDD} \leq 3.6 \text{ V}@1 \text{ MHz}$ to 16 MHz
- Note 8. Regarding the value for current to operate the subsystem clock in STOP mode, refer to that in HALT mode.
- Remark 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
- Remark 2. fHOCO: High-speed on-chip oscillator clock frequency (48 MHz max.)
- Remark 3. flH: Main system clock source frequency when the high-speed on-chip oscillator clock divided 1, 2, 4, or 8, or the PLL clock divided by 2, 4, or 8 is selected (24 MHz max.)
- Remark 4. fSUB: Subsystem clock frequency (XT1 clock oscillation frequency)
- Remark 5. Except subsystem clock operation, temperature condition of the TYP. value is TA = 25°C

(TA = -40 to +105°C, 2.4 V \leq VDD \leq 3.6 V, Vss = 0 V)

Parameter	Symbol		Condition	ons		MIN.	TYP.	MAX.	Unit
Low-speed on-chip oscillator operating current	IFIL Note 1						0.20		μA
RTC2 operating current	IRTC Notes 1, 3						0.02		μA
12-bit interval timer operating current	ITMKA Notes 1, 2, 4						0.02		μA
Watchdog timer operating current	IWDT Notes 1, 2, 5	fIL = 15 kHz					0.22		μA
A/D converter operating current	IADC Notes 6, 7	AVDD = 3.0 V, whe	n conversion at maximu	ım speed			422	720	μA
AVREF (+) current	IAVREF Note 8	AVDD = 3.0 V, ADR	EFP1 = 0, ADREFP0 =	0 Note 7			14.0	25.0	μA
		AVREFP = 3.0 V, AL	DREFP1 = 0, ADREFP0	= 1 Note 10			14.0	25.0	
A (D		ADREFP1 = 1, AD	REFP0 = 0 Note 1				14.0	25.0	
A/D converter reference voltage current	IADREF Notes 1, 9	VDD = 3.0 V					75.0		μA
Temperature sensor operating current	ITMPS Note 1						78		μA
D/A converter operating current	IDAC Notes 1, 11	Per D/A converter	channel				0.53	1.5	mA
Comparator	ICMP	VDD = 3.6 V,	Window mode				12.5		μΑ
operating current	Notes 1, 12	Regulator output voltage = 2.1 V	Comparator high-spee				4.5		μA
			Comparator low-speed	d mode			1.2		μA
LVD operating current	ILVD Notes 1, 13						0.06		μA
Self-programming operating current	IFSP Notes 1, 14						2.50	12.20	mA
BGO operating current	IBGO Notes 1, 15						1.68	12.20	mA
SNOOZE	ISNOZ Note 1	ADC operation	The mode is performe	d Note 16			0.34	1.10	mA
operating current			The A/D conversion opmode, AVREFP = VDD	•	erformed, Low voltage		0.53	2.04	
		Simplified SPI (CS	I)/UART operation				0.70	1.54	mA
LCD operating current	ILCD1 Notes 17, 18	External resistance division method	fLCD = fSUB LCD clock = 128 Hz	1/3 bias 4-time slice	VDD = 3.6 V, LV4 = 3.6 V		0.14		μA
	ILCD2 Note 17	Internal voltage boosting method	fLCD = fSUB LCD clock = 128 Hz	1/3 bias 4-time slice	VDD = 3.0 V, LV4 = 3.0 V (VLCD = 04H)		0.61		μA
	ILCD3 Note 17	Capacitor split method	fLCD = fSUB LCD clock = 128 Hz	1/3 bias 4-time slice	VDD = 3.0 V, LV4 = 3.0 V		0.12		μA
USB current	IUSB Note 20	Operating current	Operating current during USB communication						mA
Note 19	IUSB Note 21	Operating current in the USB suspended state					0.04		mA

(Notes and Remarks are listed on the next page.)



- Note 1. Current flowing to VDD.
- Note 2. When high speed on-chip oscillator and high-speed system clock are stopped.
- Note 3. Current flowing only to the real-time clock 2 (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IRTC, when the real-time clock 2 operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, IFIL should be added. IDD2 subsystem clock operation includes the operational current of the real-time clock 2.
- Note 4. Current flowing only to the 12-bit interval timer (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and ITMKA, when the 12-bit interval timer operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, IFIL should be added. IDD2 subsystem clock operation includes the operational current of the 12-bit interval timer.
- Note 5. Current flowing only to the watchdog timer (including the operating current of the low-speed on-chip oscillator). The current value of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and IWDT when the watchdog timer operates in STOP mode
- Note 6. Current flowing only to the A/D converter. The supply current of the RL78 microcontrollers is the sum of IDD1 or IDD2 and IADC, IAVREF, IADREF when the A/D converter operates in an operation mode or the HALT mode.
- Note 7. Current flowing to the AVDD.
- **Note 8.** Current flowing from the reference voltage source of A/D converter.
- **Note 9.** Operation current flowing to the internal reference voltage.
- Note 10. Current flowing to the AVREFP.
- **Note 11.** Current flowing only to the D/A converter. The current value of the RL78 microcontrollers is the sum of IDD1 or IDD2 and IDA when the D/A converter operates in an operation mode or the HALT mode.
- **Note 12.** Current flowing only to the comparator circuit. The current value of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and ICMP when the comparator circuit operates in the Operating, HALT or STOP mode.
- **Note 13.** Current flowing only to the LVD circuit. The current value of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and ILVI when the LVD circuit operates in the Operating, HALT or STOP mode.
- Note 14. Current flowing only during self-programming.
- Note 15. Current flowing only during data flash rewrite.
- Note 16. For shift time to the SNOOZE mode, see 23.3.3 SNOOZE mode in the RL78/L1C User's Manual...
- Note 17. Current flowing only to the LCD controller/driver (VDD pin). The current value of the RL78 microcontrollers is the sum of the LCD operating current (ILCD1, ILCD2 or ILCD3) to the supply current (IDD1, or IDD2) when the LCD controller/driver operates in an operation mode or HALT mode. Not including the current that flows through the LCD panel.
- Note 18. Not including the current that flows through the external divider resistor divider resistor.
- Note 19. Current flowing to the UVBUS.
- **Note 20.** Including the operating current when fPLL = 48 MHz.
- **Note 21.** Including the current supplied from the pull-up resistor of the UDP pin to the pull-down resistor of the host device, in addition to the current consumed by this MCU during the suspended state.
- Remark 1. fil: Low-speed on-chip oscillator clock frequency
- Remark 2. fSUB: Subsystem clock frequency (XT1 clock oscillation frequency)
- Remark 3. fclk: CPU/peripheral hardware clock frequency
- Remark 4. Temperature condition of the TYP. value is TA = 25°C



3.4 AC Characteristics

3.4.1 Basic operation

$(TA = -40 \text{ to } +105^{\circ}C, 2.4 \text{ V} \le AVDD = VDD \le 3.6 \text{ V}, VSS = 0 \text{ V})$

(1/2)

Items	Symbol	Conditions			MIN.	TYP.	MAX.	Unit
Instruction cycle	Tcy	Main system	HS (high-speed main)	2.7 V ≤ VDD ≤ 3.6 V	0.0417		1	μs
(minimum instruction execution time)		clock (fMAIN) operation	mode	2.4 V ≤ VDD < 2.7 V	0.0625		1	μs
		Subsystem clo	ock (fsub) operation	2.4 V ≤ VDD ≤ 3.6 V	28.5	30.5	31.3	μs
		In the self-	HS (high-speed main)	2.7 V ≤ VDD ≤ 3.6 V	0.0417		1	μs
		programming mode	mode	2.4 V ≤ VDD < 2.7 V	0.0625		1	μs
External main system clock frequency	fEX	2.7 V ≤ VDD ≤ 3.6 V		1.0		20.0	MHz	
		2.4 V ≤ VDD < 2.7 V			1.0		16.0	MHz
	fEXT				32		35	kHz
External main system clock input high-level width, low-level width	texH,	2.7 V ≤ VDD ≤	3.6 V		24			ns
	tEXL	2.4 V ≤ VDD <	2.7 V		30			ns
	tEXHS, tEXLS				13.7			μs
TI00 to TI07 input high-level width, low-level width	ttih, ttil				1/fмск + 10			ns

Remark fMCK: Timer array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of timer mode register mn (TMRmn). m: Unit number (m = 0),

n: Channel number (n = 0 to 7))

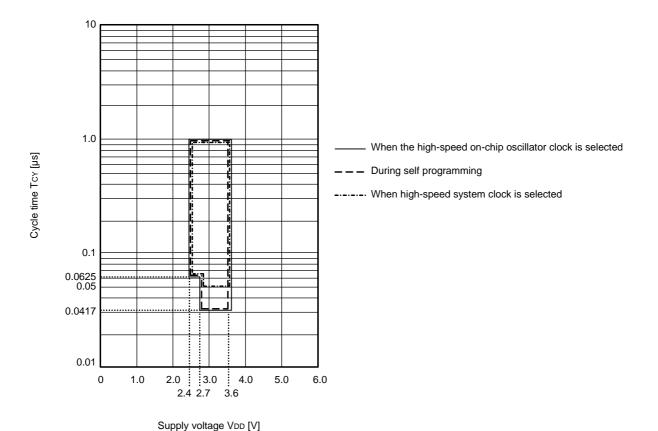
(TA = -40 to +105°C, 2.4 V \leq AVDD = VDD \leq 3.6 V, Vss = 0 V)

(2/2)

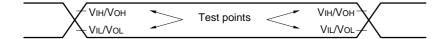
Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
TO00 to TO07, TKBO00,	fto	HS (high-speed main) mode	2.7 V ≤ VDD ≤ 3.6 V			8	MHz
TKBO01, TKBO10, TKBO11,			2.4 V ≤ VDD < 2.7 V			8	MHz
TKBO20, TKBO21							
output frequency							
PCLBUZ0, PCLBUZ1 output	fPCL	HS (high-speed main) mode	$2.7 \text{ V} \leq \text{VDD} \leq 3.6 \text{ V}$			8	MHz
frequency			$2.4 \text{ V} \leq \text{VDD} < 2.7 \text{ V}$			8	MHz
Interrupt input high-level width,	tinth,	INTP0 to INTP7	2.4 V ≤ VDD ≤ 3.6 V	1			μs
low-level width	tintl						
Key interrupt input low-level	tkr	2.4 V ≤ VDD ≤ 3.6 V		250			ns
width							
TMKB2 forced output stop input	tihr	INTP0 to INTP7	fclk > 16 MHz	125			ns
high-level width			fclk ≤ 16 MHz	2			fCLK
RESET low-level width	trsl		•	10			μs

Minimum Instruction Execution Time during Main System Clock Operation

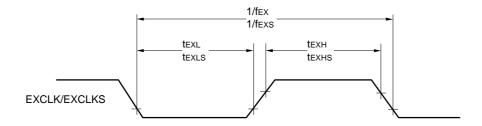
TCY vs VDD (HS (high-speed main) mode)



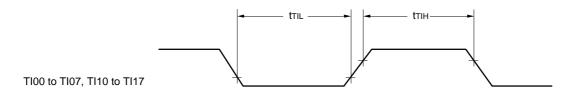
AC Timing Test Points

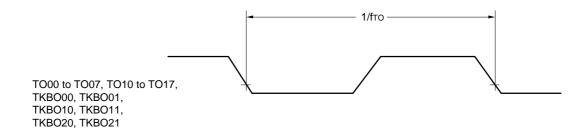


External System Clock Timing

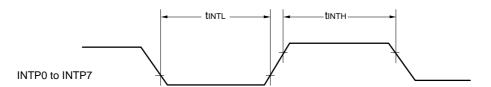


TI/TO Timing

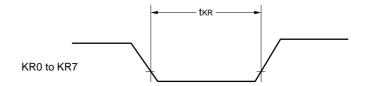




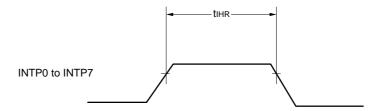
Interrupt Request Input Timing



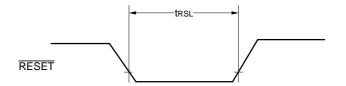
Key Interrupt Input Timing



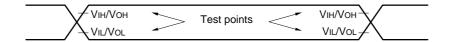
Timer KB2 Input Timing



RESET Input Timing



3.5 Peripheral Functions Characteristics



3.5.1 Serial array unit

(1) During communication at same potential (UART mode)

 $(TA = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	HS (high-spee	Unit	
		Conditions	MIN.	MAX.	Offic
Transfer rate Note 1		2.4 V ≤ VDD ≤ 3.6 V		fMCK/12 Note 2	bps
		Theoretical value of the maximum transfer rate fMCK = fCLK Note 3		2.0	Mbps

- Note 1. Transfer rate in the SNOOZE mode is 4800 bps only.
- Note 2. The following conditions are required for low voltage interface.

 $2.4 \text{ V} \leq \text{VDD} < 2.7 \text{ V: MAX. } 1.3 \text{ Mbps}$

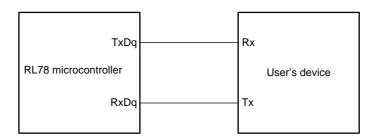
Note 3. The maximum operating frequencies of the CPU/peripheral hardware clock (fclk) are:

HS (high-speed main) mode: 24 MHz (2.7 V \leq VDD \leq 3.6 V)

16 MHz (2.4 V \leq VDD \leq 3.6 V)

Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

UART mode connection diagram (during communication at same potential)



UART mode bit width (during communication at same potential) (reference)



Remark 1. q: UART number (q = 0 to 3), g: PIM and POM number (g = 0 to 3)

Remark 2. fMCK: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00 to 03, 10 to 13))

(2) During communication at same potential (Simplified SPI (CSI) mode) (master mode, SCKp... internal clock output)

$(TA = -40 \text{ to } +105^{\circ}C, 2.4 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions		HS (high-spee	Unit		
Falametei	Symbol		Conditions		MAX.	Offic	
SCKp cycle time	tKCY1	tkcy1 ≥ fclk/4	2.7 V ≤ VDD ≤ 3.6 V	250		ns	
			2.4 V ≤ VDD ≤ 3.6 V	500		ns	
SCKp high-/low-level width	tKH1, tKL1	2.7 V ≤ VDD ≤ 3.6 V		tKCY1/2 - 36		ns	
		2.4 V ≤ VDD ≤ 3.6 V		tKCY1/2 - 76		ns	
SIp setup time (to SCKp↑) Note 1	tSIK1	2.7 V ≤ VDD ≤ 3.6 V		66		ns	
		2.4 V ≤ VDD ≤ 3.6 V		133		ns	
SIp hold time (from SCKp↑) Note 2	tKSI1			38		ns	
Delay time from SCKp↓ to SOp output Note 3	tKSO1	C = 30 pF Note 4			50	ns	

- Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from $SCKp\uparrow$ " when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 4. C is the load capacitance of the SCKp and SOp output lines.
- Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).
- **Remark 1.** p: CSI number (p = 00, 10, 20, 30), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM number (g = 0 to 3)
- Remark 2. fmck: Serial array unit operation clock frequency
 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,
 n: Channel number (mn = 00 to 03, 10 to 13))

(3) During communication at same potential (Simplified SPI (CSI) mode) (slave mode, SCKp... external clock input)

$(TA = -40 \text{ to } +105^{\circ}C, 2.4 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, \text{VSS} = 0 \text{ V})$

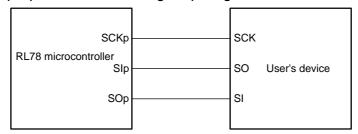
Parameter	Symbol	Cond	itions	HS (high-speed	main) Mode	Unit	
Falametei	Symbol	Cond	IIIOIIS	MIN.	MAX.	Offic	
SCKp cycle time Note 5	tKCY2	2.7 V ≤ VDD < 3.6 V	fMCK > 16 MHz	16/fMCK		ns	
			fMCK ≤ 16 MHz	12/fMCK		ns	
	2.4 V ≤ VDD < 3.6 V			12/fмск and 1000		ns	
SCKp high-/low-level width	w-level width t_{KH2} , t_{KL2} $2.7 \text{ V} \leq \text{VDD} \leq 3.6 \text{ V}$		tKCY2/2 - 16		ns		
		2.4 V ≤ VDD ≤ 3.6 V		tKCY2/2 - 36		ns	
SIp setup time (to SCKp↑) Note 1	tSIK2	2.7 V ≤ VDD ≤ 3.6 V		1/fmck + 40		ns	
		2.4 V ≤ VDD ≤ 3.6 V		1/fмcк + 60		ns	
SIp hold time (from SCKp↑) Note 2	tKSI2			1/fмcк + 62		ns	
Delay time from SCKp↓ to SOp output Note 3	tKSO2	C = 30 pF Note 4	2.7 V ≤ VDD ≤ 3.6 V		2/fмск + 66	ns	
			2.4 V ≤ VDD < 3.6 V		2/fmck + 113	ns	

- Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 4. C is the load capacitance of the SOp output lines.
- **Note 5.** The maximum transfer rate when using the SNOOZE mode is 1 Mbps.
- Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).
- **Remark 1.** p: CSI number (p = 00, 10, 20, 30), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM number (g = 0 to 3)
- Remark 2. fmck: Serial array unit operation clock frequency

 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

 n: Channel number (mn = 00 to 03, 10 to 13))

Simplified SPI (CSI) mode connection diagram (during communication at same potential)

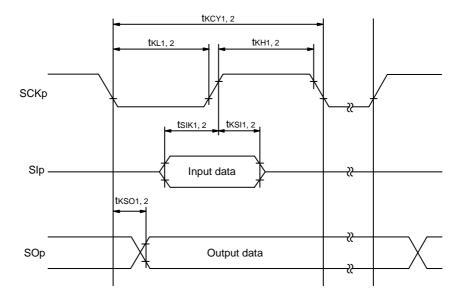


Remark 1. p: CSI number (p = 00, 10, 20, 30)

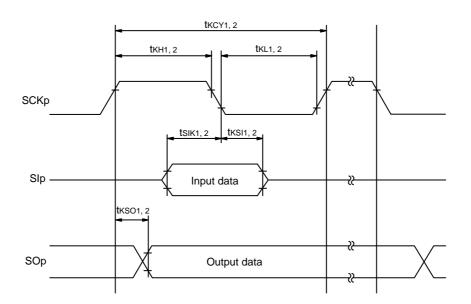
Remark 2. m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13)



Simplified SPI (CSI) mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



Simplified SPI (CSI) mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remark 1. p: CSI number (p = 00, 10, 20, 30)

Remark 2. m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13)

(4) During communication at same potential (simplified I²C mode)

 $(TA = -40 \text{ to } +105^{\circ}C, 2.4 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, \text{Vss} = 0 \text{ V})$

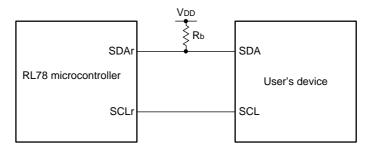
Danamatan	O. mah al	O a madistica a a	HS (high-speed	main) Mode	Unit
Parameter	Symbol	Conditions	MIN.	MAX.	Unit
SCLr clock frequency	fSCL	2.7 V ≤ VDD ≤ 3.6 V, Cb = 50 pF, Rb = 2.7 kΩ		400 Note 1	kHz
		2.4 V \leq VDD \leq 3.6 V, Cb = 100 pF, Rb = 3 kΩ		100 Note 1	kHz
Hold time when SCLr = "L"	tLOW	$2.7 \text{ V} \le \text{VDD} \le 3.6 \text{ V},$ $C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega$	1200		ns
		2.4 V ≤ VDD ≤ 3.6 V, Cb = 100 pF, Rb = 3 kΩ	4600		ns
Hold time when SCLr = "H"	tHIGH	$2.7 \text{ V} \le \text{VDD} \le 3.6 \text{ V},$ Cb = 50 pF, Rb = 2.7 k Ω	1200		ns
		2.4 V ≤ VDD ≤ 3.6 V, Cb = 100 pF, Rb = 3 kΩ	4600		ns
Data setup time (reception)	tsu: dat	2.7 V ≤ VDD ≤ 3.6 V, Cb = 50 pF, Rb = 2.7 kΩ	1/fMCK + 200 Note 2		ns
		2.4 V \leq VDD \leq 3.6 V, Cb = 100 pF, Rb = 3 kΩ	1/fMCK + 580 Note 2		ns
Data hold time (transmission)	thd: dat	$2.7 \text{ V} \le \text{VDD} \le 3.6 \text{ V},$ $C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega$	0	770	ns
		2.4 V ≤ V _{DD} ≤ 3.6 V, C _b = 100 pF, R _b = 3 kΩ	0	1420	ns

Note 1. The value must be equal to or less than fMCK/4.

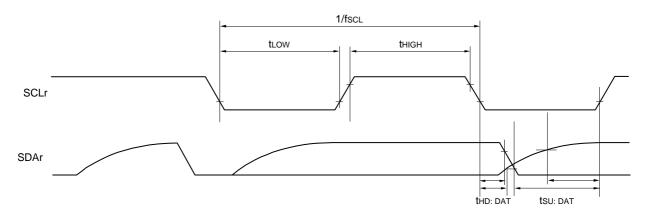
Note 2. Set the fMCK value to keep the hold time of SCLr = "L" and SCLr = "H".

Caution Select the normal input buffer and the N-ch open drain output (VDD tolerance) mode for the SDAr pin and the normal output mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register h (POMh).

Simplified I²C mode connection diagram (during communication at same potential)



Simplified I²C mode serial transfer timing (during communication at same potential)



- Remark 1. Rb[Ω]: Communication line (SDAr) pull-up resistance, Cb[F]: Communication line (SDAr, SCLr) load capacitance
- $\textbf{Remark 2.} \ \ \text{r: IIC number (r = 00, 10, 20, 30), g: PIM number (g = 0 to 3),}$

h: POM number (h = 0 to 3)

Remark 3. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0, 1),

n: Channel number (n = 0 to 3), mn = 00 to 03, 10 to 13)

(5) Communication at different potential (1.8 V, 2.5 V) (UART mode)

$(TA = -40 \text{ to } +105^{\circ}C, 2.4 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, \text{VSS} = 0 \text{ V})$

(1/2)

Parameter	Symbol			Conditions	HS (high-	speed main) Mode	Unit
raianietei	Syllibol			Conditions	MIN.	MAX.	Offic
Transfer rate Notes 1, 2			2.7 V ≤ VDD ≤ 3.6 V, 2.3 V ≤ Vb ≤ 2.7 V			fMCK/12 Note 1	bps
				Theoretical value of the maximum transfer rate fmck = fclk Note 4		2.0	Mbps
				V ≤ VDD < 3.3 V, V ≤ Vb ≤ 2.0 V		fMCK/12 Notes 1, 2, 3	bps
		Theoretical value of the maximum transfer rate fmck = fclk Note 4		1.3	Mbps		

- Note 1. Transfer rate in the SNOOZE mode is 4,800 bps only.
- **Note 2.** Use it with $VDD \ge Vb$.
- **Note 3.** The following conditions are required for low voltage interface.

 $2.4 \text{ V} \leq \text{VDD} < 2.7 \text{ V}$: MAX. 2.6 Mbps

Note 4. The maximum operating frequencies of the CPU/peripheral hardware clock (fclk) are:

HS (high-speed main) mode: 24 MHz (2.7 V \leq VDD \leq 3.6 V) 16 MHz (2.4 V \leq VDD \leq 3.6 V)

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the

DC characteristics with TTL input buffer selected.

- Remark 1. Vb[V]: Communication line voltage
- Remark 2. q: UART number (q = 0 to 3), g: PIM and POM number (g = 0 to 3)
- Remark 3. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00 to 03, 10 to 13))

(5) Communication at different potential (1.8 V, 2.5V) (UART mode)

$(TA = -40 \text{ to } +105^{\circ}C, 2.4 \le VDD \le 3.6 \text{ V}, VSS = 0 \text{ V})$

(2/2)

Parameter	Symbol			Conditions	HS (high-	Unit	
raiametei	Syllibol		_	Conditions	MIN.	MAX.	Offic
Transfer rate Note 2		Transmission		$V \le VDD \le 3.6 V$, $V \le Vb \le 2.7 V$		Note 1	bps
				Theoretical value of the maximum transfer rate $Cb = 50$ pF, $Rb = 2.7$ k Ω , $Vb = 2.3$ V		1.2 Note 2	Mbps
				V ≤ VDD < 3.3 V, V ≤ Vb ≤ 2.0 V		Notes 3, 4	bps
				Theoretical value of the maximum transfer rate $Cb = 50 \ pF, \ Rb = 5.5 \ k\Omega, \ Vb = 1.6 \ V$		0.43 Note 5	Mbps

Note 1. The smaller maximum transfer rate derived by using fMCK/6 or the following expression is the valid maximum transfer rate. Expression for calculating the transfer rate when $2.7 \text{ V} \le \text{VDD} < 3.6 \text{ V}$ and $2.3 \text{ V} \le \text{Vb} \le 2.7 \text{ V}$

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{2.0}{V_b})\} \times 3}$$
 [bps]

Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.0}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 [\%]$$

- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- **Note 2.** This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 1 above to calculate the maximum transfer rate under conditions of the customer.
- **Note 3.** Use it with $VDD \ge V_b$.
- Note 4. The smaller maximum transfer rate derived by using fMCK/6 or the following expression is the valid maximum transfer rate. Expression for calculating the transfer rate when 2.4 V \leq VDD < 3.3 V and 1.6 V \leq Vb \leq 2.0 V

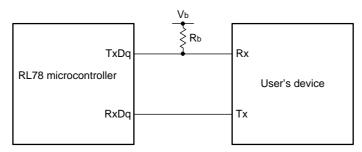
Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{1.5}{V_b})\} \times 3}$$
 [bps]

Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-\text{Cb} \times \text{Rb} \times \text{In} (1 - \frac{1.5}{\text{Vb}})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \, [\%]$$

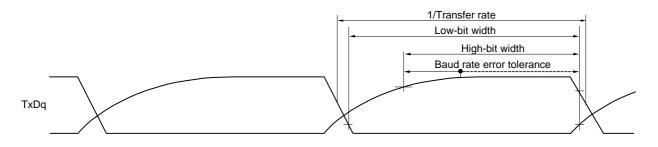
- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- **Note 5.** This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 4 above to calculate the maximum transfer rate under conditions of the customer.
- Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

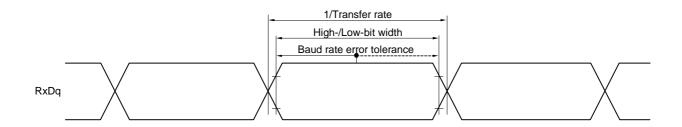


UART mode connection diagram (during communication at different potential)



UART mode bit width (during communication at different potential) (reference)





- Remark 1. $Rb[\Omega]$: Communication line (TxDq) pull-up resistance, Cb[F]: Communication line (TxDq) load capacitance, Vb[V]: Communication line voltage
- Remark 2. q: UART number (q = 0 to 3), g: PIM and POM number (g = 0 to 3)
- Remark 3. fmck: Serial array unit operation clock frequency
 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,
 n: Channel number (mn = 00 to 03, 10 to 13))

(6) Communication at different potential (1.8 V, 2.5 V) (Simplified SPI (CSI) mode) (master mode, SCKp... internal clock output)

 $(TA = -40 \text{ to } +105^{\circ}C, 2.4 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, \text{Vss} = 0 \text{ V})$

(1/2)

Parameter	Symbol		Conditions	HS (high-speed	d main) Mode	Unit
Farameter	Symbol		Conditions	MIN.	MAX.	Onit
SCKp cycle time	ne tkcy1 tkcy1		tkCY1 ≥ fCLK/4 2.7 V ≤ VDD ≤ 3.6 V, 2.3 V ≤ Vb ≤ 2.7 V, Cb = 30 pF, Rb = 2.7 kΩ			ns
			$2.4 \text{ V} \le \text{VDD} < 3.3 \text{ V}, 1.6 \text{ V} \le \text{Vb} \le 1.8 \text{ V},$ Cb = 30 pF, Rb = 5.5 kΩ	2300 Note		ns
SCKp high-level width	tKH1	2.7 V ≤ VDD ≤ 3 Cb = 30 pF, Rb	3.6 V, 2.3 V \leq Vb \leq 2.7 V, = 2.7 k Ω	tKCY1/2 - 340		ns
		$2.4 \text{ V} \le \text{VDD} < 3.3 \text{ V}, 1.6 \text{ V} \le \text{Vb} \le 2.0 \text{ V},$ Cb = 30 pF, Rb = 5.5 kΩ		tKCY1/2 - 916		ns
SCKp low-level width	tKL1	$2.7 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, 2.3 \text{ V} \le \text{Vb} \le 2.7 \text{ V},$ Cb = 30 pF, Rb = 2.7 k Ω		tKCY1/2 - 36		ns
		2.4 V ≤ VDD < 3 Cb = 30 pF, Rb	3.3 V, 1.6 V ≤ V _b ≤ 2.0 V, = 5.5 kΩ	tKCY1/2 - 100		ns

Note Use it with $VDD \ge Vb$.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the page after the next page.)

(6) Communication at different potential (1.8 V, 2.5 V) (Simplified SPI (CSI) mode) (master mode, SCKp... internal clock output)

 $(TA = -40 \text{ to } +105^{\circ}C, 2.4 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, \text{Vss} = 0 \text{ V})$

(2/2)

Parameter	Symbol	Conditions	, ,	peed main) ode	Unit	
			MIN.	MAX.		
SIp setup time (to SCKp↑) Note 1	tSIK1	$2.7 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, 2.3 \text{ V} \le \text{Vb} \le 2.7 \text{ V},$ $Cb = 30 \text{ pF}, Rb = 2.7 \text{ k}\Omega$	354		ns	
		$2.4 \text{ V} \le \text{VDD} < 3.3 \text{ V}, 1.6 \text{ V} \le \text{Vb} \le 2.0 \text{ V}$ Note 3, $Cb = 30 \text{ pF}, Rb = 5.5 \text{ k}\Omega$	958		ns	
SIp hold time (from SCKp↑) Note 1	tKSI1	$2.7 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, 2.3 \text{ V} \le \text{Vb} \le 2.7 \text{ V},$ $Cb = 30 \text{ pF}, Rb = 2.7 \text{ k}\Omega$	38		ns	
		$2.4 \text{ V} \le \text{VDD} < 3.3 \text{ V}, 1.6 \text{ V} \le \text{Vb} \le 2.0 \text{ V} \text{ Note } 3,$ $C_b = 30 \text{ pF}, R_b = 5.5 \text{ k}\Omega$	38		ns	
Delay time from SCKp↓ to SOp output Note 1	tKSO1	$2.7 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, 2.3 \text{ V} \le \text{Vb} \le 2.7 \text{ V},$ $Cb = 30 \text{ pF}, Rb = 2.7 \text{ k}\Omega$		390	ns	
		$2.4 \text{ V} \leq \text{VDD} < 3.3 \text{ V}, \ 1.6 \text{ V} \leq \text{V}_b \leq 2.0 \text{ V} \text{ Note } 3, \\ C_b = 30 \text{ pF}, \ R_b = 5.5 \text{ k}\Omega$		966	ns	
SIp setup time (to SCKp↓) Note 2	tSIK1	$2.7 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, 2.3 \text{ V} \le \text{Vb} \le 2.7 \text{ V},$ $Cb = 30 \text{ pF}, Rb = 2.7 \text{ k}\Omega$	88		ns	
		$2.4 \text{ V} \leq \text{VDD} < 3.3 \text{ V}, \ 1.6 \text{ V} \leq \text{V}_b \leq 2.0 \text{ V} \text{ Note } 3, \\ C_b = 30 \text{ pF}, \ R_b = 5.5 \text{ k}\Omega$	220		ns	
SIp hold time (from SCKp↓) Note 2	tKSI1	$2.7 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, 2.3 \text{ V} \le \text{Vb} \le 2.7 \text{ V},$ $Cb = 30 \text{ pF}, Rb = 2.7 \text{ k}\Omega$	38		ns	
		$2.4 \text{ V} \le \text{VDD} < 3.3 \text{ V}, 1.6 \text{ V} \le \text{Vb} \le 2.0 \text{ V} \text{ Note } 3,$ $C_b = 30 \text{ pF}, R_b = 5.5 \text{ k}\Omega$	38		ns	
Delay time from SCKp↑ to SOp output Note 2	tKSO1	$2.7 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, 2.3 \text{ V} \le \text{Vb} \le 2.7 \text{ V},$ $Cb = 30 \text{ pF}, Rb = 2.7 \text{ k}\Omega$		50	ns	
		$2.4 \text{ V} \leq \text{VDD} < 3.3 \text{ V}, \ 1.6 \text{ V} \leq \text{V}_b \leq 2.0 \text{ V} \text{ Note 3}, \\ C_b = 30 \text{ pF}, \ R_b = 5.5 \text{ k}\Omega$		50	ns	

Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

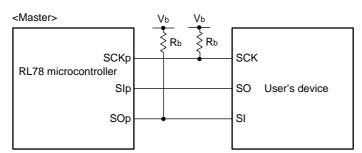
Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the next page.)

Note 2. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

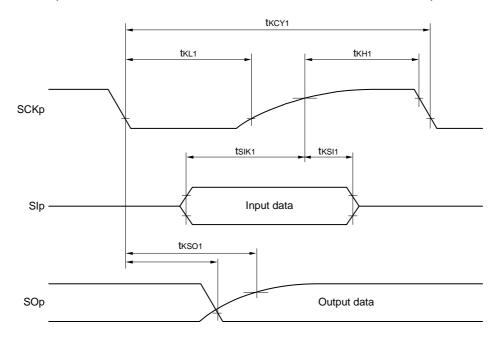
Note 3. Use it with $VDD \ge V_b$.

Simplified SPI (CSI) mode connection diagram (during communication at different potential)

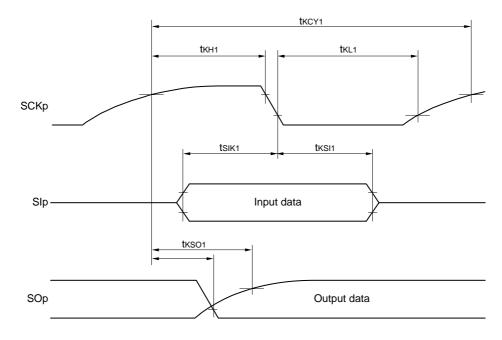


- Remark 1. $Rb[\Omega]$: Communication line (SCKp, SOp) pull-up resistance, Cb[F]: Communication line (SCKp, SOp) load capacitance, Vb[V]: Communication line voltage
- **Remark 2.** p: CSI number (p = 00, 10, 20, 30), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM and POM number (g = 0 to 3)
- Remark 3. fMCK: Serial array unit operation clock frequency
 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,
 n: Channel number (mn = 00))

Simplified SPI (CSI) mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



Simplified SPI (CSI) mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remark p: CSI number (p = 00, 10, 20, 30), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM and POM number (g = 0 to 3)

(7) Communication at different potential (1.8 V, 2.5 V) (Simplified SPI (CSI) mode) (slave mode, SCKp... external clock input)

 $(TA = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, \text{Vss} = 0 \text{ V})$

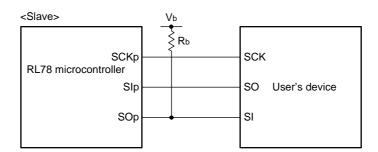
Demonstra	0	0.55	ditions	HS (high-spe	ed main) Mode	11-4
Parameter	Symbol	Con	uitions	MIN.	MAX.	Unit
SCKp cycle time Note 1	tKCY2	2.7 V ≤ VDD ≤ 3.6 V,	20 MHz < fMCK ≤ 24 MHz	32/fmck		ns
		2.3 V ≤ Vb ≤ 2.7 V	16 MHz < fMCK ≤ 20 MHz	28/fmck		ns
			8 MHz < fMCK ≤ 16 MHz	24/fmck		ns
			4 MHz < fMCK ≤ 8 MHz	16/fmck		ns
			fMCK ≤ 4 MHz	12/fmck		ns
		2.4 V ≤ VDD < 3.3 V,	20 MHz < fMCK ≤ 24 MHz	72/fmck		ns
		1.6 V ≤ V _b ≤ 2.0 V Note 2	16 MHz < fMCK ≤ 20 MHz	64/fmck		ns
			8 MHz < fMCK ≤ 16 MHz	52/fmck		ns
			4 MHz < fMCK ≤ 8 MHz	32/fmck		ns
			fMCK ≤ 4 MHz	20/fmck		ns
SCKp high-/low-level width	tKH2, tKL2	2.7 V ≤ VDD ≤ 3.6 V, 2.3 V ≤ Vb ≤ 2.7 V		tKCY2/2 - 36		ns
		2.4 V ≤ VDD < 3.3 V, 1.6 V ≤ Vb ≤ 2.0 V Note 2		tKCY2/2 - 100		ns
SIp setup time (to SCKp↑) Note 3	tSIK2	2.7 V ≤ VDD ≤ 3.6 V		1/fмcк + 40		ns
		2.4 V ≤ VDD < 3.3 V	1/fмcк + 60		ns	
SIp hold time (from SCKp↑) Note 4	tKSI2			1/fмск + 62		ns
Delay time from SCKp↓ to SOp output Note 5	tKSO2	$2.7 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, 2.3 \text{ V} \le \text{Vb} \le 2.7 \text{ V}$ Cb = 30 pF, Rb = 2.7 k Ω			2/fMCK + 428	ns
		$2.4 \text{ V} \le \text{VDD} < 3.3 \text{ V}, 1.6 \text{ V} \le \text{V}_b \le 2.0 \text{ V}$ Note 2 Cb = 30 pF, Rb = 5.5 kΩ			2/fMCK + 1146	ns

- Note 1. Transfer rate in the SNOOZE mode: MAX. 1 Mbps
- **Note 2.** Use it with $VDD \ge Vb$.
- Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 4. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 5. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Caution Select the TTL input buffer for the SIp pin and SCKp pin and the N-ch open drain output (VDD tolerance) mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the next page.)

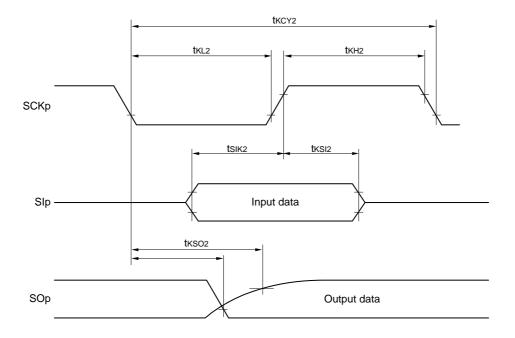


Simplified SPI (CSI) mode connection diagram (during communication at different potential)

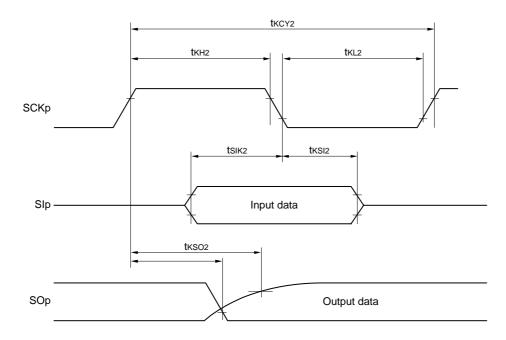


- Remark 1. $Rb[\Omega]$: Communication line (SOp) pull-up resistance, Cb[F]: Communication line (SOp) load capacitance, Vb[V]: Communication line voltage
- **Remark 2.** p: CSI number (p = 00, 10, 20, 30), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM and POM number (g = 0 to 3)
- Remark 3. fmck: Serial array unit operation clock frequency
 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 02, 10, 12))

Simplified SPI (CSI) mode serial transfer timing (slave mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



Simplified SPI (CSI) mode serial transfer timing (slave mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remark p: CSI number (p = 00, 10, 20, 30), m: Unit number (m = 0, 1),

n: Channel number (n = 0 to 3), g: PIM and POM number (g = 0 to 3)

(8) Communication at different potential (1.8 V, 2.5 V) (simplified I²C mode)

 $(TA = -40 \text{ to } +105^{\circ}C, 2.4 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, \text{Vss} = 0 \text{ V})$

D	0	O a madistica ma	HS (high-speed	I main) Mode	1.1-14
Parameter	Symbol	Conditions	MIN.	MAX.	Unit
SCLr clock frequency	fscL	$2.7 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, 2.3 \text{ V} \le \text{Vb} < 2.7 \text{ V},$ $\text{Cb} = 50 \text{ pF}, \text{Rb} = 2.7 \text{ k}\Omega$		400 Note 1	kHz
		$2.7 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, 2.3 \text{ V} \le \text{Vb} < 2.7 \text{ V},$ Cb = 100 pF, Rb = 2.7 kΩ		100 Note 1	kHz
		$2.4 \text{ V} \le \text{VDD} < 3.3 \text{ V}, 1.6 \text{ V} \le \text{Vb} \le 2.0 \text{ V}$ Note 2, Cb = 100 pF, Rb = 5.5 kΩ		100 Note 1	kHz
Hold time when SCLr = "L"	tLOW	$2.7 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, 2.3 \text{ V} \le \text{Vb} < 2.7 \text{ V},$ Cb = 50 pF, Rb = 2.7 k Ω	1200		ns
		$2.7 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, 2.3 \text{ V} \le \text{Vb} < 2.7 \text{ V},$ Cb = 100 pF, Rb = 2.7 kΩ	4600		ns
		$2.4 \text{ V} \le \text{VDD} < 3.3 \text{ V}, 1.6 \text{ V} \le \text{Vb} \le 2.0 \text{ V}$ Note 2, Cb = 100 pF, Rb = 5.5 kΩ	4650		ns
Hold time when SCLr = "H"	tHIGH	$2.7 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, 2.3 \text{ V} \le \text{Vb} < 2.7 \text{ V},$ Cb = 50 pF, Rb = 2.7 k Ω	500		ns
		$2.7 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, 2.3 \text{ V} \le \text{Vb} < 2.7 \text{ V},$ Cb = 100 pF, Rb = 2.7 kΩ	2400		ns
		$2.4 \text{ V} \le \text{VDD} < 3.3 \text{ V}, 1.6 \text{ V} \le \text{V}_b \le 2.0 \text{ V}$ Note 2, Cb = 100 pF, Rb = 5.5 kΩ	1830		ns
Data setup time (reception)	tsu:dat	$2.7 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, 2.3 \text{ V} \le \text{Vb} < 2.7 \text{ V},$ Cb = 50 pF, Rb = 2.7 k Ω	1/fMCK + 340 Note 3		ns
		$2.7 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, 2.3 \text{ V} \le \text{Vb} < 2.7 \text{ V},$ Cb = 100 pF, Rb = 2.7 kΩ	1/fMCK + 760 Note 3		ns
		$2.4 \text{ V} \le \text{VDD} < 3.3 \text{ V}, 1.6 \text{ V} \le \text{Vb} \le 2.0 \text{ V}$ Note 2, Cb = 100 pF, Rb = 5.5 kΩ	1/fMCK + 570 Note 3		ns
Data hold time (transmission)	thd:dat	$2.7 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, 2.3 \text{ V} \le \text{Vb} < 2.7 \text{ V},$ Cb = 50 pF, Rb = 2.7 k Ω	0	770	ns
		$2.7 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, 2.3 \text{ V} \le \text{Vb} < 2.7 \text{ V},$ Cb = 100 pF, Rb = 2.7 kΩ	0	1420	ns
		$2.4 \text{ V} \le \text{VDD} < 3.3 \text{ V}, 1.6 \text{ V} \le \text{Vb} \le 2.0 \text{ V}$ Note 2, Cb = 100 pF, Rb = 5.5 kΩ	0	1215	ns

Note 1. The value must be equal to or less than fMCK/4.

Note 2. Use it with $VDD \ge Vb$.

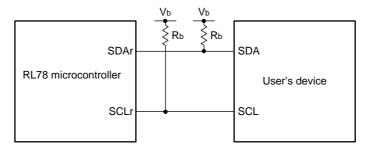
Note 3. Set the fMCK value to keep the hold time of SCLr = "L" and SCLr = "H".

Caution Select the TTL input buffer and the N-ch open drain output (VDD tolerance) mode for the SDAr pin and the N-ch open drain output (VDD tolerance) mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

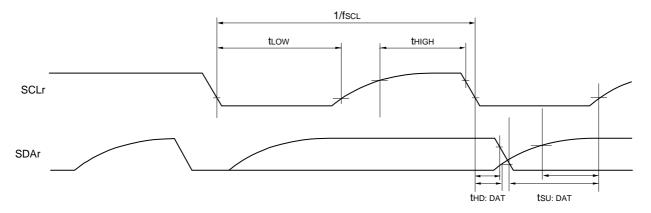
(Remarks are listed on the next page.)



Simplified I²C mode connection diagram (during communication at different potential)



Simplified I²C mode serial transfer timing (during communication at different potential)



Remark 1. Rb[Ω]: Communication line (SDAr, SCLr) pull-up resistance, Cb[F]: Communication line (SDAr, SCLr) load capacitance, Vb[V]: Communication line voltage

Remark 2. r: IIC number (r = 00, 10, 20, 30), g: PIM, POM number (g = 0 to 3)

Remark 3. fmck: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), mn = 00, 02, 10, 12)

3.5.2 Serial interface IICA

 $(TA = -40 \text{ to } +105^{\circ}C, 2.4 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, \text{Vss} = 0 \text{ V})$

			H	S (high-spee	ed main) Mo	de	
Parameter	Symbol	Conditions	Standa	rd mode	Fast	Unit	
			MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	fSCL	Fast mode: fclk ≥ 3.5 MHz	_	_	0	400	kHz
		Standard mode: fcLK ≥ 1 MHz	0	100	_	_	kHz
Setup time of restart condition	tsu: sta		4.7		0.6		μs
Hold time Note 1	thd: STA		4.0		0.6		μs
Hold time when SCLA0 = "L"	tLOW		4.7		1.3		μs
Hold time when SCLA0 = "H"	tHIGH		4.0		0.6		μs
Data setup time (reception)	tsu: dat		250		100		ns
Data hold time (transmission) Note 2	thd: dat		0	3.45	0	0.9	μs
Setup time of stop condition	tsu: sto		4.0		0.6		μs
Bus-free time	tBUF		4.7		1.3		μs

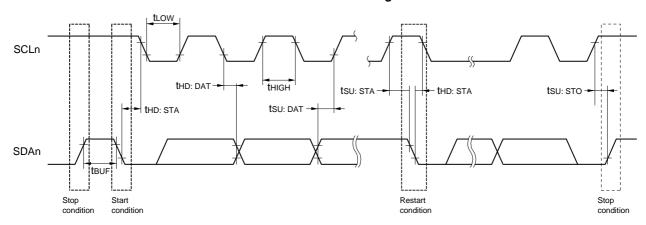
Note 1. The first clock pulse is generated after this period when the start/restart condition is detected.

Note 2. The maximum value (MAX.) of thd:DAT is during normal transfer and a clock stretch state is inserted in the ACK (acknowledge) timing.

Remark The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

Standard mode: $C_b = 400 \text{ pF}, R_b = 2.7 \text{ k}\Omega$ Fast mode: $C_b = 320 \text{ pF}, R_b = 1.1 \text{ k}\Omega$

IICA serial transfer timing



3.5.3 USB

(1) Electrical specifications

$(TA = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter		Symbol	Conditions	MIN.	TYP.	MAX.	Unit
UREGC	UREGC output voltage characteristic	UREGC	UVBUS = 4.0 to 5.5 V, PXXCON = VDDUSBE = 1	3.0	3.3	3.6	V
UVBUS	UVBUS input voltage characteristic	UVBUS	Function	4.35 (4.02 ^{Note})	5.00	5.25	V

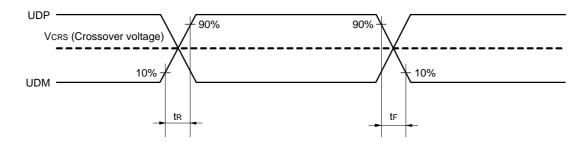
Note Value of instantaneous voltage

(TA = -40 to +105°C, 4.35 V \leq UVBUS \leq 5.25 V, 2.4 V \leq VDD \leq 3.6 V, VSS = 0 V)

	Parameter		Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Input	Input voltag	ge	VIH		2.0			V
characteristic			VIL				0.8	V
(FS/LS receiver)	Difference sensitivity	Difference input sensitivity		UDP voltage - UDM voltage	0.2			V
		Difference common mode range			0.8		2.5	V
Output	Output volt	age	Vон	IOH = -200 μA	2.8		3.6	V
characteristic			VoL	IoL = 2 mA	0		0.3	V
(FS driver)	Transition	Rising	tFR	Rising: From 10% to 90% of amplitude,	4		20	ns
	time	Falling	tFF	Falling: From 90% to 10% of amplitude,	4		20	ns
	Matching (Matching (TFR/TFF)		- CL = 50 pF	90		111.1	%
	Crossover	Crossover voltage					2.0	V
	Output Imp	Output Impedance			28		44	Ω
	Output voltage		Vон		2.8		3.6	V
characteristic			VoL		0		0.3	V
(LS driver)	Transition	Rising	tLR	Rising: From 10% to 90% of amplitude,	75		300	ns
	time	Falling	tLF	Falling: From 90% to 10% of amplitude,	75		300	ns
	Matching (TFR/TFF)	VLTFM	CL = 250 pF to 750 pF	80		125	%
	Note			The UDP and UDM pins are individually pulled				
	Crossover	voltage Note	VLCRS	down via 15 kΩ	1.3		2.0	V
Pull-up,	Pull-down i	esistor	RPD		14.25		24.80	kΩ
Pull-down	Pull-up	Idle	Rpui		0.9		1.575	kΩ
	resistor	Reception	RPUA		1.425		3.09	kΩ
UVBUS	UVBUS pull resistor	-down	Rvbus	UVBUS voltage = 5.5 V		1000		kΩ
	UVBUS inpu	ut voltage	VIH		3.20			V
			VIL				0.8	V

Note Excludes the first signal transition from the idle state.

Timing of UDP and UDM



(2) BC standard

(TA = -40 to +105°C, 4.35 V \leq UVBUS \leq 5.25 V, 2.4 V \leq VDD \leq 3.6 V, VSS = 0 V)

	Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
USB	UDP sink current	IDP_SINK		25	100	175	μΑ
standard	UDM sink current	IDM_SINK		25	100	175	μΑ
BC1.2	DCD source current	IDP_SRC		7	10	13	μΑ
	Data detection voltage	VDAT_REF		0.25	0.325	0.4	V
	UDP source voltage	VDP_SRC	Output current 250 µA	0.5	0.6	0.7	V
	UDM source voltage	VDM_SRC	Output current 250 µA	0.5	0.6	0.7	V

(3) BC option standard

(TA = -40 to +105°C, 4.35 V \leq UVBUS \leq 5.25 V, 2.4 V \leq VDD \leq 3.6, VSS = 0 V)

Para	meter		Symbol	Conditions	MIN.	TYP.	MAX.	Unit
UDP/UDM input reference	VDSELi [3: 0]	0000	VDDET0		27	32	37	%UVBUS
voltage	(i = 0, 1)	0001	VDDET1		29	34	39	%UVBUS
(UVBUS divider ratio)		0010	VDDET2		32	37	42	%UVBUS
(Function)		0011	VDDET3		35	40	45	%UVBUS
		0100	VDDET4		38	43	48	%UVBUS
		0101	VDDET5		41	46	51	%UVBUS
		0110	VDDET6		44	49	54	%UVBUS
		0111	VDDET7		47	52	57	%UVBUS
		1000	VDDET8		51	56	61	%UVBUS
		1001	VDDET9		55	60	65	%UVBUS
		1010	VDDET10		59	64	69	%UVBUS
		1011	VDDET11		63	68	73	%UVBUS
		1100	VDDET12		67	72	73	%UVBUS
		1101	VDDET13		71	76	81	%UVBUS
		1110	VDDET14		75	80	85	%UVBUS
		1111	VDDET15		79	84	89	%UVBUS

3.6 Analog Characteristics

3.6.1 A/D converter characteristics

Classification of A/D converter characteristics

Reference Voltage Input Channel	Reference voltage (+) = AVREFP Reference voltage (-) = AVREFM	Reference voltage (+) = AVDD Reference voltage (-) = AVSS	Reference voltage (+) = Internal reference voltage Reference voltage (-) = AVss
High-accuracy channel; ANI0 to ANI6 (input buffer power supply: AVDD)	Refer to 3.6.1 (1) .	Refer to 3.6.1 (2) .	Refer to 3.6.1 (5) .
Standard channel; ANI16 to ANI21 (input buffer power supply: VDD)	Refer to 3.6.1 (3) .	Refer to 3.6.1 (4) .	
Internal reference voltage, Temperature sensor output voltage	Refer to 3.6.1 (3) .	Refer to 3.6.1 (4) .	_

(1) When reference voltage (+) = AVREFP/ANIO (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), conversion target: ANI2 to ANI6

(TA = -40 to +105°C, 2.4 V \leq AVREFP \leq AVDD = VDD \leq 3.6 V, VSS = 0 V, AVSS = 0 V, Reference voltage (+) = AVREFP, Reference voltage (-) = AVREFM = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	Res		2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V	8		12	bit
Overall error Note	AINL	12-bit resolution	2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±6.0	LSB
Conversion time	tCONV	ADTYP = 0, 12-bit resolution	2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V	3.375			μs
Zero-scale error Note	Ezs	12-bit resolution	2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±4.5	LSB
Full-scale error Note	EFS	12-bit resolution	2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±4.5	LSB
Integral linearity error Note	ILE	12-bit resolution	2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±2.0	LSB
Differential linearity error Note	DLE	12-bit resolution	2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±1.5	LSB
Analog input voltage	VAIN			0		AVREFP	V

Note Excludes quantization error (±1/2 LSB).

(2) When reference voltage (+) = AVDD (ADREFP1 = 0, ADREFP0 = 0), reference voltage (-) = AVSS (ADREFM = 0), conversion target: ANI0 to ANI6

(TA = -40 to +105°C, 2.4 V \leq AVDD = VDD \leq 3.6 V, Vss = 0 V, AVss = 0 V, Reference voltage (+) = AVDD, Reference voltage (-) = AVss = 0 V)

Parameter	Symbol	C	Conditions		TYP.	MAX.	Unit
Resolution	RES		2.4 V ≤ AVDD ≤ 3.6 V	8		12	bit
Overall error Note	AINL	12-bit resolution	2.4 V ≤ AVDD ≤ 3.6 V			±7.5	LSB
Conversion time	tCONV	ADTYP = 0, 12-bit resolution	2.4 V ≤ AVDD ≤ 3.6 V	3.375			μs
Zero-scale error Note	Ezs	12-bit resolution	2.4 V ≤ AVDD ≤ 3.6 V			±6.0	LSB
Full-scale error Note	EFS	12-bit resolution	2.4 V ≤ AVDD ≤ 3.6 V			±6.0	LSB
Integral linearity error Note	ILE	12-bit resolution	2.4 V ≤ AVDD ≤ 3.6 V			±3.0	LSB
Differential linearity error Note	DLE	12-bit resolution	2.4 V ≤ AVDD ≤ 3.6 V			±2.0	LSB
Analog input voltage	Vain			0		AVDD	V

Note Excludes quantization error (±1/2 LSB).

(3) When reference voltage (+) = AVREFP/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), conversion target ANI16 to ANI21, internal reference voltage, temperature sensor output voltage

(TA = -40 to +105°C, 2.4 V \leq VDD \leq 3.6 V, 2.4 V \leq AVREFP \leq AVDD = VDD \leq 3.6 V, Vss = 0 V, AVss = 0 V, Reference voltage (+) = AVREFP, Reference voltage (-) = AVREFM = 0 V)

Parameter	Symbol		Conditions	MIN.	TYP.	MAX.	Unit	
Resolution	Res		2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V	8		12	bit	
Overall error Note 1	AINL	12-bit resolution	2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±7.0	LSB	
Conversion time	tCONV	ADTYP = 0, 12-bit resolution	2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V	4.125			μs	
Zero-scale error Note 1	Ezs	12-bit resolution	2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±5.0	LSB	
Full-scale error Note 1	EFS	12-bit resolution	2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±5.0	LSB	
Integral linearity error Note 1	ILE	12-bit resolution	2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±3.0	LSB	
Differential linearity error	DLE	12-bit resolution	2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±2.0	LSB	
Analog input voltage	VAIN			0		AVREFP	V	
		Internal reference (2.4 V ≤ V _{DD} ≤ 3.6	VBGR Note 2					
		·	Temperature sensor output voltage (2.4 V ≤ VDD ≤ 3.6 V, HS (high-speed main) mode)			V _{TMP25} Note 2		

Note 1. Excludes quantization error (±1/2 LSB).

Note 2. Refer to 3.6.2 Temperature sensor, internal reference voltage output characteristics.

(4) When reference voltage (+) = AVDD (ADREFP1 = 0, ADREFP0 = 0), reference voltage (-) = AVSS (ADREFM = 0), conversion target: ANI16 to ANI21, internal reference voltage, temperature sensor output voltage

(TA = -40 to +105°C, 2.4 V \leq VDD \leq 3.6 V, 2.4 V \leq AVDD = VDD \leq 3.6 V, Vss = 0 V, AVss = 0 V, Reference voltage (+) = AVDD, Reference voltage (-) = AVss = 0)

Parameter	Symbol	Cond	ditions	MIN.	TYP.	MAX.	Unit
Resolution	Res		2.4 V ≤ AVDD ≤ 3.6 V	8		12	bit
Overall error Note 1	AINL	12-bit resolution	2.4 V ≤ AVDD ≤ 3.6 V			±8.5	LSB
Conversion time	tCONV	ADTYP = 0, 12-bit resolution	2.4 V ≤ AVDD ≤ 3.6 V	4.125			μs
Zero-scale error Note 1	Ezs	12-bit resolution	2.4 V ≤ AVDD ≤ 3.6 V			±8.0	LSB
Full-scale error Note 1	EFS	12-bit resolution	2.4 V ≤ AVDD ≤ 3.6 V			±8.0	LSB
Integral linearity error Note 1	ILE	12-bit resolution	2.4 V ≤ AVDD ≤ 3.6 V			±3.5	LSB
Differential linearity error Note 1	DLE	12-bit resolution	2.4 V ≤ AVDD ≤ 3.6 V			±2.5	LSB
Analog input voltage	VAIN		-	0		AVDD	V
		Internal reference voltage (2.4 V ≤ VDD ≤ 3.6 V, HS	\	/BGR Note	2		
	_	Temperature sensor outp (2.4 V ≤ VDD ≤ 3.6 V, HS	ut voltage (high-speed main) mode)	V	TMP25 Note	2	

Note 1. Excludes quantization error (±1/2 LSB).

Note 2. Refer to 3.6.2 Temperature sensor, internal reference voltage output characteristics.

(5) When reference voltage (+) = Internal reference voltage (1.45 V) (ADREFP1 = 1, ADREFP0 = 0), reference voltage (-) = AVSS (ADREFM = 0), conversion target: ANI0 to ANI6, ANI16 to ANI21

(TA = -40 to +105°C, 2.4 V \leq VDD \leq 3.6 V, 2.4 V \leq VDD, 2.4 V \leq AVDD = VDD, Vss = 0 V, AVss = 0 V, Reference voltage (+) = internal reference voltage, Reference voltage (-) = AVss = 0 V, HS (high-speed main) mode)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Resolution	RES		8			bit
Conversion time	tconv	8-bit resolution	16.0			μs
Zero-scale error Note	Ezs	8-bit resolution			±4.0	LSB
Integral linearity error Note	ILE	8-bit resolution			±2.0	LSB
Differential linearity error Note	DLE	8-bit resolution			±2.5	LSB
Reference voltage (+)	AVREF(+)	= Internal reference voltage (VBGR)	1.38	1.45	1.5	V
Analog input voltage	VAIN		0		VBGR	V

Note Excludes quantization error (±1/2 LSB).

Caution Always use AVDD pin with the same potential as the VDD pin.

3.6.2 Temperature sensor, internal reference voltage output characteristics

(TA = -40 to +105°C, 2.4 V \leq VDD \leq 3.6 V, Vss = 0 V (HS (high-speed main) mode))

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Temperature sensor output voltage	VTMPS25	Setting ADS register = 80H, TA = +25°C		1.05		V
Internal reference voltage	VBGR	Setting ADS register = 81H	1.38	1.45	1.5	V
Temperature coefficient	FVTMPS	Temperature sensor output voltage that depends on the temperature		-3.6		mV/°C
Operation stabilization wait time	tamp		10			μs

3.6.3 D/A converter characteristics

 $(TA = -40 \text{ to } +105^{\circ}C, 2.4 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Cor	MIN.	TYP.	MAX.	Unit	
Resolution	RES					8	bit
Overall error	AINL	Rload = 4 MΩ	2.4 V ≤ VDD ≤ 3.6 V			±2.5	LSB
		Rload = 8 MΩ	2.4 V ≤ VDD ≤ 3.6 V			±2.5	LSB
Settling time	tset	Cload = 20 pF	2.7 V ≤ VDD ≤ 3.6 V			3	μs
			2.4 V ≤ VDD < 2.7 V			6	μs

3.6.4 Comparator

 $(TA = -40 \text{ to } +105^{\circ}C, 2.4 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Cor	nditions	MIN.	TYP.	MAX.	Unit
Input voltage range	Ivref			0		VDD - 1.4	V
	Ivcmp			-0.3		VDD + 0.3	V
Output delay	td	VDD = 3.0 V Input slew rate > 50 mV/µs	3 1			1.2	μs
			High-speed comparator mode, window mode			2.0	μs
			Low-speed comparator mode, standard mode		3	5.0	μs
High-electric-potential judgment voltage	VTW+	High-speed comparator mod	de, window mode		0.76 VDD		V
Low-electric-potential judgment voltage	VTW-	High-speed comparator mod	de, window mode		0.24 VDD		V
Operation stabilization wait time	tCMP			100			μs
Internal reference voltage Note	VBGR	2.4 V ≤ VDD ≤ 3.6 V, HS (hig	h-speed main) mode	1.38	1.45	1.50	V

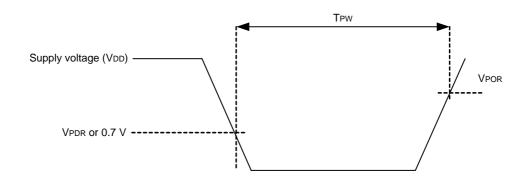
Note Not usable in sub-clock operation or STOP mode.

3.6.5 POR circuit characteristics

 $(TA = -40 \text{ to } +105^{\circ}\text{C}, Vss = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	VPOR	Power supply rise time	1.45	1.51	1.57	V
	VPDR	Power supply fall time Note	1.44	1.50	1.56	V
Minimum pulse width	TPW		300			μs

Minimum time required for a POR reset when VDD exceeds below VPDR. This is also the minimum time required for a POR reset from when VDD exceeds below 0.7 V to when VDD exceeds VPOR while STOP mode is entered or the main system clock is stopped through setting bit 0 (HIOSTOP) and bit 7 (MSTOP) in the clock operation status control register (CSC).



3.6.6 LVD circuit characteristics

(TA = -40 to +105°C, VPDR \leq VDD \leq 3.6 V \leq VSS = 0 V)

Pa	rameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	Supply voltage level	VLVD2	Power supply rise time	3.01	3.13	3.25	V
			Power supply fall time	2.94	3.06	3.18	V
		VLVD3	Power supply rise time	2.90	3.02	3.14	V
			Power supply fall time	2.85	2.96	3.07	V
		VLVD4	Power supply rise time	2.81	2.92	3.03	V
			Power supply fall time	2.75	2.86	2.97	V
		VLVD5	Power supply rise time	2.71	2.81	2.92	V
			Power supply fall time	2.64	2.75	2.86	V
		VLVD6	Power supply rise time	2.61	2.71	2.81	V
			Power supply fall time	2.55	2.65	2.75	V
		VLVD7	Power supply rise time	2.51	2.61	2.71	V
			Power supply fall time	2.45	2.55	2.65	V
Minimum pulse wic	Minimum pulse width			300			μs
Detection delay tim	ne					300	μs

Caution Set the detection voltage (VLVD) to be within the operating voltage range. The operating voltage range depends on the setting of the user option byte (000C2H/010C2H). The following shows the operating voltage range.

HS (high-speed main) mode: VDD = 2.7 to 3.6 V at 1 MHz to 24 MHz

VDD = 2.4 to 3.6 V at 1 MHz to 16 MHz

LVD Detection Voltage of Interrupt & Reset Mode

(TA = -40 to +105°C, VPDR \leq VDD \leq 3.6 V, Vss = 0 V)

Parameter	Symbol		Conditions			TYP.	MAX.	Unit
Interrupt and reset mode	VLVDD0	VPOC0,	VPOC0, VPOC1, VPOC2 = 0, 1, 1, falling reset voltage: 2.7 V			2.75	2.86	V
	VLVDD1		LVIS0, LVIS1 = 1, 0	Rising release reset voltage	2.81	2.92	3.03	V
				Falling interrupt voltage	2.75	2.86	2.97	V
	VLVDD2		LVIS0, LVIS1 = 0, 1	Rising release reset voltage	2.90	3.02	3.14	V
				Falling interrupt voltage	2.85	2.96	3.07	V

3.7 Power supply voltage rising slope characteristics

 $(TA = -40 \text{ to } +105^{\circ}\text{C}, Vss = 0 \text{ V})$

Parameter	Conditions	MIN.	TYP.	MAX.	Unit
Power supply voltage rising slope	SVDD			54	V/ms

Caution Make sure to keep the internal reset state by the LVD circuit or an external reset until VDD reaches the operating voltage range shown in 3.4 AC Characteristics.

3.8 LCD Characteristics

3.8.1 Resistance division method

(1) Static display mode

(TA = -40 to +105°C, VL4 (MIN.) \leq VDD \leq 3.6 V, VSS = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
LCD drive voltage	VL4		2.0		VDD	V

(2) 1/2 bias method, 1/4 bias method

 $(TA = -40 \text{ to } +105^{\circ}\text{C}, VL4 (MIN.) \le VDD \le 3.6 \text{ V}, VSS = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
LCD drive voltage	VL4		2.7		VDD	V

(3) 1/3 bias method

(TA = -40 to +105°C, VL4 (MIN.) \leq VDD \leq 3.6 V, Vss = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
LCD drive voltage	VL4		2.5		VDD	V

3.8.2 Internal voltage boosting method

(1) 1/3 bias method

(TA = -40 to +105°C, 2.4 V \leq VDD \leq 3.6 V, Vss = 0 V)

Parameter	Symbol	Cond	litions	MIN.	TYP.	MAX.	Unit
LCD output voltage variation range	VL1	C1 to C4 Note 1	VLCD = 04H	0.90	1.00	1.08	V
		= 0.47 µF Note 2	VLCD = 05H	0.95	1.05	1.13	V
			VLCD = 06H	1.00	1.10	1.18	V
			VLCD = 07H	1.05	1.15	1.23	V
			VLCD = 08H	1.10	1.20	1.28	V
			VLCD = 09H	1.15	1.25	1.33	V
			VLCD = 0AH	1.20	1.30	1.38	V
			VLCD = 0BH	1.25	1.35	1.43	V
			VLCD = 0CH	1.30	1.40	1.48	V
			VLCD = 0DH	1.35	1.45	1.53	V
			VLCD = 0EH	1.40	1.50	1.58	V
			VLCD = 0FH	1.45	1.55	1.63	V
			VLCD = 10H	1.50	1.60	1.68	V
			VLCD = 11H	1.55	1.65	1.73	V
			VLCD = 12H	1.60	1.70	1.78	V
			VLCD = 13H	1.65	1.75	1.83	V
Doubler output voltage	VL2	C1 to C4 ^{Note 1} =	0.47 μF	2 V _{L1} - 0.1	2 VL1	2 VL1	V
Tripler output voltage	VL3	C1 to C4 ^{Note 1} = 0.47 µF		3 V _{L1} - 0.15	3 VL1	3 VL1	V
Reference voltage setup time Note 2	tvwait1			5			ms
Voltage boost wait time Note 3	tVWAIT2	C1 to C4 ^{Note 1} =	0.47µF	500			ms

Note 1. This is a capacitor that is connected between voltage pins used to drive the LCD.

- C1: A capacitor connected between CAPH and CAPL
- C2: A capacitor connected between VL1 and GND
- C3: A capacitor connected between VL2 and GND
- C4: A capacitor connected between VL4 and GND
- $C1 = C2 = C3 = C4 = 0.47 \mu F \pm 30\%$
- Note 2. This is the time required to wait from when the reference voltage is specified by using the VLCD register (or when the internal voltage boosting method is selected (by setting the MDSET1 and MDSET0 bits of the LCDM0 register to 01B) if the default value reference voltage is used) until voltage boosting starts (VLCON = 1).
- Note 3. This is the wait time from when voltage boosting is started (VLCON = 1) until display is enabled (LCDON = 1).

(2) 1/4 bias method

$(TA = -40 \text{ to } +105^{\circ}C, 2.4 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conc	ditions	MIN.	TYP.	MAX.	Unit
LCD output voltage variation range	VL1	C1 to C4 Note 1	VLCD = 04H	0.90	1.00	1.08	V
		= 0.47 µF Note 2	VLCD = 05H	0.95	1.05	1.13	V
			VLCD = 06H	1.00	1.10	1.18	V
			VLCD = 07H	1.05	1.15	1.23	V
			VLCD = 08H	1.10	1.20	1.28	V
			VLCD = 09H	1.15	1.25	1.33	V
			VLCD = 0AH	1.20	1.30	1.38	V
Doubler output voltage	VL2	C1 to C4 Note 1 =	= 0.47 μF	2 VL1 - 0.08	2 VL1	2 VL1	V
Tripler output voltage	VL3	C1 to C4 Note 1 =	= 0.47 μF	3 V _{L1} - 0.12	3 VL1	3 VL1	V
Quadruply output voltage	VL4	C1 to C5 Note 1 = 0.47 µF		4 VL1 - 0.16	4 VL1	4 VL1	V
Reference voltage setup time Note 2	tVWAIT1			5			ms
Voltage boost wait time Note 3	tVWAIT2	C1 to C5 Note 1 =	= 0.47µF	500			ms

- **Note 1.** This is a capacitor that is connected between voltage pins used to drive the LCD.
 - C1: A capacitor connected between CAPH and CAPL
 - C2: A capacitor connected between VL1 and GND
 - C3: A capacitor connected between VL2 and GND
 - C4: A capacitor connected between VL3 and GND
 - C5: A capacitor connected between VL4 and GND
 - $C1 = C2 = C3 = C4 = 0.47 \mu F \pm 30\%$
- Note 2. This is the time required to wait from when the reference voltage is specified by using the VLCD register (or when the internal voltage boosting method is selected (by setting the MDSET1 and MDSET0 bits of the LCDM0 register to 01B) if the default value reference voltage is used) until voltage boosting starts (VLCON = 1).
- Note 3. This is the wait time from when voltage boosting is started (VLCON = 1) until display is enabled (LCDON = 1).

3.8.3 Capacitor split method

(1) 1/3 bias method

$(TA = -40 \text{ to } +105^{\circ}C, 2.4 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, \text{VSS} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
VL4 voltage	VL4	C1 to C4 = 0.47 µF Note 2		VDD		V
VL2 voltage	VL2	C1 to C4 = 0.47 µF Note 2	2/3 VL4 - 0.07	2/3 VL4	2/3 V _{L4} + 0.07	V
VL1 voltage	VL1	C1 to C4 = 0.47 µF Note 2	1/3 V _{L4} - 0.08	1/3 VL4	1/3 V _{L4} + 0.08	V
Capacitor split wait time Note 1	tvwait		100			ms

Note 1. This is the wait time from when voltage bucking is started (VLCON = 1) until display is enabled (LCDON = 1).

Note 2. This is a capacitor that is connected between voltage pins used to drive the LCD.

C1: A capacitor connected between CAPH and CAPL

C2: A capacitor connected between VL1 and GND

C3: A capacitor connected between VL2 and GND

C4: A capacitor connected between VL4 and GND

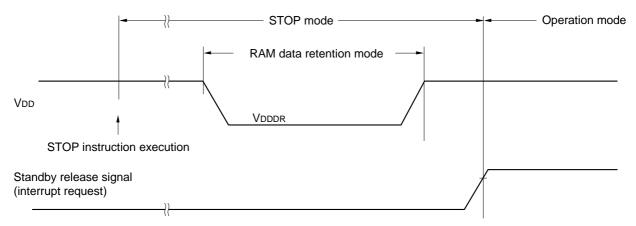
 $C1 = C2 = C3 = C4 = 0.47 \mu F \pm 30\%$

3.9 RAM Data Retention Characteristics

$(TA = -40 \text{ to } +105^{\circ}\text{C}, Vss = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	VDDDR		1.44 Note		3.6	V

Note This depends on the POR detection voltage. For a falling voltage, data in RAM are retained until the voltage reaches the level that triggers a POR reset but not once it reaches the level at which a POR reset is generated.



3.10 Flash Memory Programming Characteristics

$(TA = -40 \text{ to } +105^{\circ}C, 2.4 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
CPU/peripheral hardware clock frequency	fCLK	2.4 V ≤ VDD ≤ 3.6 V	1		24	MHz
Number of code flash rewrites Notes 1, 2, 3	Cerwr	Retained for 20 years TA = 85°C ^{Note 4}	1,000			Times
Number of data flash rewrites Notes 1, 2, 3		Retained for 1 year TA = 25°C		1,000,000		
		Retained for 5 years TA = 85°CNote 4	100,000			
		Retained for 20 years TA = 85°C ^{Note 4}	10,000			

- Note 1. 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the rewrite.
- Note 2. When using flash memory programmer and Renesas Electronics self programming library
- **Note 3.** These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.
- Note 4. This temperature is the average value at which data are retained.

3.11 Dedicated Flash Memory Programmer Communication (UART)

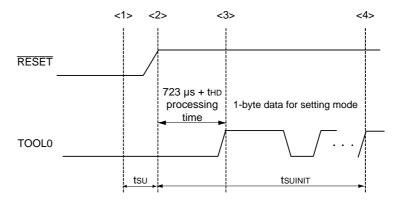
$(TA = -40 \text{ to } +105^{\circ}C, 2.4 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115,200		1,000,000	bps

3.12 Timing of Entry to Flash Memory Programming Modes

 $(TA = -40 \text{ to } +105^{\circ}C, 2.4 \text{ V} \le \text{VDD} \le 3.6 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
How long from when an external reset ends until the initial communication settings are specified	tsuinit	POR and LVD reset must end before the external reset ends.			100	ms
How long from when the TOOL0 pin is placed at the low level until an external reset ends	tsu	POR and LVD reset must end before the external reset ends.	10			μs
Time to hold the TOOL0 pin at the low level after an external reset is released (excluding the processing time of the firmware to control the flash memory)	tHD	POR and LVD reset must end before the external reset ends.	1			ms



- <1> The low level is input to the TOOL0 pin.
- <2> The external reset ends (POR and LVD reset must end before the external reset ends.).
- <3> The TOOL0 pin is set to the high level.
- <4> Setting of the flash memory programming mode by UART reception and complete the baud rate setting.

Remark tsuinit: The segment shows that it is necessary to finish specifying the initial communication settings within 100 ms from

tsu: How long from when the TOOL0 pin is placed at the low level until a external reset ends

thd: How long to keep the TOOL0 pin at the low level from when the external and internal resets end (except soft

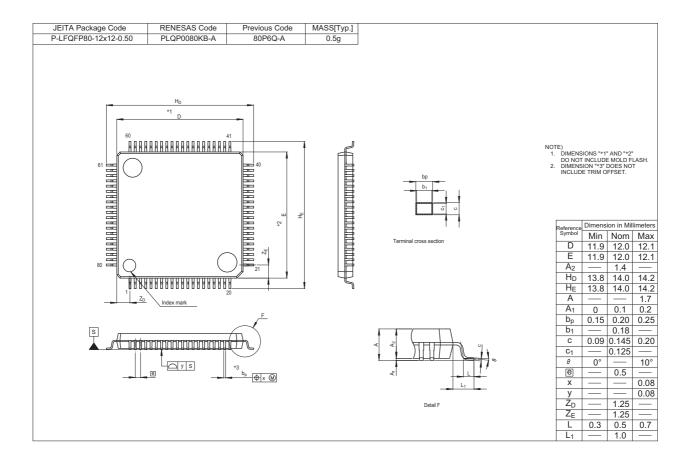
processing time)

RL78/L1C 4. PACKAGE DRAWINGS

4. PACKAGE DRAWINGS

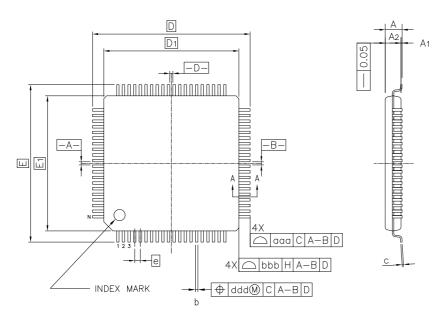
4.1 80-pin products

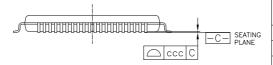
R5F110MEAFB, R5F110MFAFB, R5F110MGAFB, R5F110MHAFB, R5F110MJAFB R5F111MEAFB, R5F111MFAFB, R5F111MGAFB, R5F111MHAFB, R5F111MJAFB R5F110MEGFB, R5F110MFGFB, R5F110MGGFB, R5F110MHGFB, R5F110MJGFB R5F111MEGFB, R5F111MFGFB, R5F111MGGFB, R5F111MHGFB, R5F111MJGFB

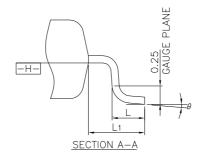


<R>

JEITA Package code	RENESAS code	MASS(TYP.)[g]
P-LFQFP80-12x12-0.50	PLQP0080KJ-A	0.49





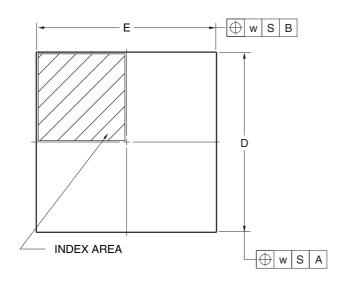


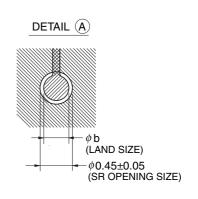
Reference	Dimension in Millimeters				
Symbol	Min.	Nom.	Max.		
А	=	-	1.60		
A ₁	0.05	_	0.15		
A_2	1.35	1.40	1.45		
D	-	14.00	_		
D ₁	-	12.00	_		
E	-	14.00	-		
E ₁	-	12.00	1		
N	ı	80	-		
е	-	0.50	_		
b	0.17	0.22	0.27		
С	0.09	_	0.20		
θ	0,	3.5°	7*		
L	0.45	0.60	0.75		
L ₁	-	1.00	_		
aaa	-	_	0.20		
bbb	_	_	0.20		
ccc		_	0.08		
ddd		_	0.08		

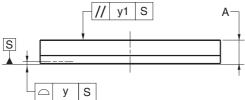
4.2 85-pin products

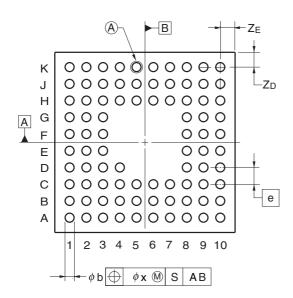
R5F110NEALA, R5F110NFALA, R5F110NGALA, R5F110NHALA, R5F110NJALA R5F111NEALA, R5F111NFALA, R5F111NGALA, R5F111NHALA, R5F111NJALA R5F110NEGLA, R5F110NFGLA, R5F110NGGLA, R5F110NHGLA, R5F111NGGLA, R5F111NHGLA, R5F111NJGLA

JEITA Package code	RENESAS code	Previous code	MASS(TYP.)[g]
P-VFLGA85-7x7-0.65	PVLG0085JA-A	P85FC-65-BN4	0.1









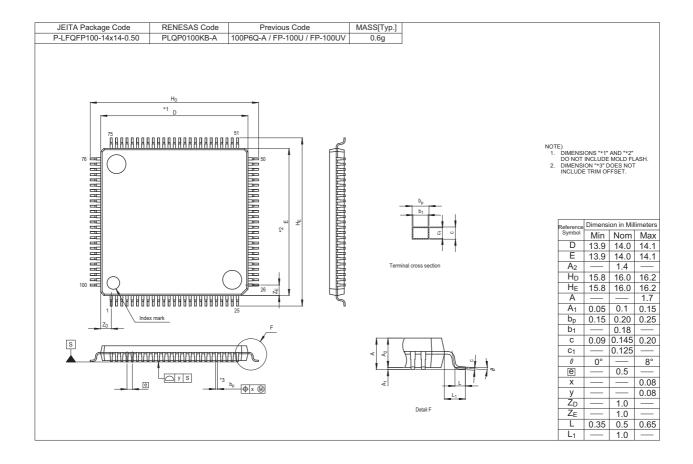
Referance	Dimension in Millimeters			
Symbol	Min	Nom	Max	
D	6.90	7.00	7.10	
E	6.90	7.00	7.10	
Α			1.00	
е		0.65		
b	0.30	0.35	0.40	
х			0.08	
у			0.10	
У1			0.20	
Z _D		0.575		
Z _E		0.575		
W			0.20	

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RL78/L1C 4. PACKAGE DRAWINGS

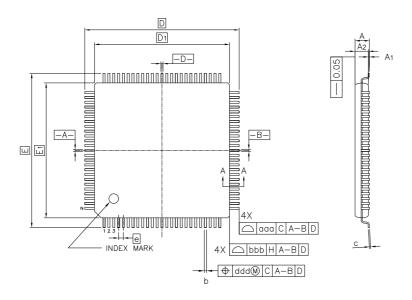
4.3 100-pin products

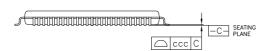
R5F110PEAFB, R5F110PFAFB, R5F110PGAFB, R5F110PHAFB, R5F110PJAFB R5F111PEAFB, R5F111PFAFB, R5F111PGAFB, R5F111PHAFB, R5F111PJAFB R5F110PEGFB, R5F110PFGFB, R5F110PGGFB, R5F110PHGFB, R5F110PJGFB R5F111PEGFB, R5F111PFGFB, R5F111PGGFB, R5F111PHGFB, R5F111PJGFB

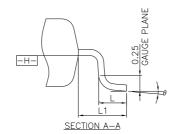


<R>

JEITA Package code	RENESAS code	MASS(TYP.)[g]
P-LFQFP100-14x14-0.50	PLQP0100KP-A	0.67







Reference	Dimension in Millimeters				
Symbol	Min.	Nom.	Max.		
А	_	-	1.60		
A ₁	0.05	_	0.15		
A_2	1.35	1.40	1.45		
D	ı	16.00	ı		
D_1	I	14.00	I		
E	ı	16.00	1		
E ₁	1	14.00	1		
N	1	100	1		
е	-	0.50	ı		
b	0.17	0.22	0.27		
С	0.09	ı	0.20		
θ	°	3.5°	7*		
L	0.45	0.60	0.75		
L ₁	-	1.00	_		
aaa	_	_	0.20		
bbb	_	_	0.20		
ccc		_	0.08		
ddd		_	0.08		

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RL78/L1C Datasheet

	5 /	Description		
Rev.	Date	Page	Summary	
0.01	Oct 15, 2012	_	First Edition issued	
1.00	Nov 18, 2013	1, 2	Modification of 1.1 Features	
		3, 4	Modification of 1.2 Ordering Information	
		5 to 8	Modification of package type in 1.3 Pin Configuration (Top View)	
		14 to 17	Modification of vectored interrupt sources in 1.6 Outline of Functions	
		14 to 17	Modification of operating ambient temperature in 1.6 Outline of Functions	
		19 to 21	Modification of description in tables in 2.1 Absolute Maximum Ratings	
		22, 23	Modification of description in 2.2 Oscillator Characteristics	
		25	Modification of low-level output current in 2.3.1 Pin characteristics	
		26	Modification of error of high-level input voltage conditions in 2.3.1 Pin characteristics	
		26	Modification of error of low-level input voltage conditions in 2.3.1 Pin characteristics	
		27	Modification of low-level output voltage in 2.3.1 Pin characteristics	
		28	Modification of error of internal pull-up resistor conditions in 2.3.1 Pin characteristics	
		29 to 34	Modification of 2.3.2 Supply current characteristics	
		35, 36	Modification of 2.4 AC Characteristics	
		37, 38	Addition of minimum instruction execution time during main system clock operation	
		41 to 63	Addition of LS mode and LV mode characteristics in 2.5.1 Serial array unit	
		64 to 66	Addition of LS mode and LV mode characteristics in 2.5.2 Serial interface IICA	
		67, 68	Modification of conditions in 2.5.3 USB	
		69	Addition of (3) BC option standard in 2.5.3 USB	
		70 to 75	Addition of characteristics about conversion of internal reference voltage and temperature sensor in 2.6.1 A/D converter characteristics	
		76	Addition of characteristic in 2.6.4 Comparator	
		76	Deletion of detection delay in 2.6.5 POR circuit characteristics	
		78	Modification of 2.7 Power supply voltage rising slope characteristics	
		79 to 82	Modification of 2.8 LCD Characteristics	
		83	Modification of 2.9 Data Memory STOP Mode Low Supply Voltage Data Retention Characteristics	
		83	Modification of 2.10 Flash Memory Programming Characteristics	
		84	Addition of 2.12 Timing Specs for Switching Modes	
		85 to 144	Addition of 3. ELECTRICAL SPECIFICATIONS (G: TA = -40 to +105°C)	
2.00	Feb 21, 2014	All	Addition of 85-pin product information	
		All	Modification from 80-pin to 80/85-pin	
		All	Modification from $x = M$, P to $x = M$, N, P	
		All	Modification from high-accuracy real-time clock to real-time clock 2	
		All	Modification from RTC to RTC2	
		1	Modification of 1.1 Features	
		3	Modification of 1.2 Ordering Information	

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RL78/L1C Datasheet

Davi	Data	Description		
Rev.	Date	Page	Summary	
2.00	Feb 21, 2014	4	Modification of Figure 1 - 1 Part Number, Memory Size, and Package of RL78/L1C	
		69	Modification of (1) Electrical specifications in 2.5.3 USB	
		82	Modification of note 1 in (1) 1/3 bias method in 2.8.2 Internal voltage boosting method	
		130	Modification of (1) Electrical specifications in 3.5.3 USB	
		142	Modification of note 1 in (1) 1/3 bias method in 3.8.2 Internal voltage boosting method	
2.10	Aug 12, 2016	5	Addition of product name (RL78/L1C) and description (Top View) in 1.3.1 80-pin products (with USB)	
		6	Addition of product name (RL78/L1C) and description (Top View) in 1.3.2 80-pin products (without USB)	
		9	Addition of product name (RL78/L1C) and description (Top View) in 1.3.5 100-pin products (with USB)	
		10	Addition of product name (RL78/L1C) and description (Top View) in 1.3.6 100-pin products (without USB)	
		17, 19	Modification of 1.6 Outline of Functions	
		23	Modification of description in Absolute Maximum Ratings (TA = 25°C)	
		26, 27	Modification of description in 2.3.1 Pin characteristics	
		39, 40	Modification of the graph for Minimum Instruction Execution Time during Main System Clock Operation	
		72	Modification of conditions in (1) of 2.6.1 A/D converter characteristics	
		85	Modification of the title and note in 2.9 RAM Data Retention Characteristics	
		85	Modification of conditions in 2.10 Flash Memory Programming Characteristics	
		87	Modification of description in 3. ELECTRICAL SPECIFICATIONS (G: INDUSTRIAL APPLICATIONS T _A = -40 to +105 °C)	
		88, 90	Modification of description in Absolute Maximum Ratings (TA = 25°C)	
		93, 94, 96	Modification of description in 3.3.1 Pin characteristics	
		106	Modification of the graph for Minimum Instruction Execution Time during Main System Clock Operation	
		144	Modification of the title and note in 3.9 RAM Data Retention Characteristics	
		145	Modification of conditions and addition of note 4 in 3.10 Flash Memory Programming Characteristics	
2.20	Dec 28, 2017	13	Modification of figure in 1.5.2 80/85-pin products (without USB)	
		17, 19	Modification of tables in 1.6 Outline of Functions	
		26, 27	Modification of table and note 3 in 2.3.1 Pin characteristics	
		85	Modification of figure in 2.12 Timing of Entry to Flash Memory Programming Modes	
		89	Modification of table in 3.1 Absolute Maximum Ratings	
		92, 93	Modification of table and note 3 in 3.3.1 Pin characteristics	
		144	Modification of figure in 3.12 Timing of Entry to Flash Memory Programming Modes	

REVISION HISTORY	RL78/L1C Datasheet
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Rev.	Date	Description	
		Page	Summary
2.21	Nov 30, 2022	All	The module name for CSI was changed to Simplified SPI(CSI)
		All	"wait" for IIC was modified to "clock stretch"
		3	Modification of description in two tables in 1.2 Ordering Information
		4	Modification of packaging specification in Figure1-1
		146	Addition of package drawing in 4.1 80-pin Package
		149	Addition of package drawing in 4.3 100-pin Package

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The following usage notes are applicable to all Microprocessing unit and Microcontroller unit products from Renesas. For detailed usage notes on the products covered by this document, refer to the relevant sections of the document as well as any technical updates that have been issued for the products.

1. Precaution against Electrostatic Discharge (ESD)

A strong electrical field, when exposed to a CMOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop the generation of static electricity as much as possible, and quickly dissipate it when it occurs. Environmental control must be adequate. When it is dry, a humidifier should be used. This is recommended to avoid using insulators that can easily build up static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work benches and floors must be grounded. The operator must also be grounded using a wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions must be taken for printed circuit boards with mounted semiconductor devices.

Processing at power-on

The state of the product is undefined at the time when power is supplied. The states of internal circuits in the LSI are indeterminate and the states of register settings and pins are undefined at the time when power is supplied. In a finished product where the reset signal is applied to the external reset pin, the states of pins are not guaranteed from the time when power is supplied until the reset process is completed. In a similar way, the states of pins in a product that is reset by an on-chip power-on reset function are not guaranteed from the time when power is supplied until the power reaches the level at which resetting is specified.

3. Input of signal during power-off state

Do not input signals or an I/O pull-up power supply while the device is powered off. The current injection that results from input of such a signal or I/O pull-up power supply may cause malfunction and the abnormal current that passes in the device at this time may cause degradation of internal elements. Follow the guideline for input signal during power-off state as described in your product documentation.

4. Handling of unused pins

Handle unused pins in accordance with the directions given under handling of unused pins in the manual. The input pins of CMOS products are generally in the high-impedance state. In operation with an unused pin in the open-circuit state, extra electromagnetic noise is induced in the vicinity of the LSI, an associated shoot-through current flows internally, and malfunctions occur due to the false recognition of the pin state as an input signal become possible.

Clock signals

After applying a reset, only release the reset line after the operating clock signal becomes stable. When switching the clock signal during program execution, wait until the target clock signal is stabilized. When the clock signal is generated with an external resonator or from an external oscillator during a reset, ensure that the reset line is only released after full stabilization of the clock signal. Additionally, when switching to a clock signal produced with an external resonator or by an external oscillator while program execution is in progress, wait until the target clock signal is stable.

- 6. Voltage application waveform at input pin
 - Waveform distortion due to input noise or a reflected wave may cause malfunction. If the input of the CMOS device stays in the area between V_{IL} (Max.) and V_{IH} (Min.) due to noise, for example, the device may malfunction. Take care to prevent chattering noise from entering the device when the input level is fixed, and also in the transition period when the input level passes through the area between V_{IL} (Max.) and V_{IH} (Min.).
- 7. Prohibition of access to reserved addresses

Access to reserved addresses is prohibited. The reserved addresses are provided for possible future expansion of functions. Do not access these addresses as the correct operation of the LSI is not guaranteed.

8. Differences between products

Before changing from one product to another, for example to a product with a different part number, confirm that the change will not lead to problems. The characteristics of a microprocessing unit or microcontroller unit products in the same group but having a different part number might differ in terms of internal memory capacity, layout pattern, and other factors, which can affect the ranges of electrical characteristics, such as characteristic values, operating margins, immunity to noise, and amount of radiated noise. When changing to a product with a different part number, implement a system-evaluation test for the given product.

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